LARGE SCALE STUDIES OF MEMORY, STORAGE, AND NETWORK FAILURES IN A MODERN DATA CENTER

THESIS ORAL

JUSTIN MEZA

Committee

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Prof. James Hoe

Dr. Kaushik Veeraraghavan (Facebook, Inc.)





100'S SOFTWARE SYSTEMS

[Hahn LISA'18]

1,000,000 S CONTAINERS

[Hahn LISA'18]

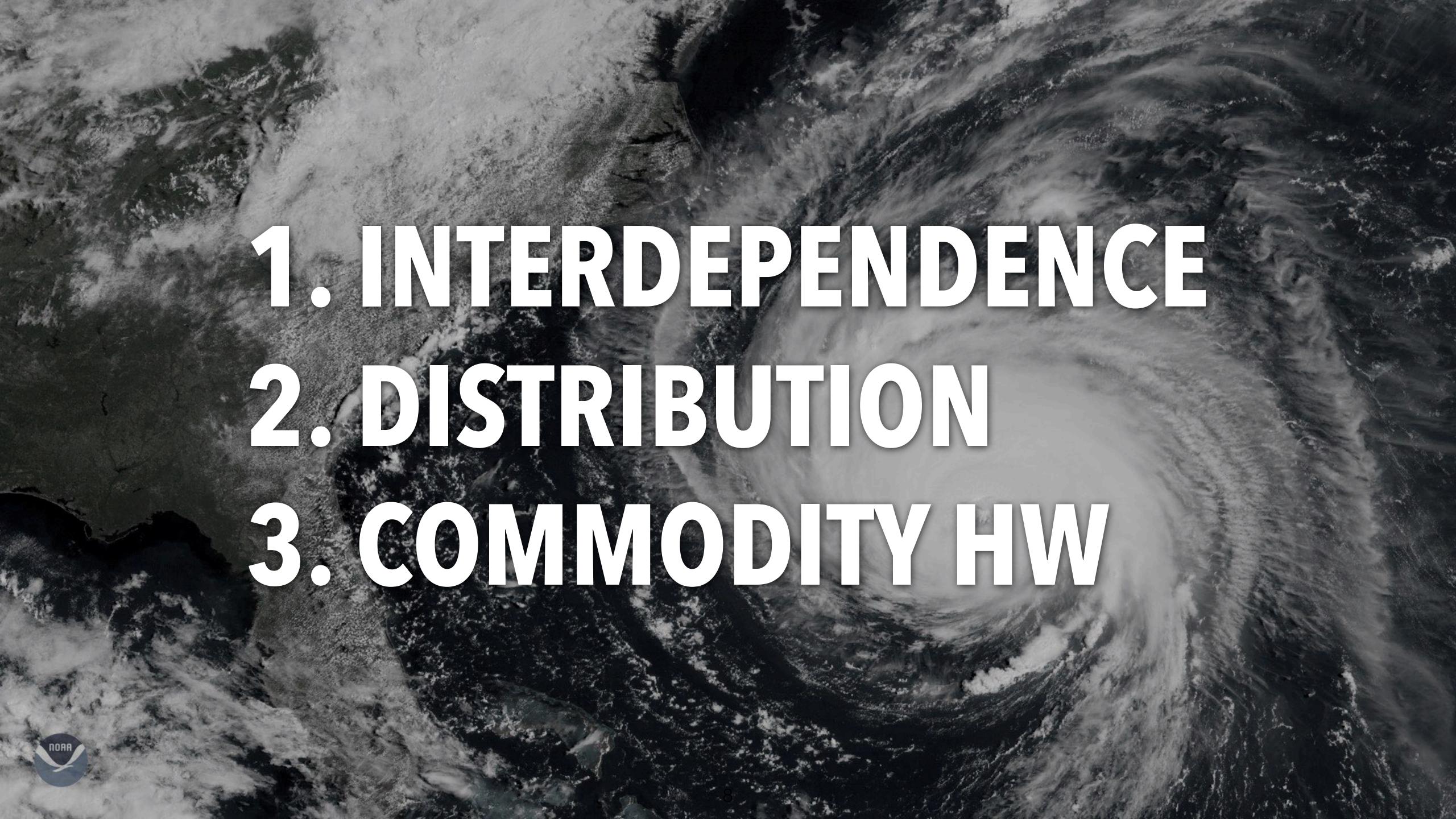
1,000,000,000'S REQUESTS PER SECOND

[Hahn LISA'18]



PROBLEM

Device failures disrupt data center workloads



WEB SERVER

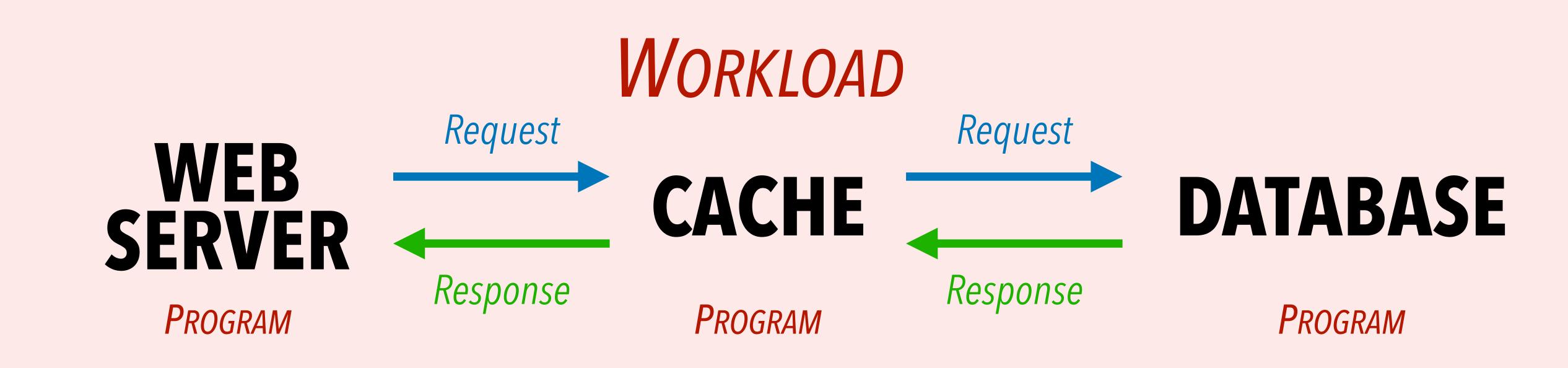
PROGRAM

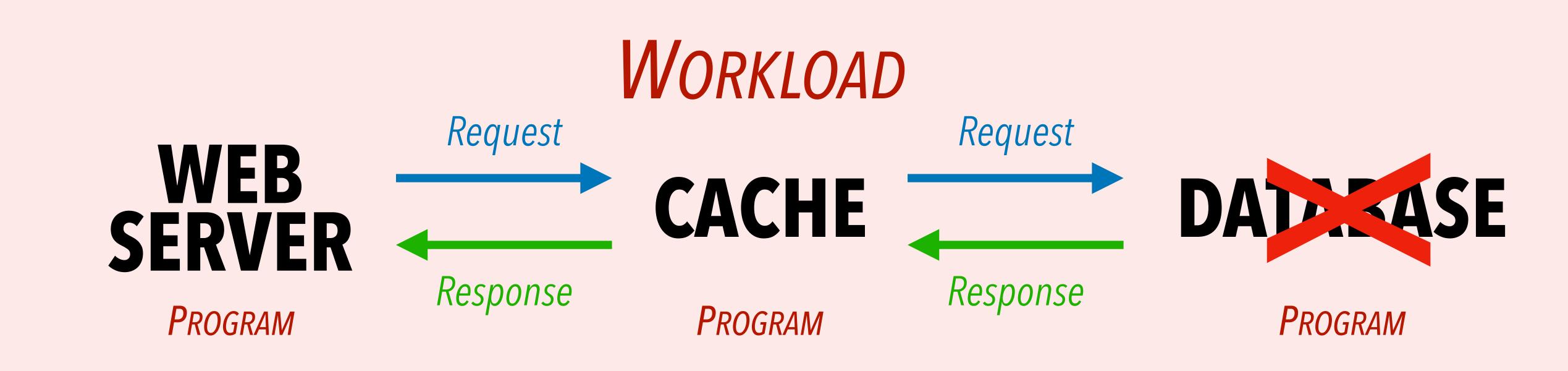
CACHE

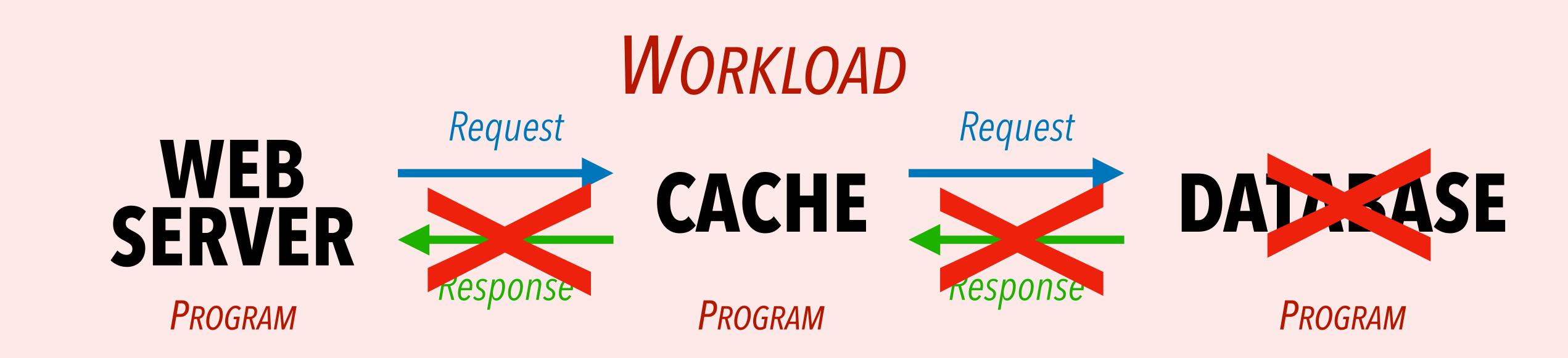
PROGRAM

DATABASE

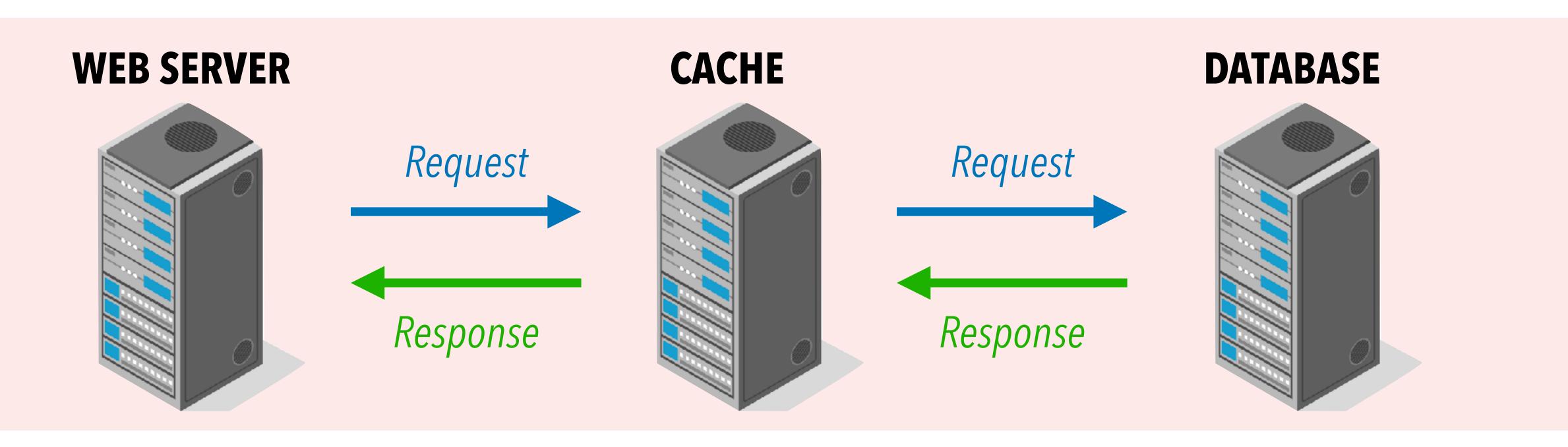
PROGRAM





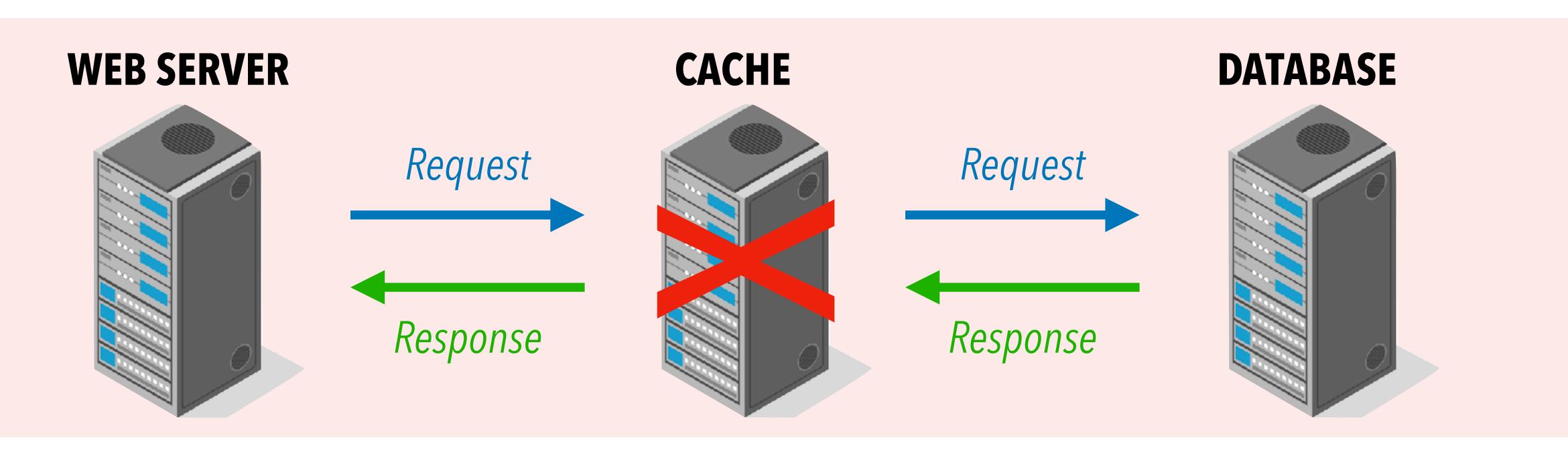


PROBLEM 2: DISTRIBUTION



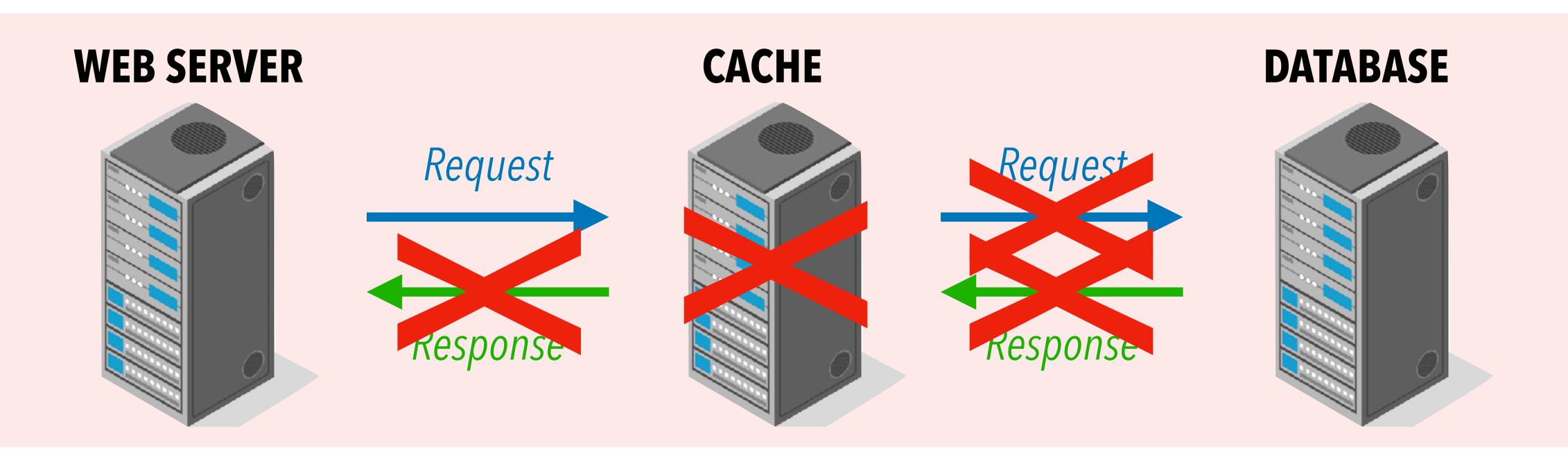
Workloads in modern data centers are distributed across many servers.

PROBLEM 2: DISTRIBUTION



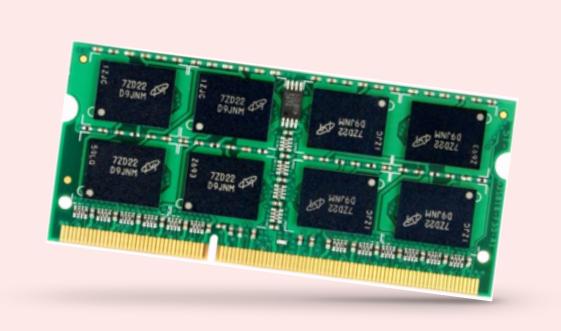
Workloads in modern data centers are distributed across many servers.

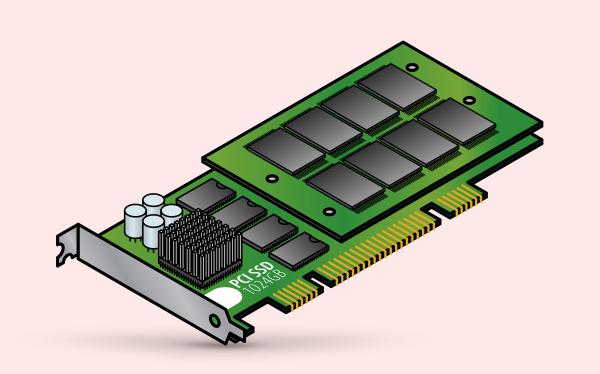
PROBLEM 2: DISTRIBUTION



Workloads in modern data centers are distributed across many servers.

PROBLEM 3: COMMODITY HW



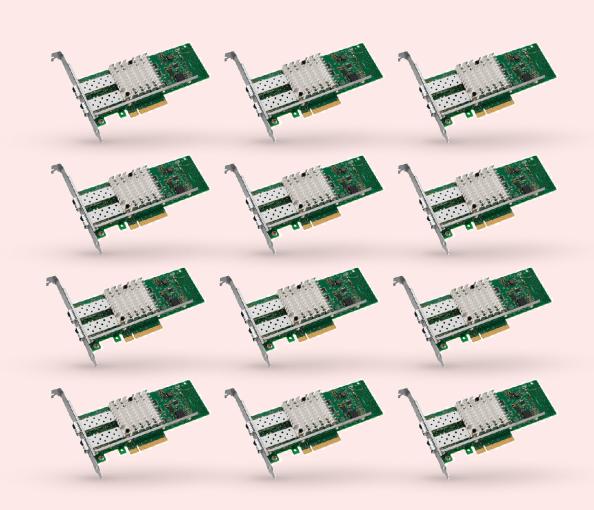




Modern data centers trade off reliability for using simpler, commodity hardware.

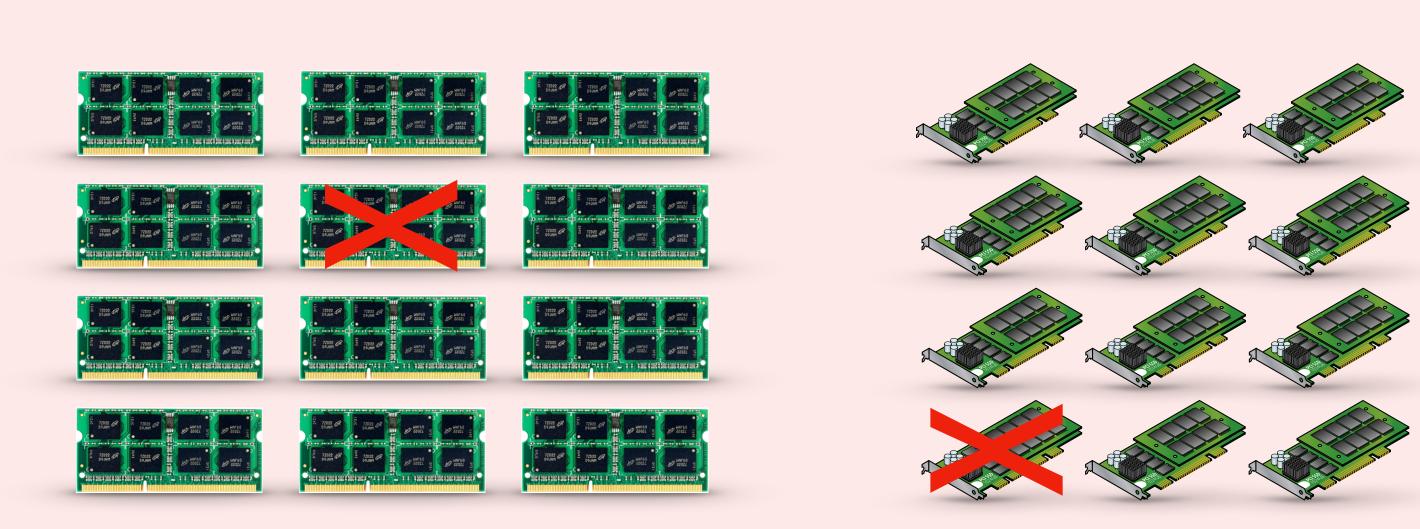
PROBLEM 3: COMMODITY HW

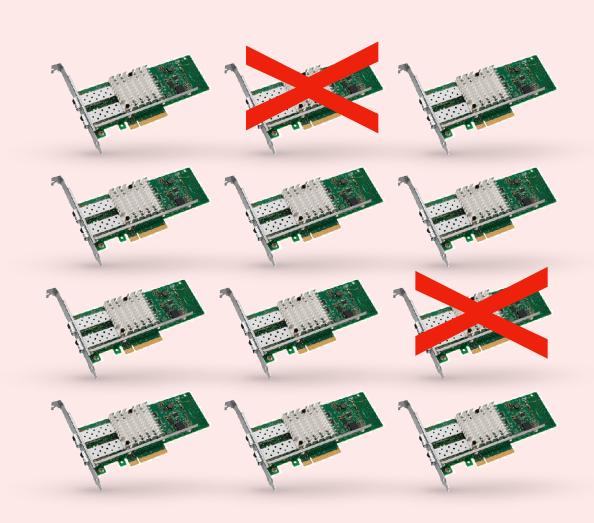




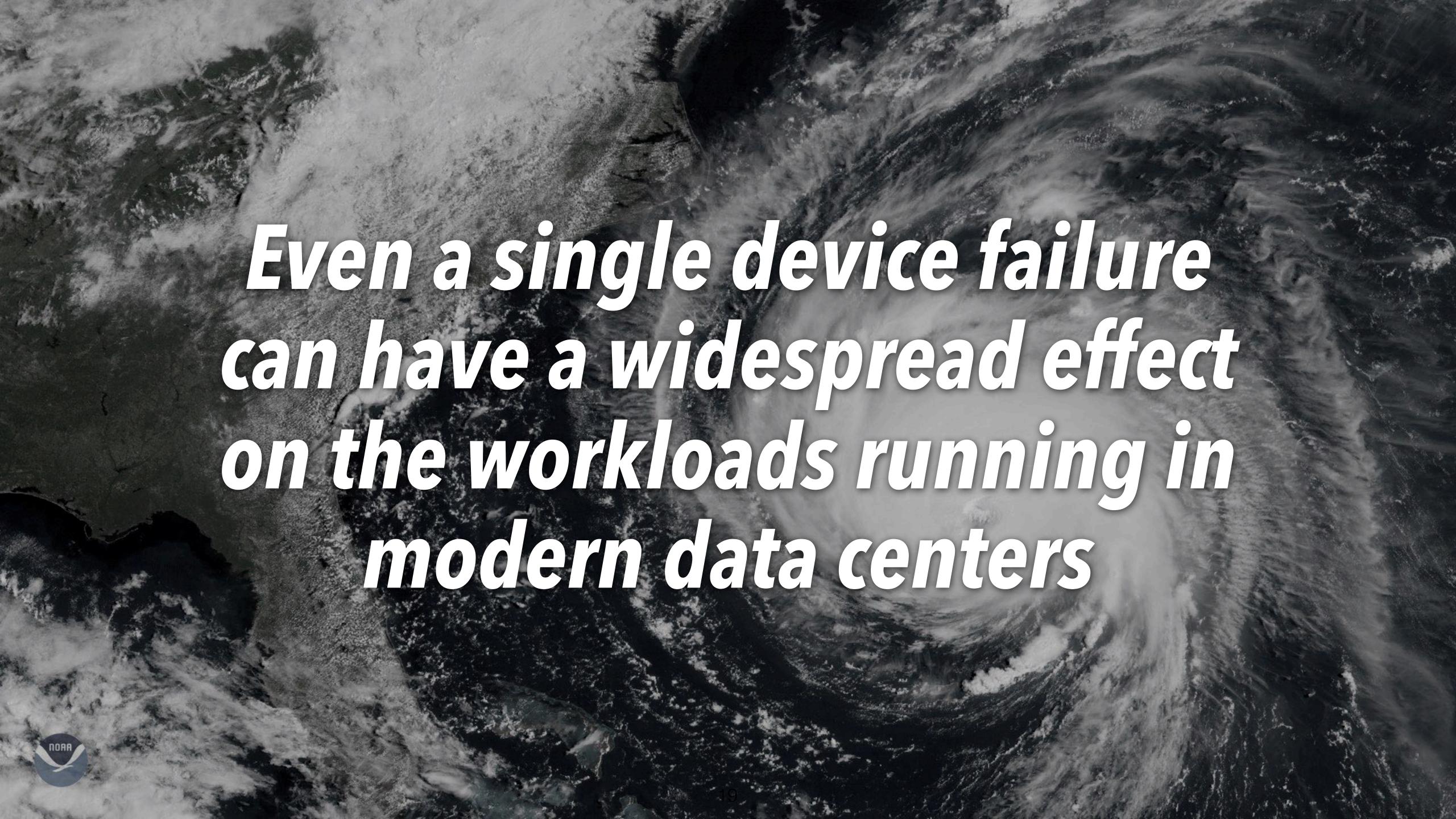
Modern data centers trade off reliability for using simpler, commodity hardware.

PROBLEM 3: COMMODITY HW





Modern data centers trade off reliability for using simpler, commodity hardware.



Here's why Azure's South Central US data center went down earlier this month HOME > NEWS > MIDDLE EAST TO THE BACK Online

Visa details cause of widespread outage, blames data center switch

GitHub suffers major outage caused by faulty Amazon websites outage was due to hardware failure

storage appliance

Where is your Octocat now?

Fail-Slow at Scale: Evidence of Hardware Performance Faults in Large Production Systems

Haryadi S. Gunawi¹, Riza O. Suminto¹, Russell Sears², Casey Golliher², Swaminathan Sundararaman³, Xing Lin⁴, Tim Emami⁴, Weiguang Sheng⁵, Nematollah Bidokhti⁵, Caitie McCaffrey⁶, Gary Grider⁷, Parks M. Fields⁷, Kevin Harms⁸, Robert B. Ross⁸, Andree Jacobson⁹, Robert Ricci¹⁰, Kirk Webb¹⁰, Peter Alvaro¹¹, H. Birali Runesha¹², Mingzhe Hao¹, and Huaicheng Li¹

¹University of Chicago, ²Pure Storage, ³Parallel Machines, ⁴NetApp, ⁵Huawei, ⁶Twitter, ⁷Los Alamos National Laboratory, ⁸Argonne National Laboratory, ⁹New Mexico Consortium, ¹⁰University of Utah, ¹¹University of California, Santa Cruz, and ¹²UChicago Research Computing Center

[FAST'18]

"A fail-slow hardware can collapse the entire cluster performance; for example, a degraded NIC made many jobs lock task slots/containers in healthy machines, hence new jobs cannot find enough free slots."

Measure, model, and learn from device failures to improve data center reliability

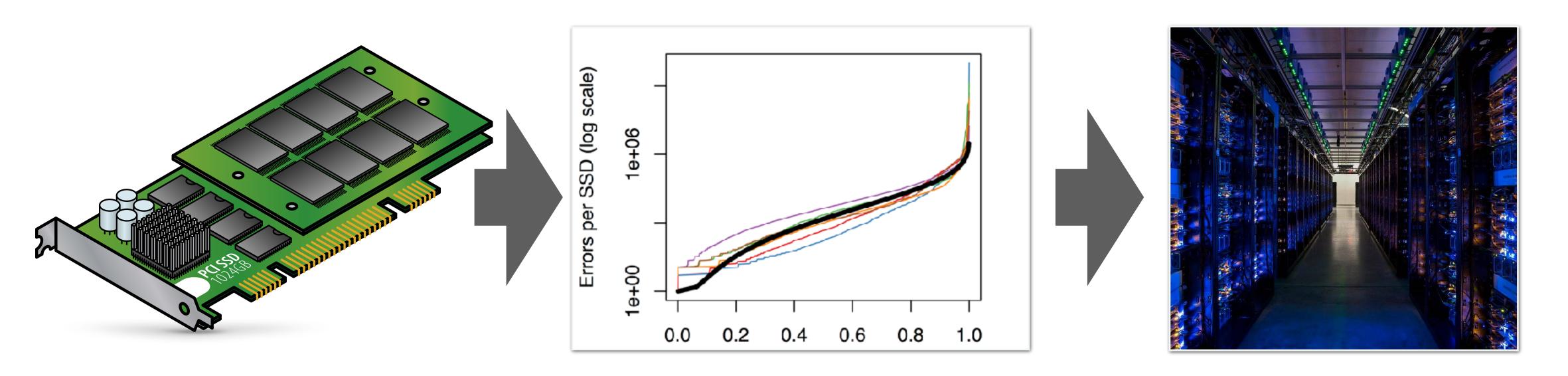
CHALLENGES

- 1. Most device reliability studies are small scale
 - 2. Prior large scale studies hard to generalize
- 3. Limited evaluation of techniques in the wild

THESIS STATEMENT

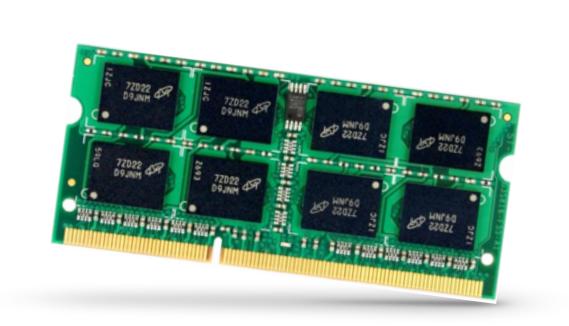
If we **measure** the device failures in modern data centers, then we can learn the reasons why devices fail, develop **models** to predict device failures, and learn from failure trends to make **recommendations** to enable workloads to tolerate device failures.

MEASURE MODEL EVALUATE

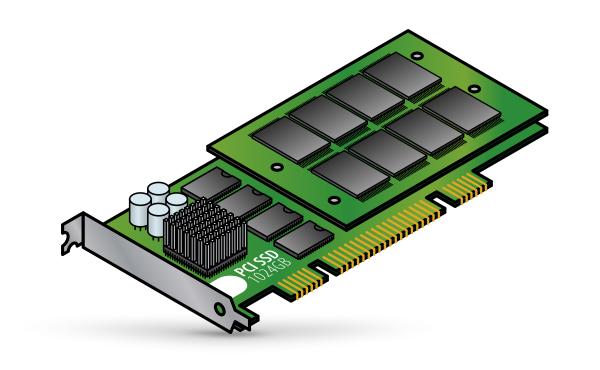


CONTRIBUTIONS

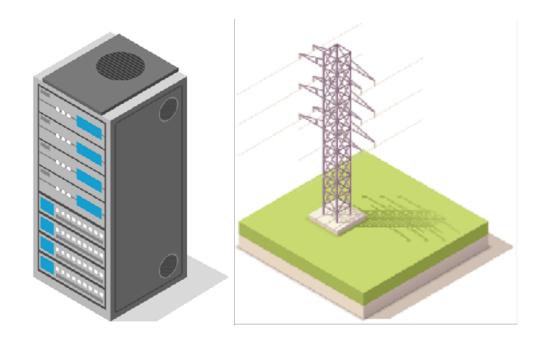
1. Large scale failure studies







SSDS
[SIGMETRICS '15]

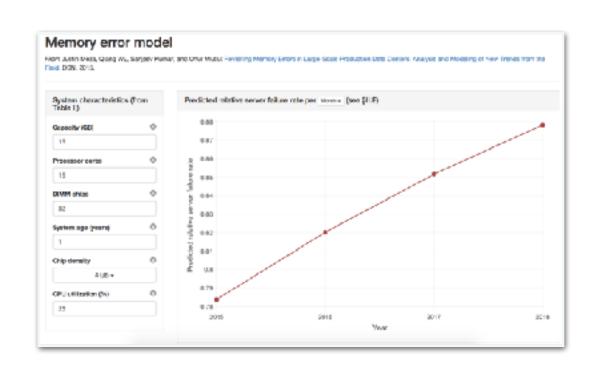


Networks
[IMC '18]

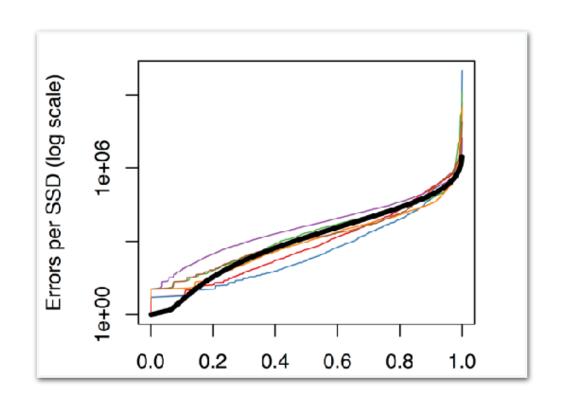
We shed new light on device trends from the field

CONTRIBUTIONS

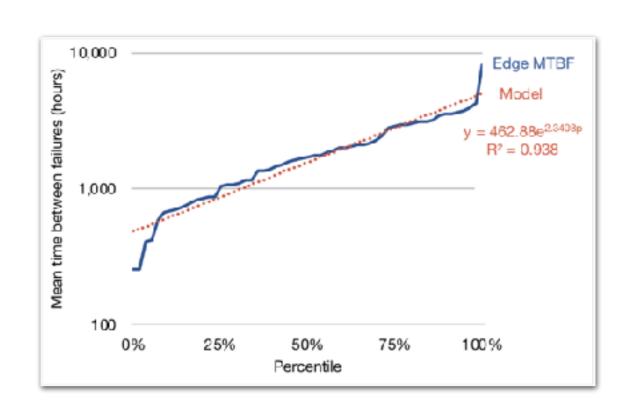
2. Statistical failure models



DRAM
[DSN '15]



SSDS
[SIGMETRICS '15]

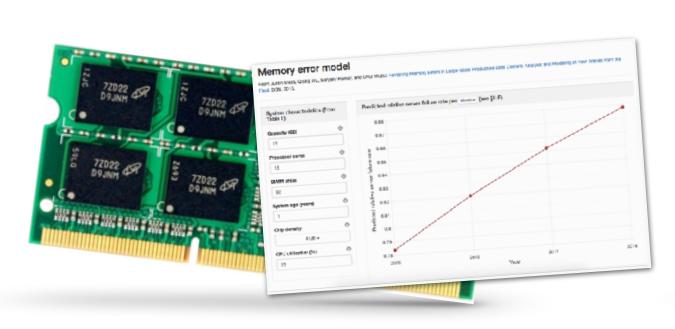


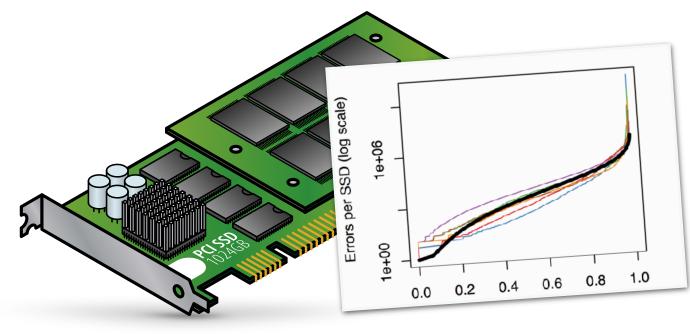
Networks
[IMC '18]

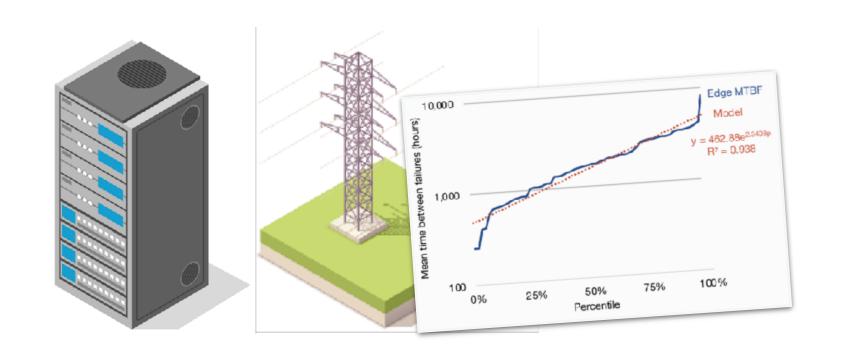
We enable the community to apply what we learn

CONTRIBUTIONS

3. Evaluate best practices in the field







DRAM
Page offlining

SSDS OS write buffering Networks
Software-based
networks

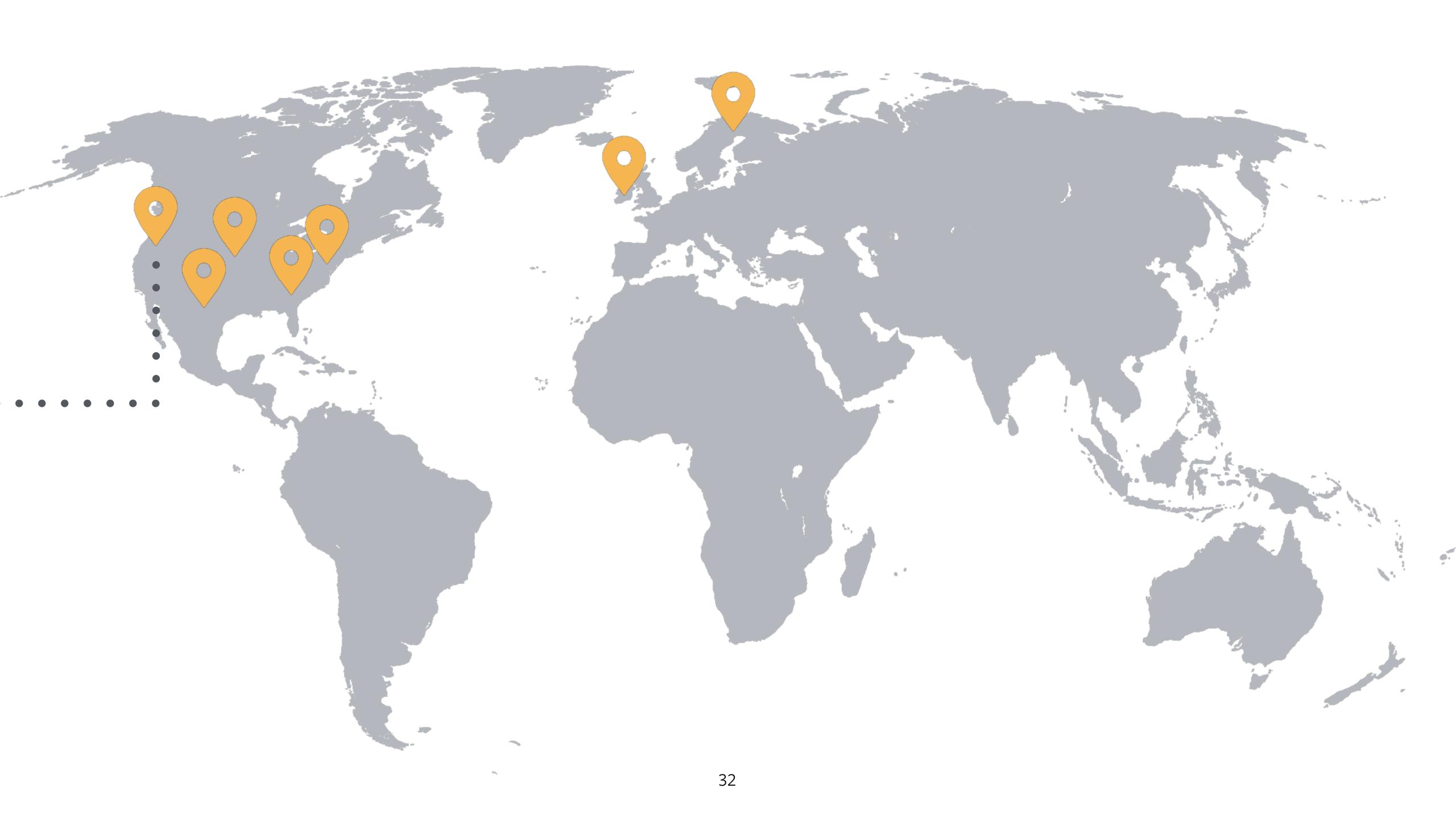
We provide insight into how to tolerate failures

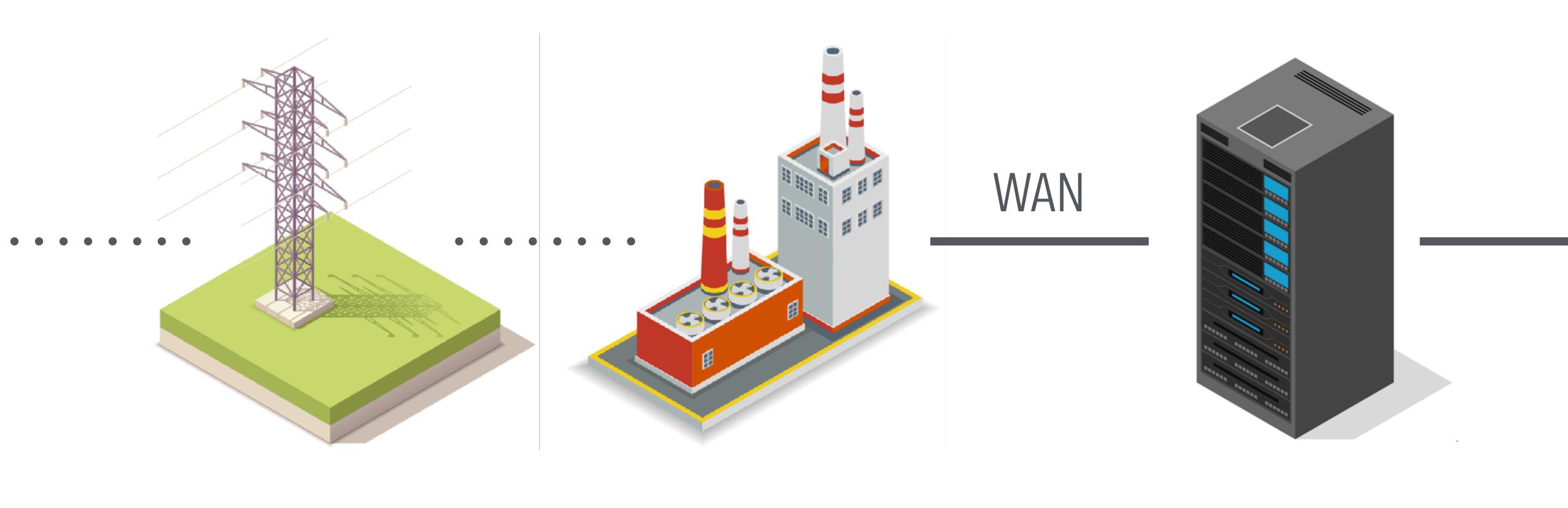
OUTLINE

- 1. Modern data center background
- 2. Large scale device failure studies
 - Memory: DRAM
 - Storage: SSDs
 - Network: Switches and WAN
- 3. Conclusion

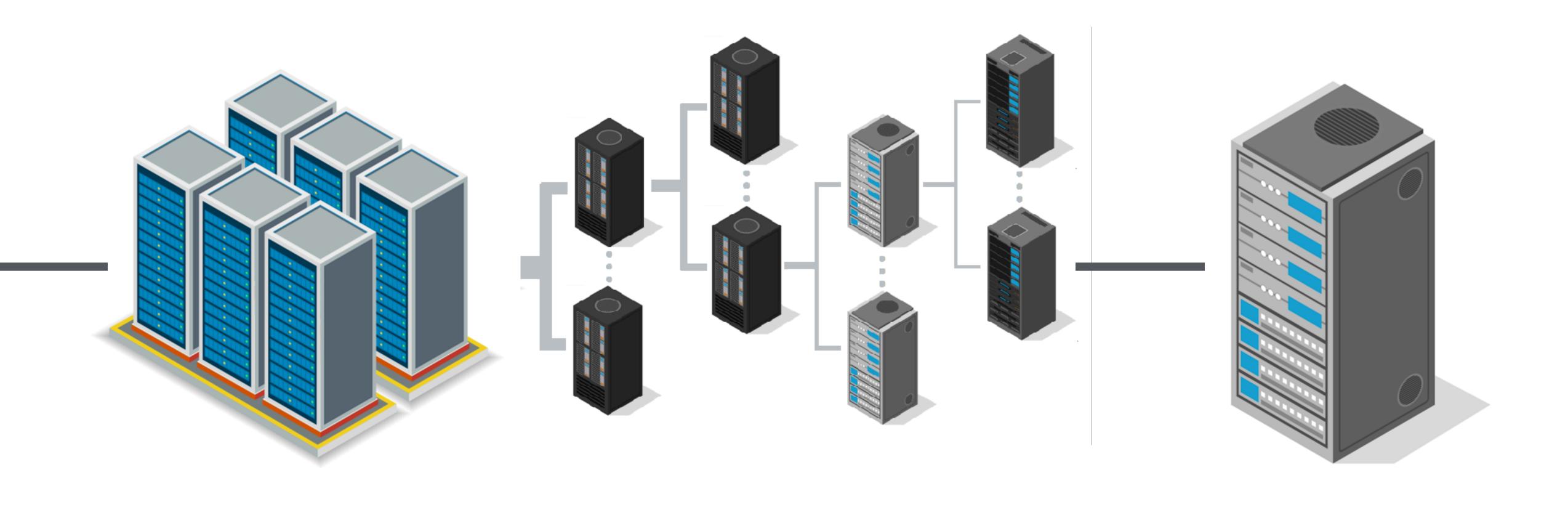








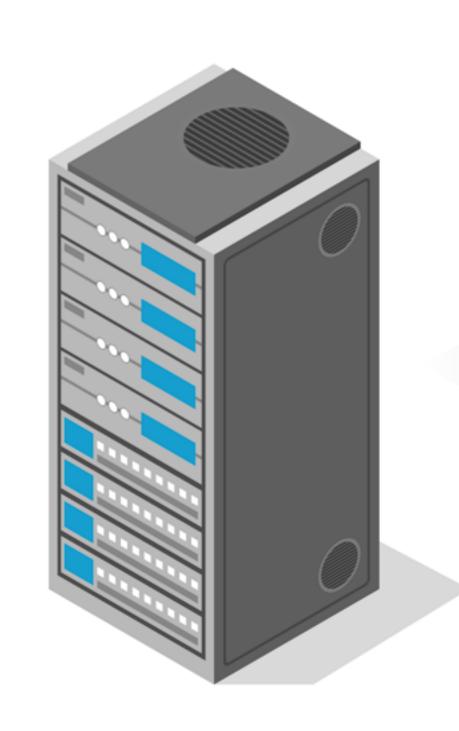
Internet ISP Edge Node



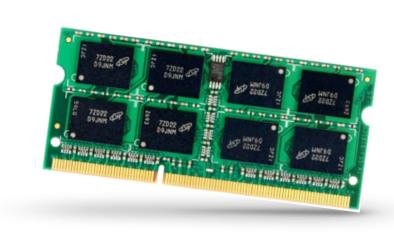
Core Switches

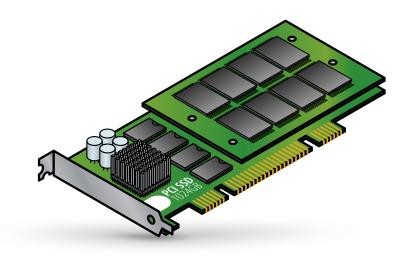
Data Center Fabric

Top of Rack Switch











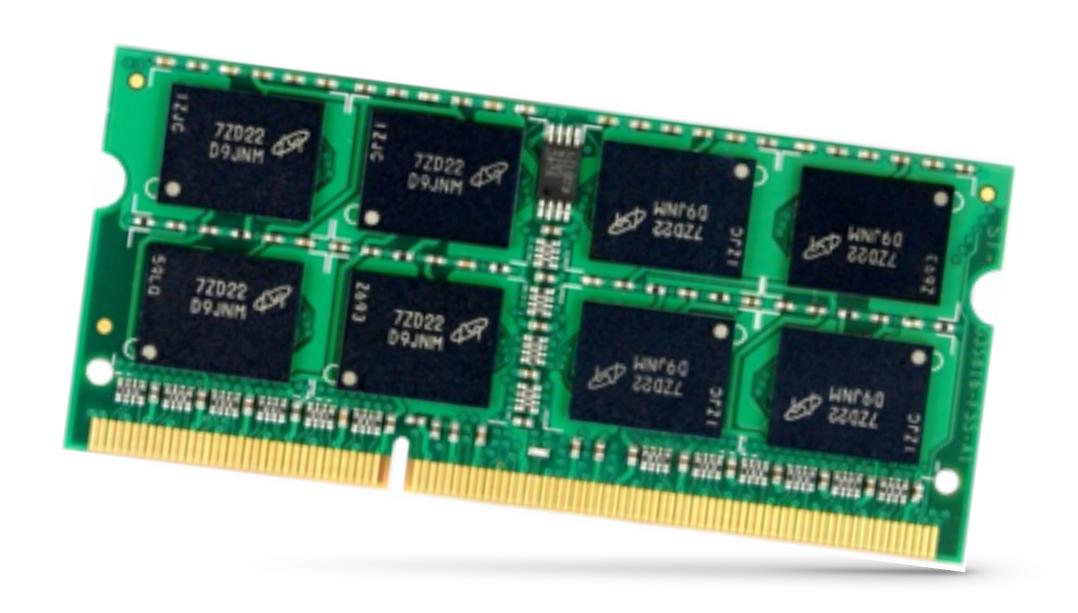
Devices

Server Rack

Server Sleds

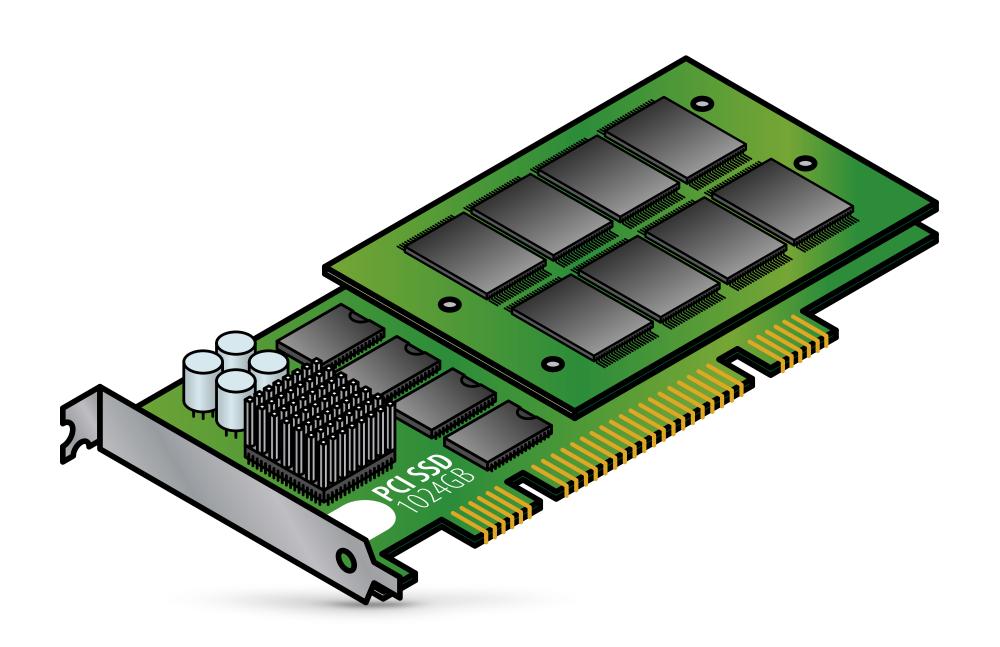
MEMORY

Dynamic Random Access Memory (DRAM)



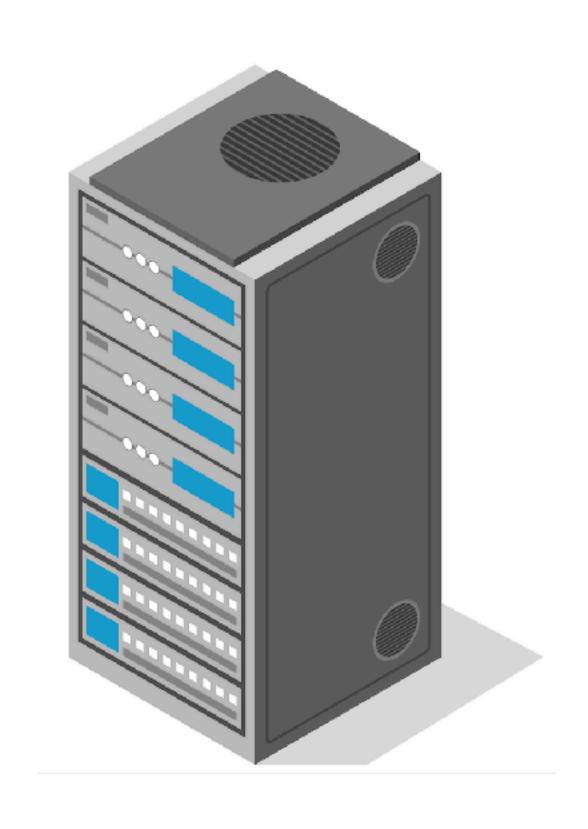
STORAGE

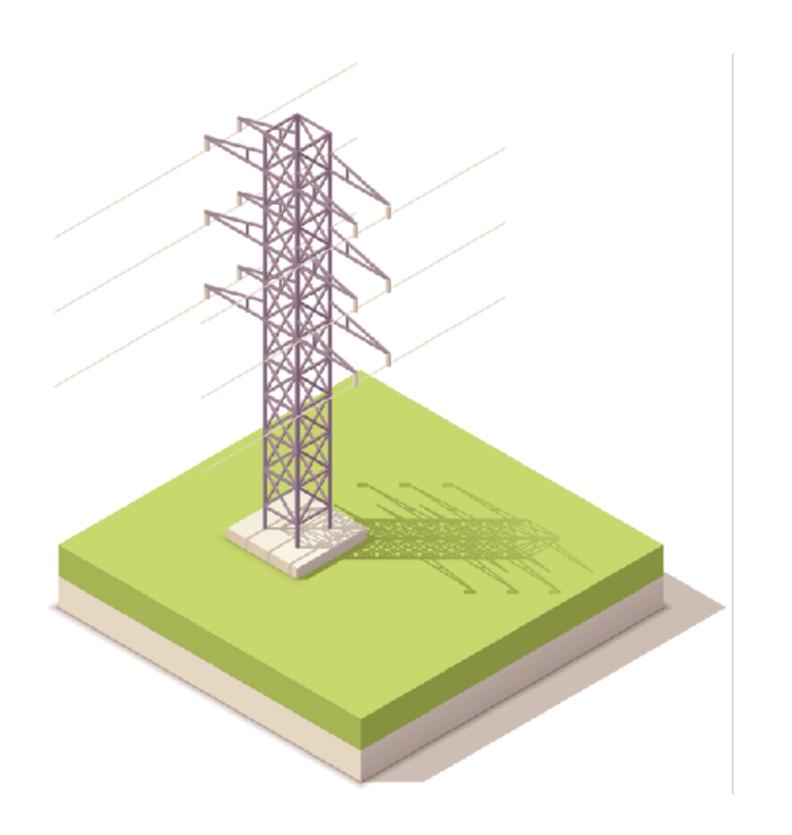
Solid State Drives (SSDs)



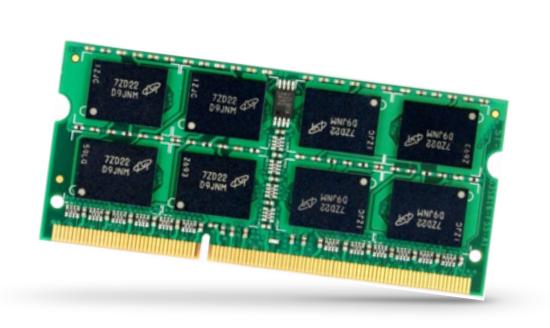
NETWORK

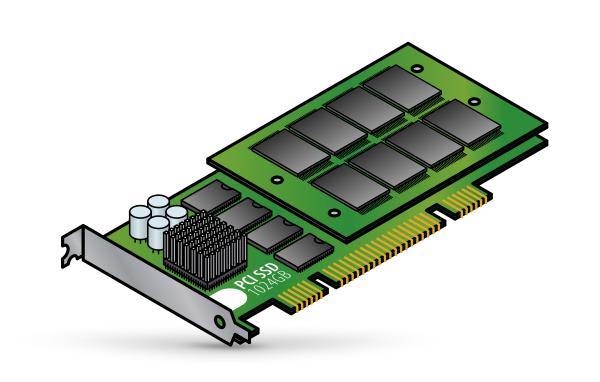
Switches and Wide Area Network (WAN) Backbone

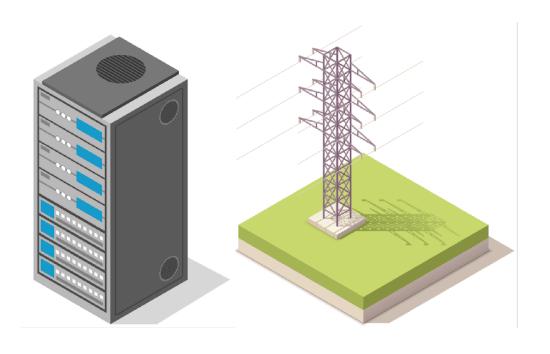




WHY DO DEVICES FAIL?







DRAM

- Retention
- Disturbance
- Endurance

SSDS

- Endurance
- Disturbance
 - Temperature

Networks

- BugsFaulty hardware
- Human error

DATA CENTER DIVERSITY

• Different system configurations

- Diverse workloads (Web, Database, Cache, Media)
- Diverse CPU/memory/storage requirements

Different device organizations

- Capacity, frequency, vendors, ...
- Across various stages of lifecycle

KEY OBSERVATIONS

- 1. Large scale data centers have diverse device populations
- 2. Large sample sizes mean we can build accurate models
- 3. We can observe infrequent failure types at large scale

RELIABILITY EVENTS

ERROR

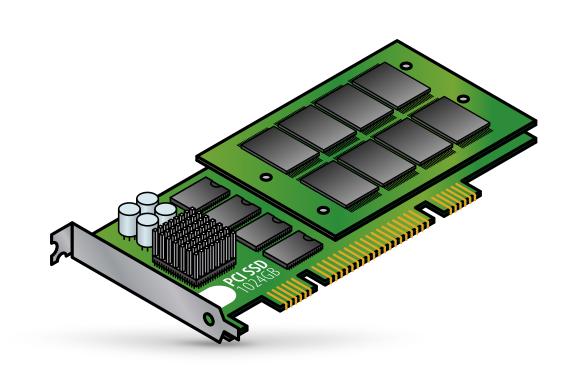
How failures manifest in software using a device

FAULT

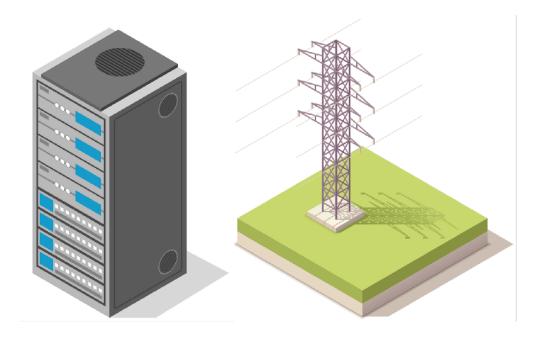
- The underlying reason why a device fails
- **Permanent:** the fault appears every time
- Transient: the appears only sometimes

LARGE SCALE STUDIES



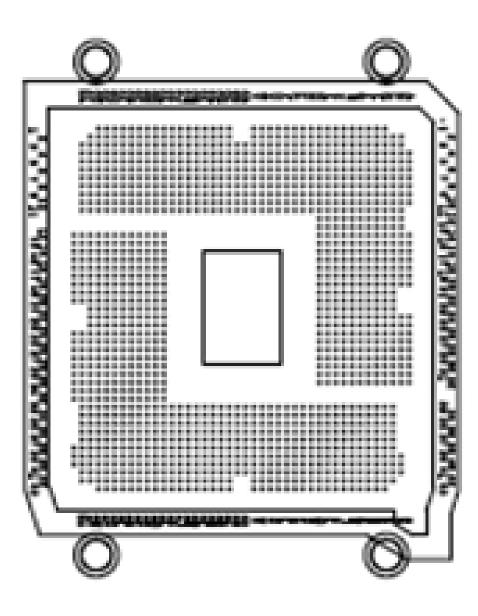


SSDs [SIGMETRICS '15]

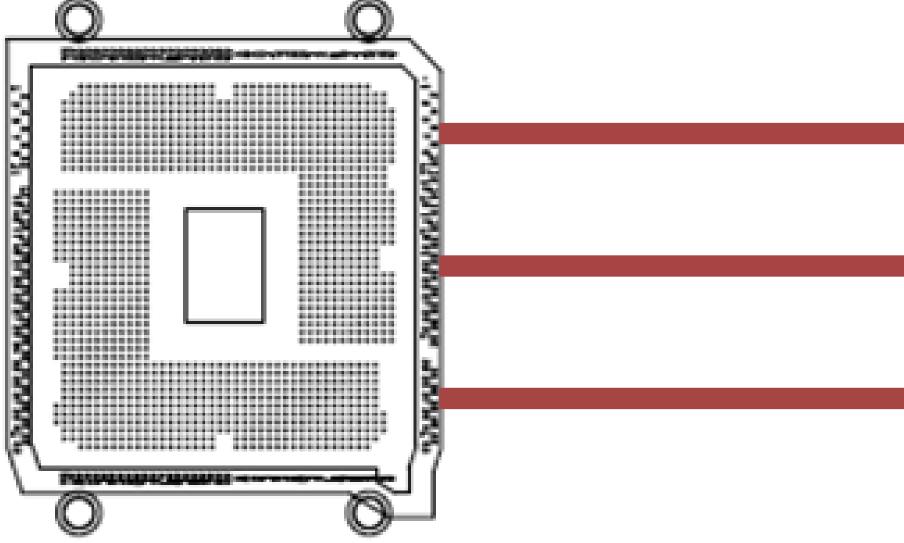


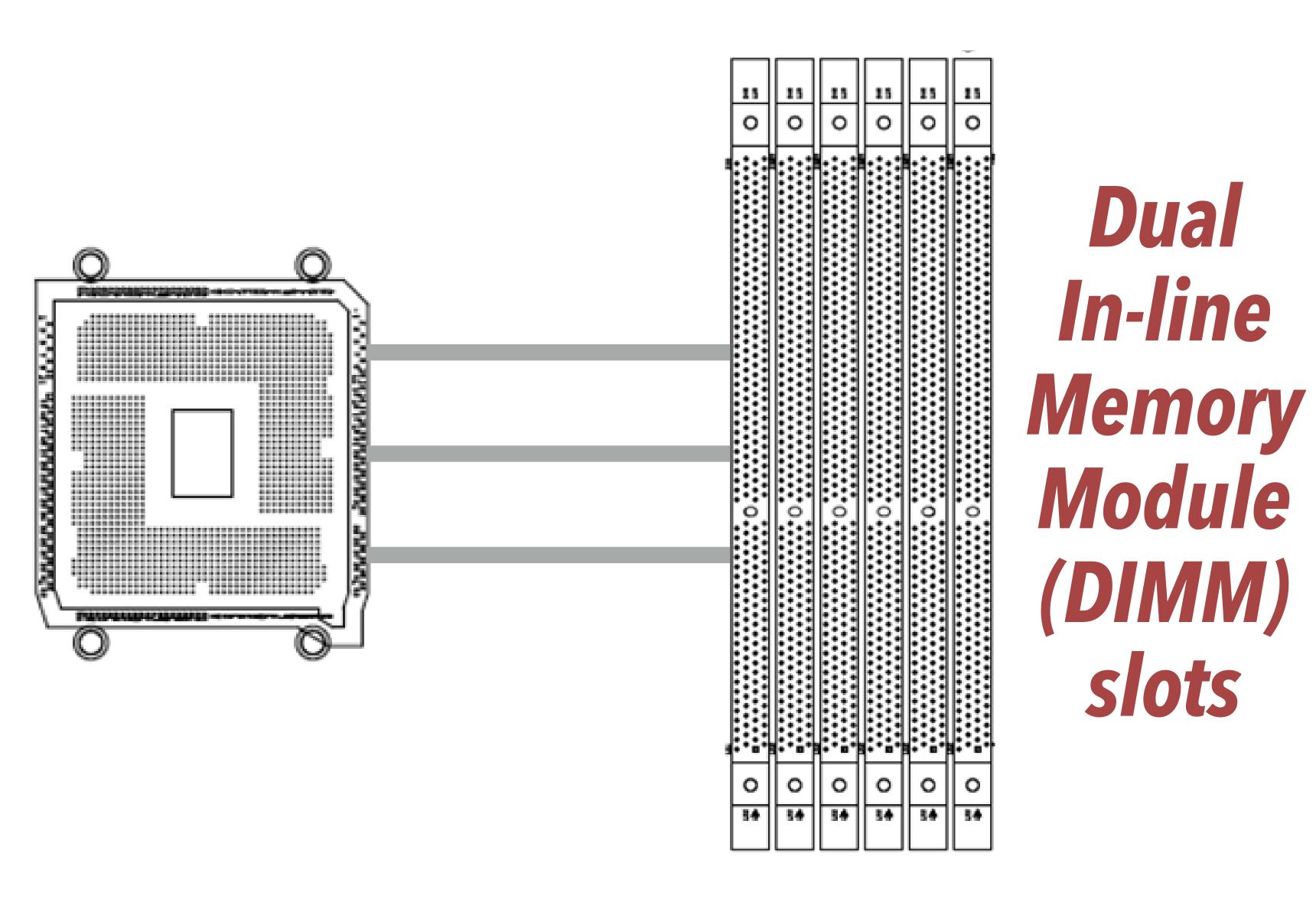
Networks
[IMC '18]

Socket



Memory channels

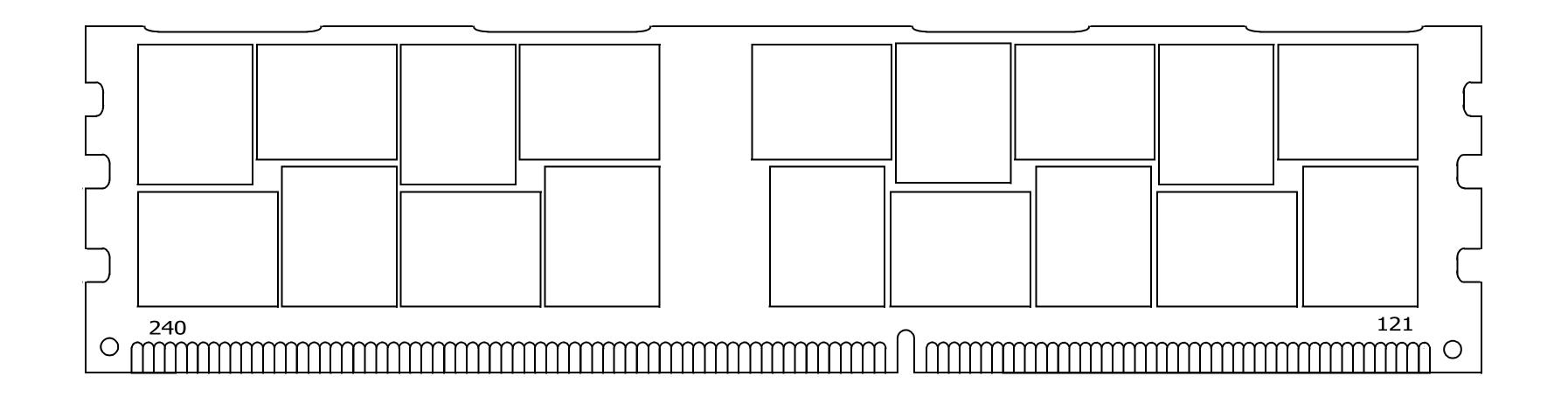


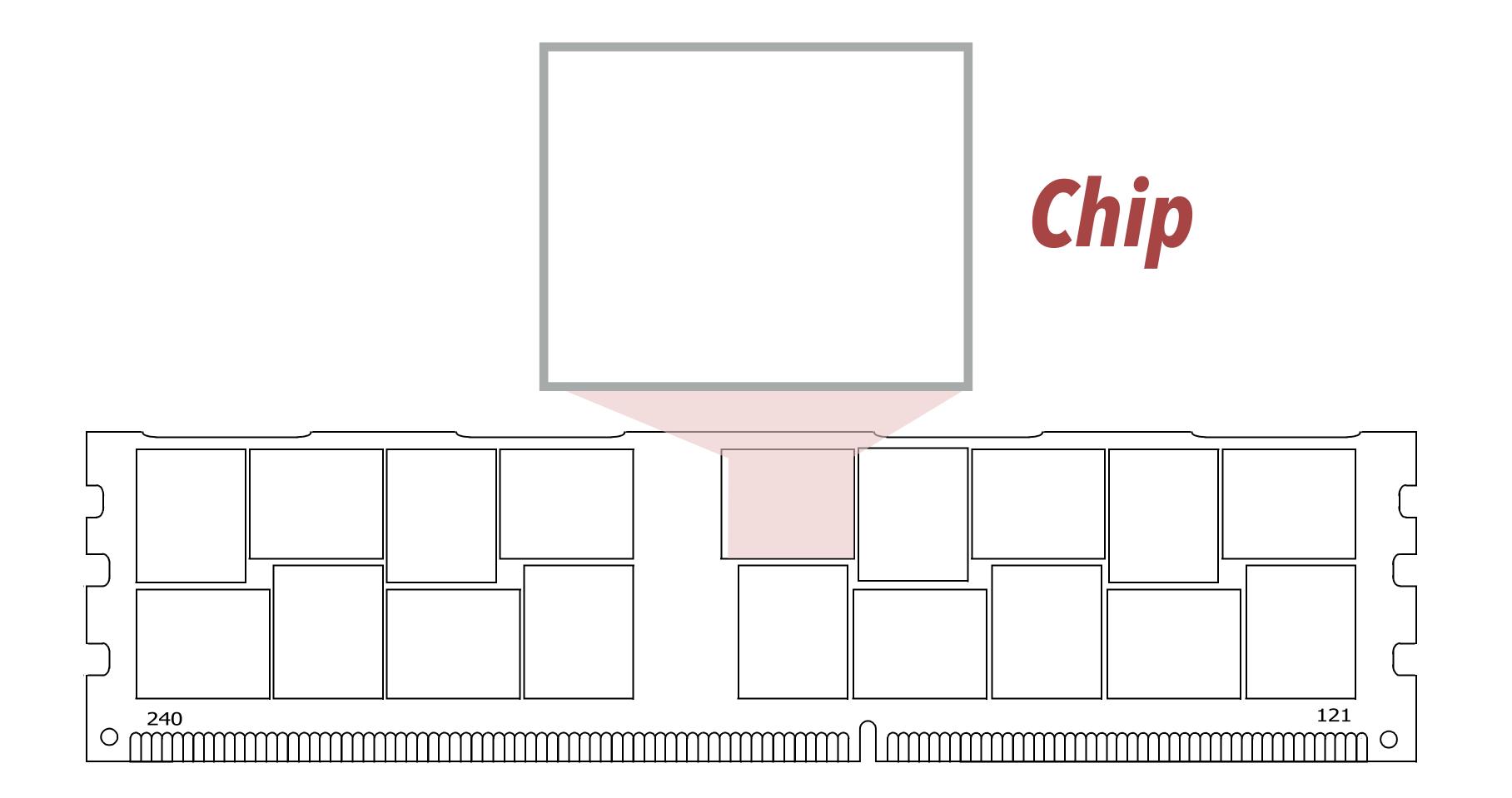


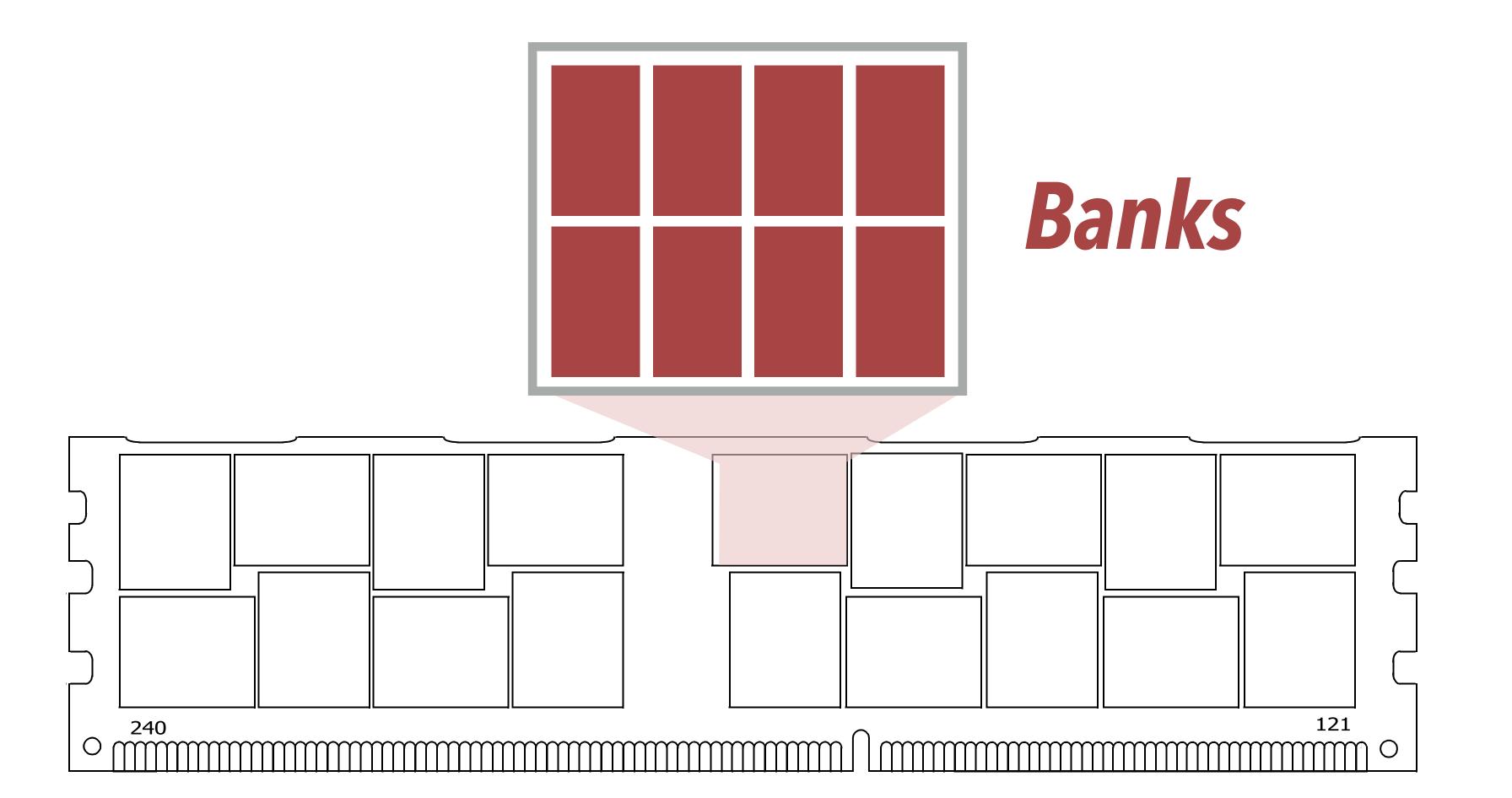
Dual

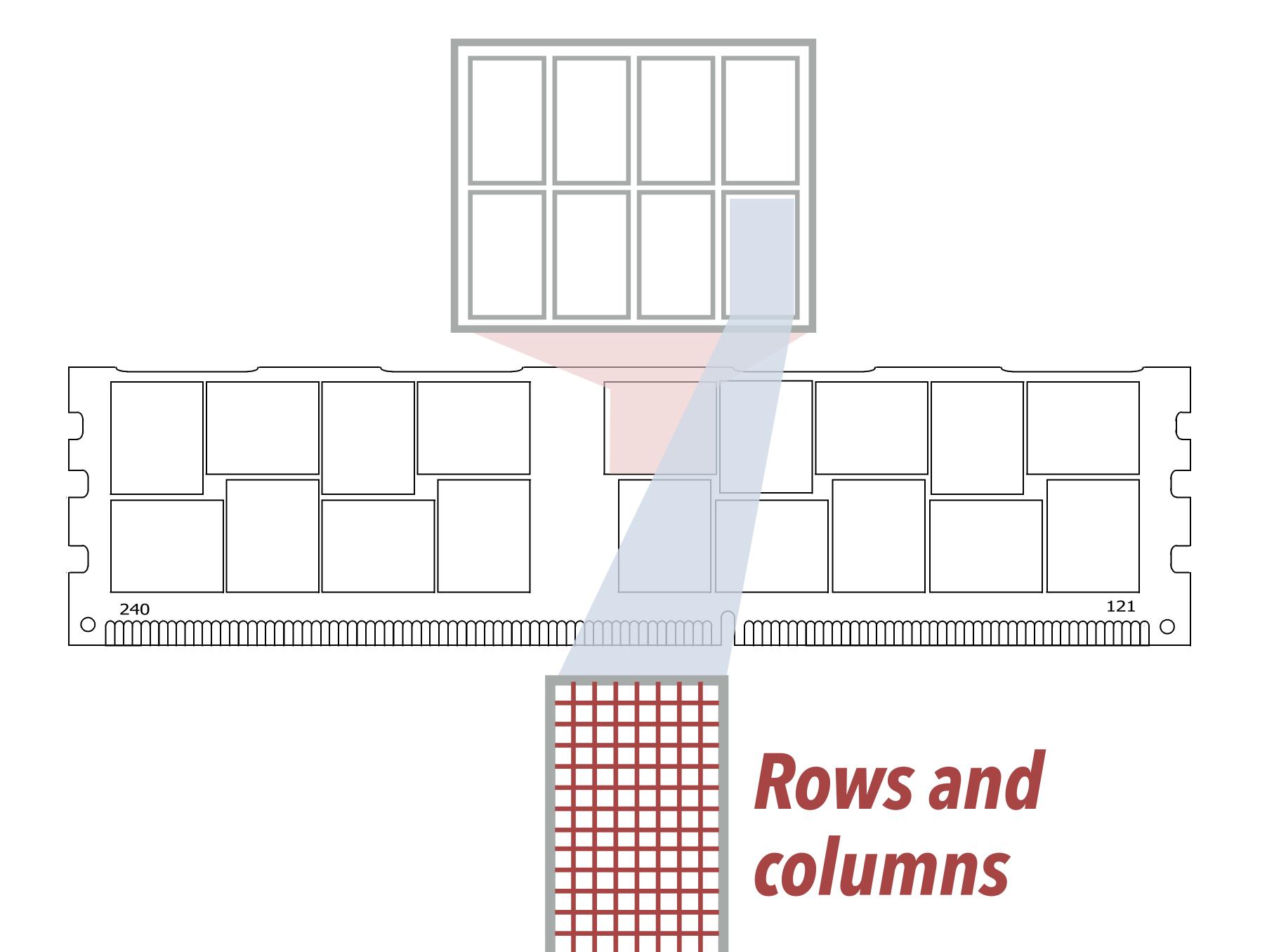
In-line

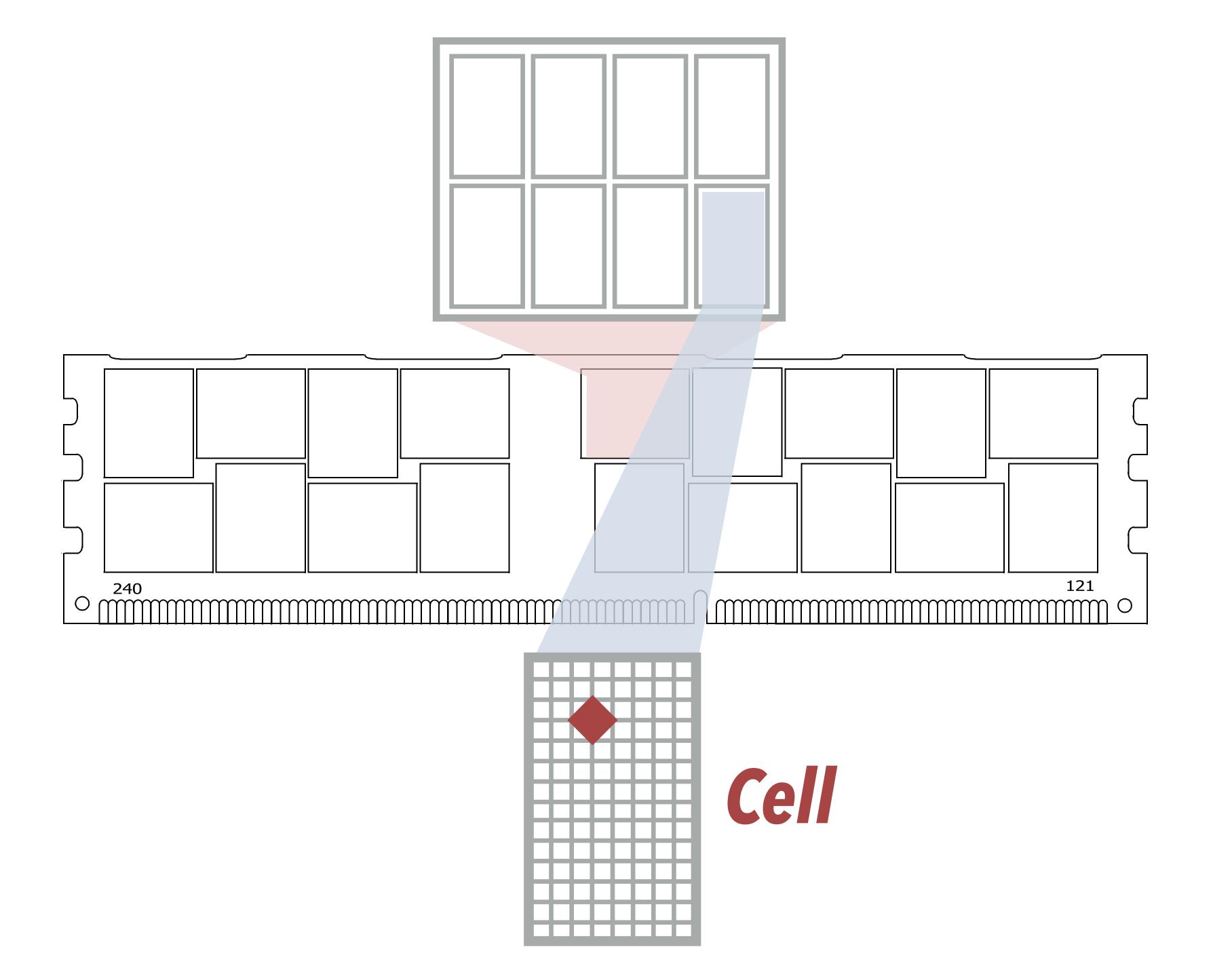
DIMM



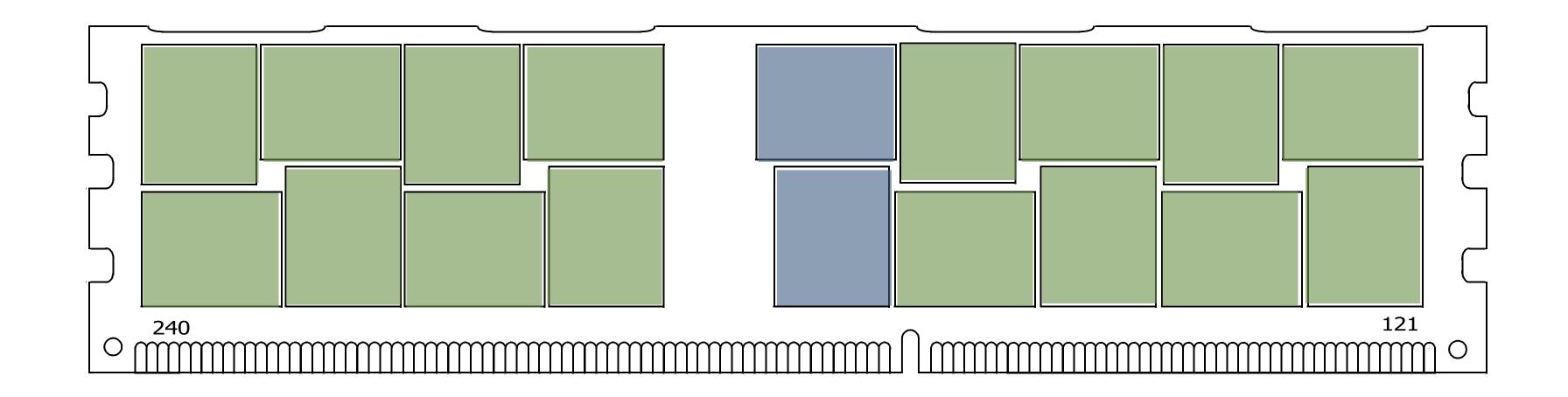








Memory data



Error Correcting Code (ECC) metadata

MEASURING DRAM ERRORS

- Measured every logged error
 - Across Facebook's fleet
 - For 14 months
 - Metadata associated with each error
- Parallelized Map-Reduce to process
- Used R for further analysis

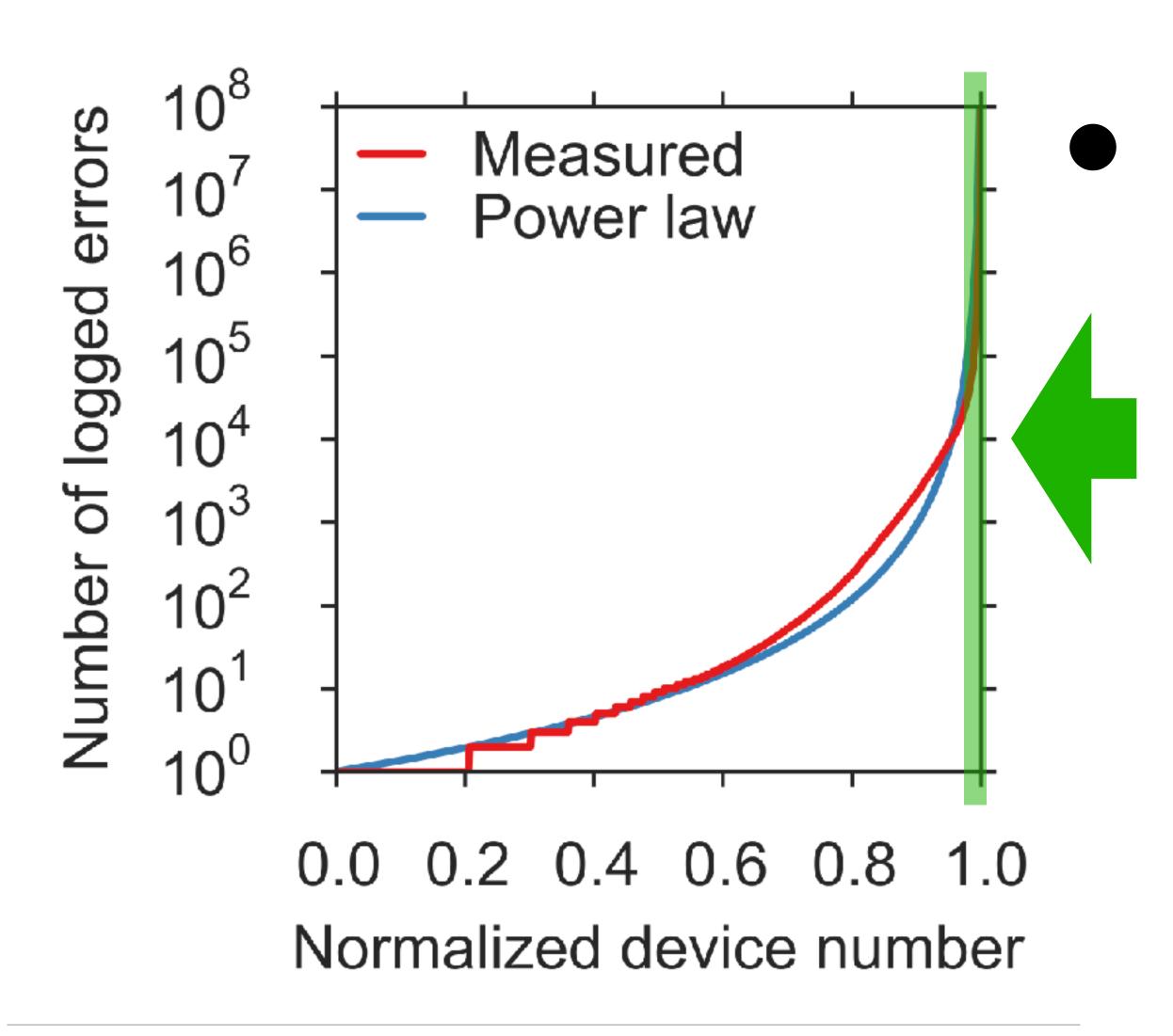
ANALYTICAL METHODOLOGY

- Measure server characteristics
 - Examined all servers with errors (error group)
 - Sampled servers without errors (control group)
- Bucket devices based on characteristics
- Measure relative failure rate
 - Of error group vs. control group
 - Within each bucket

KEY DRAM CONTRIBUTIONS

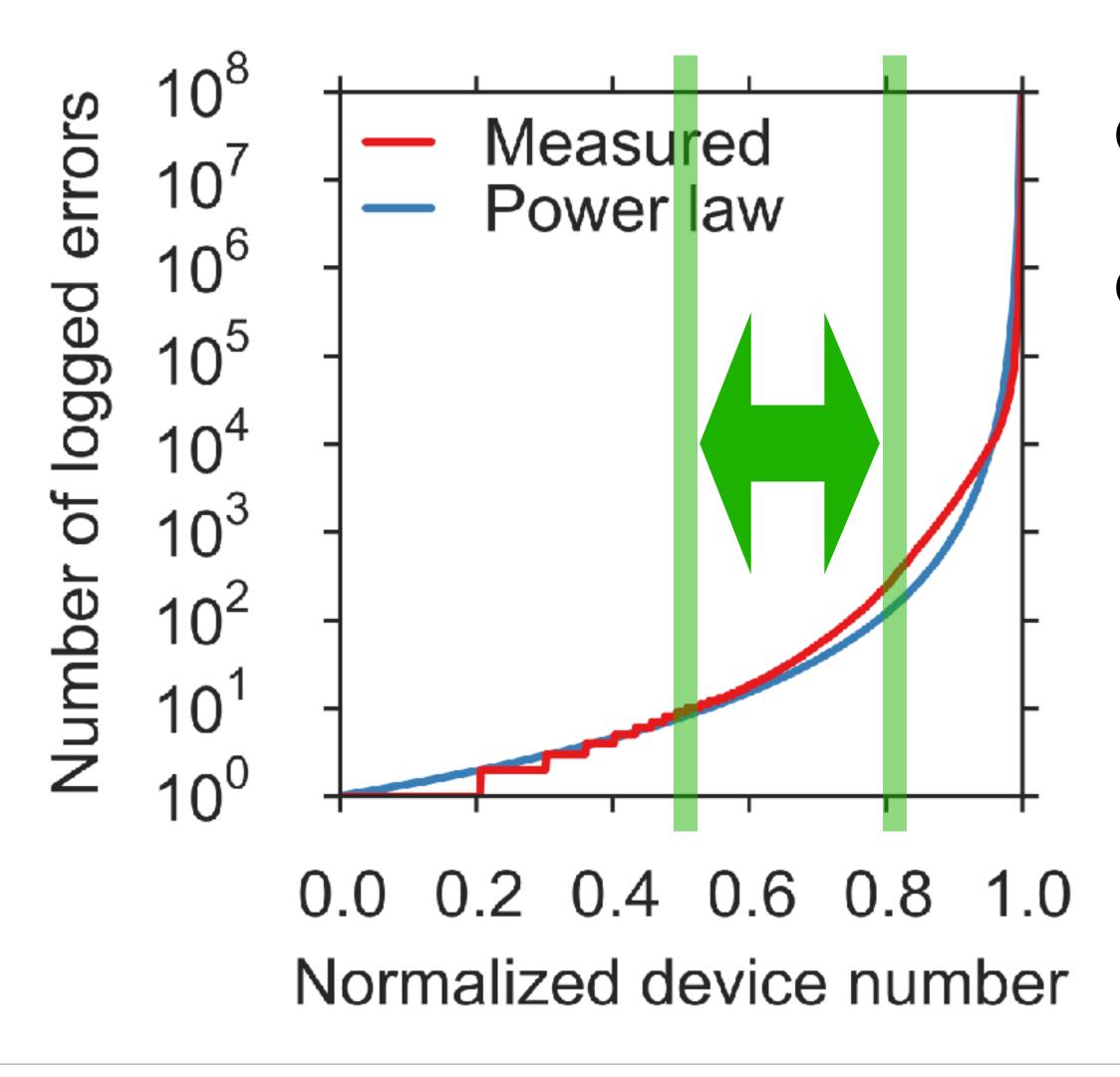
- Errors follow a power-law distribution
- Denial of service due to socket/channel
- Higher density = more failures
- DIMM architectural effects on reliability
- Workload influence on failures
- Model, page-offlining, page randomization

POWER-LAW DISTRIBUTION



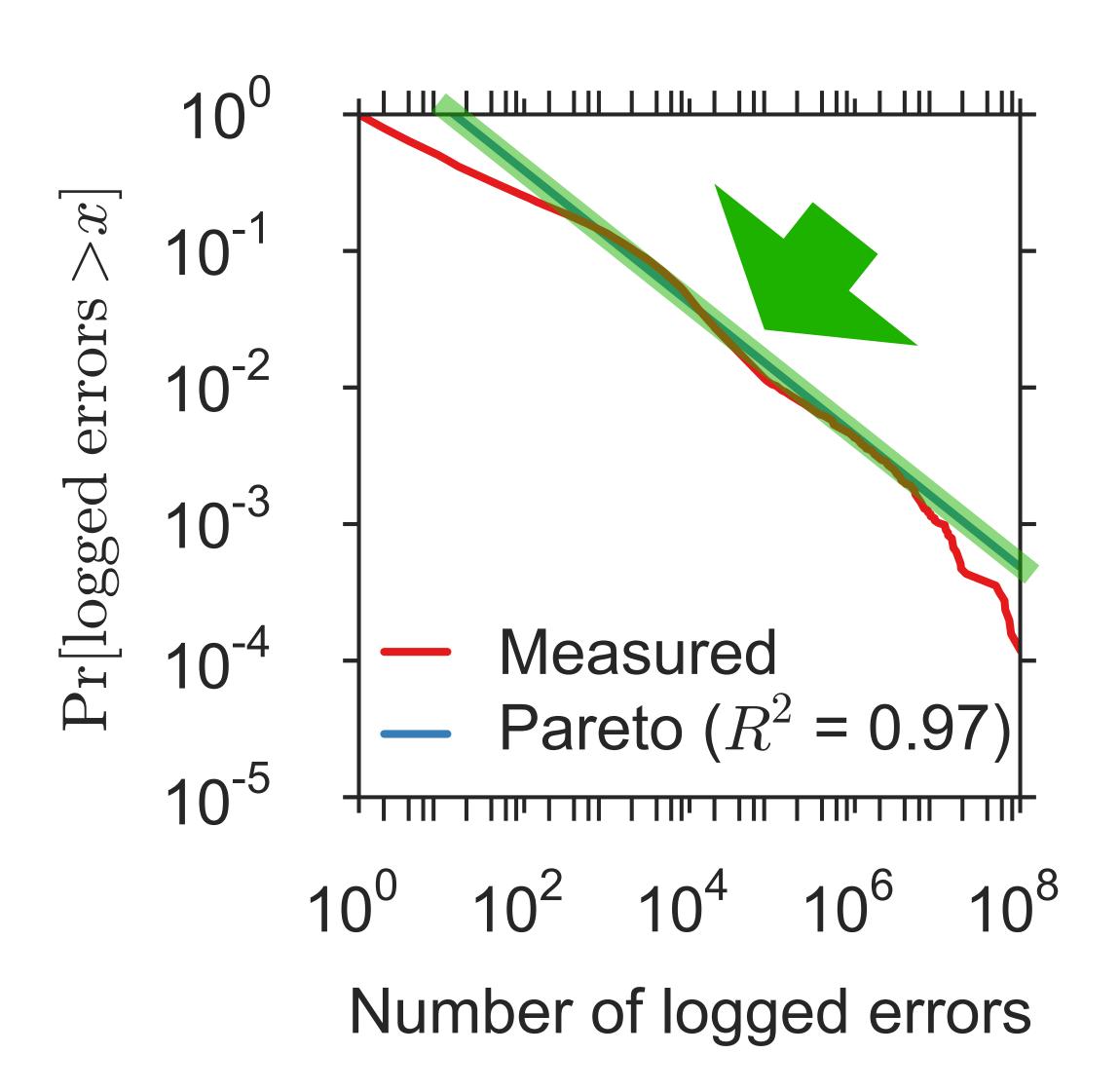
• 1% of servers = 97.8% errors

POWER-LAW DISTRIBUTION



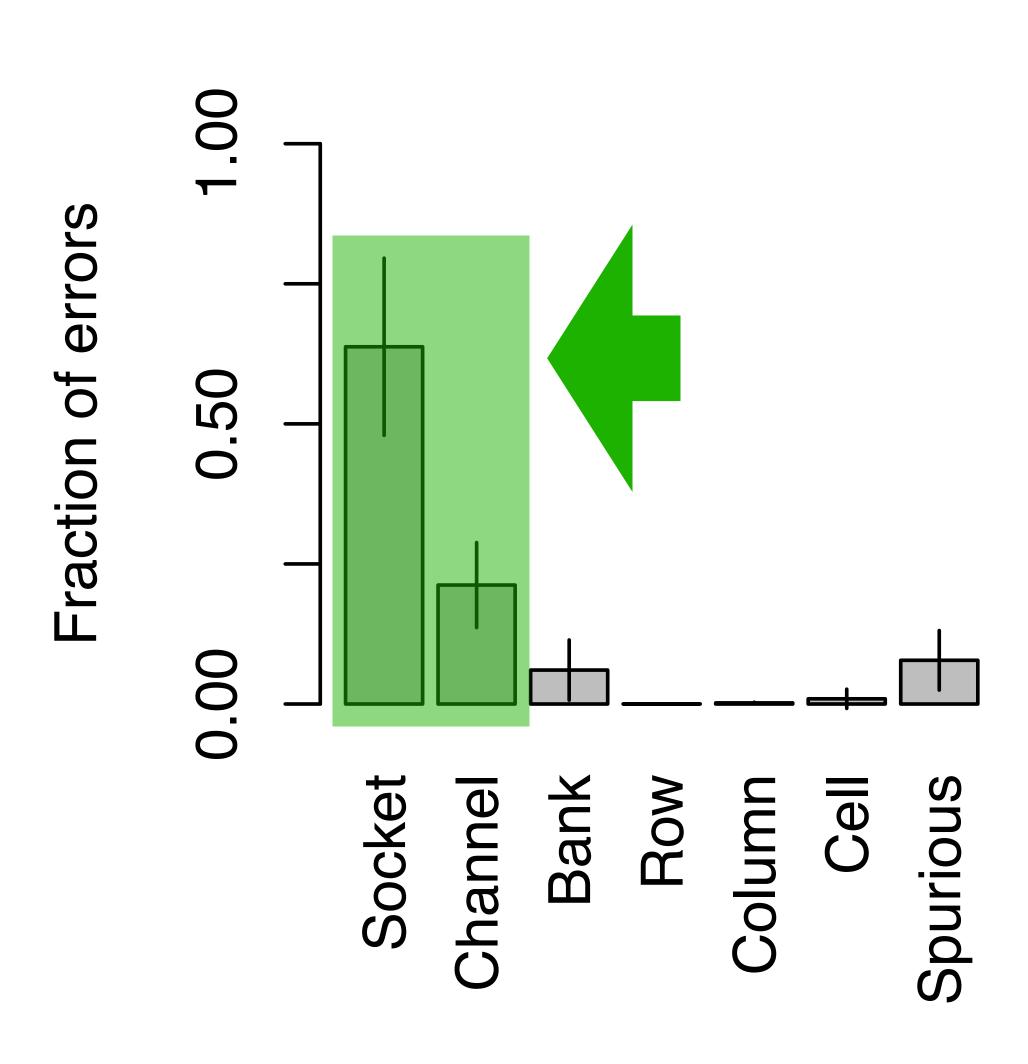
- 1% of servers = 97.8% errors
- Average is 55X median

POWER-LAW DISTRIBUTION



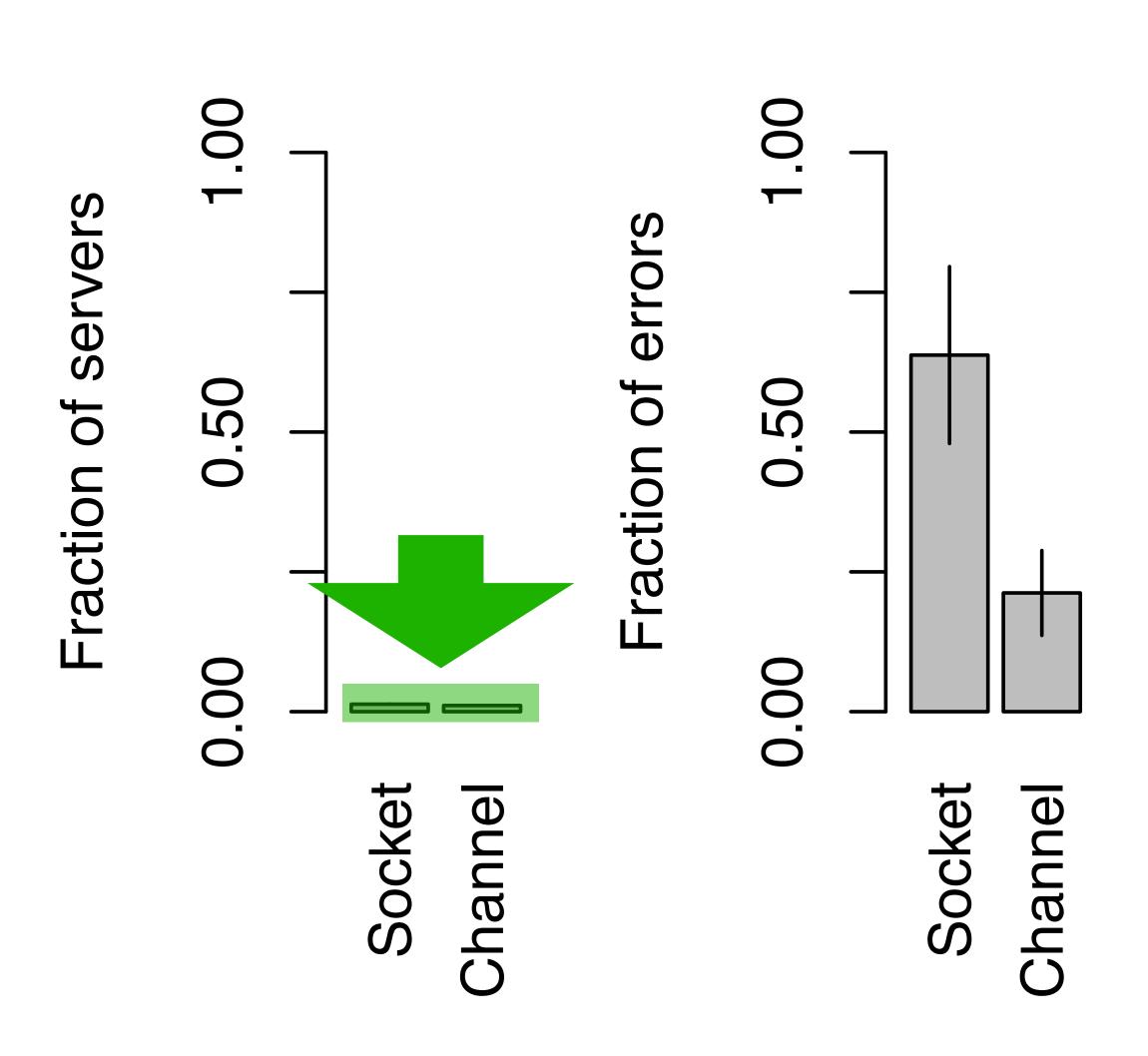
- 1% of servers = 97.8% errors
- Average is 55X median
- Pareto distribution fits
 - Devices without errors
 tend to stay without errors

SOCKET/CHANNEL ERRORS



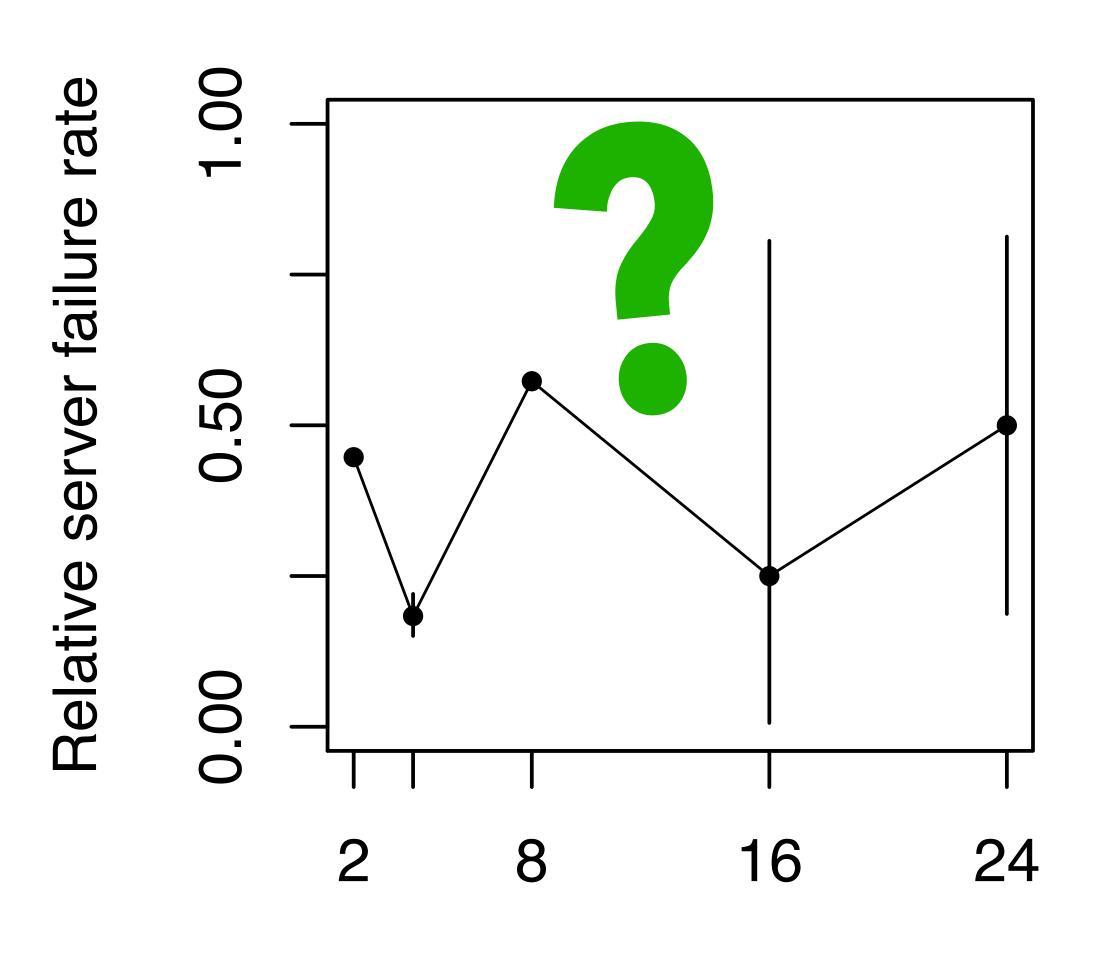
Contribute majority of errors

SOCKET/CHANNEL ERRORS



- Contribute majority of errors
- Concentrated on a few hosts
- Symptoms ≈ server DoS

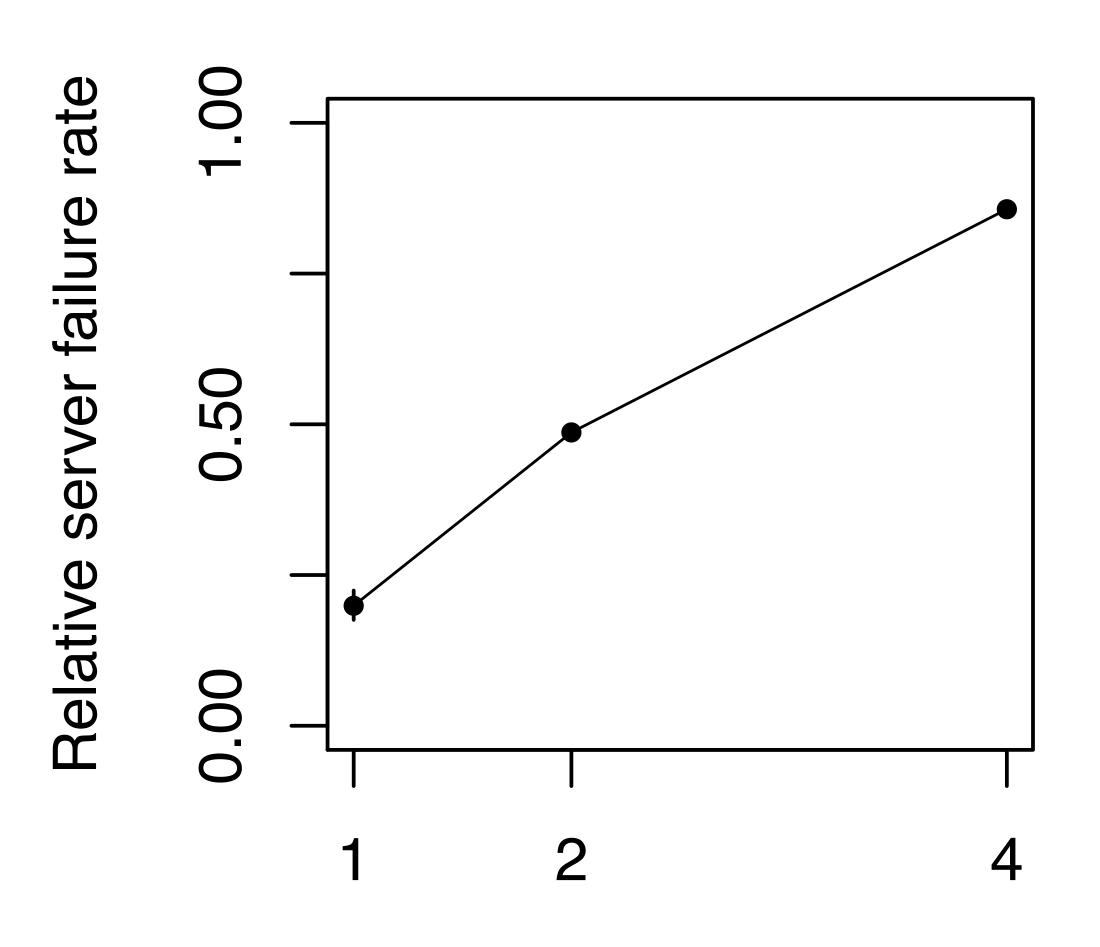
HIGHER DENSITY TRENDS



Capacity, NO! Density, YES!

DIMM capacity (GB)

HIGHER DENSITY TRENDS

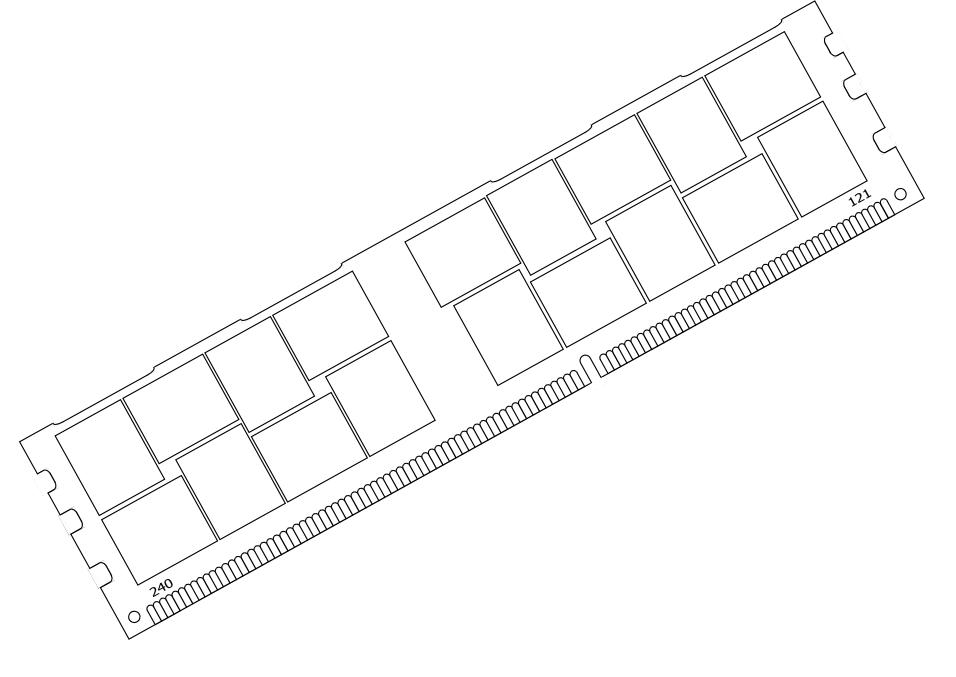


- Capacity, NO! Density, YES!
- Higher density, more failure
 - Due to smaller feature sizes

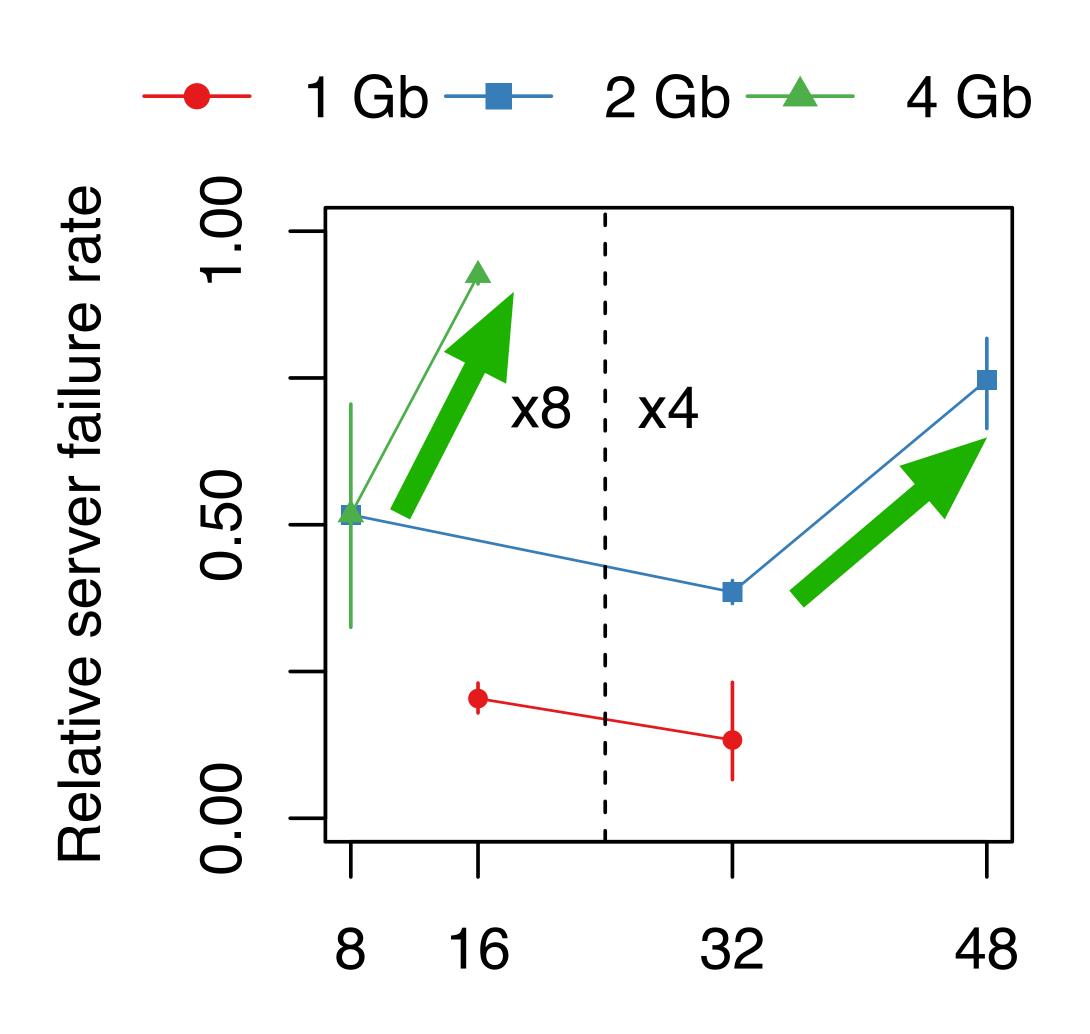
Chip density (Gb)

DIMM architecture

- Chips per DIMM, transfer width
 - 8 to 48 chips
 - x4, x8 = 4 or 8 bits per cycle
 - Electrical implications



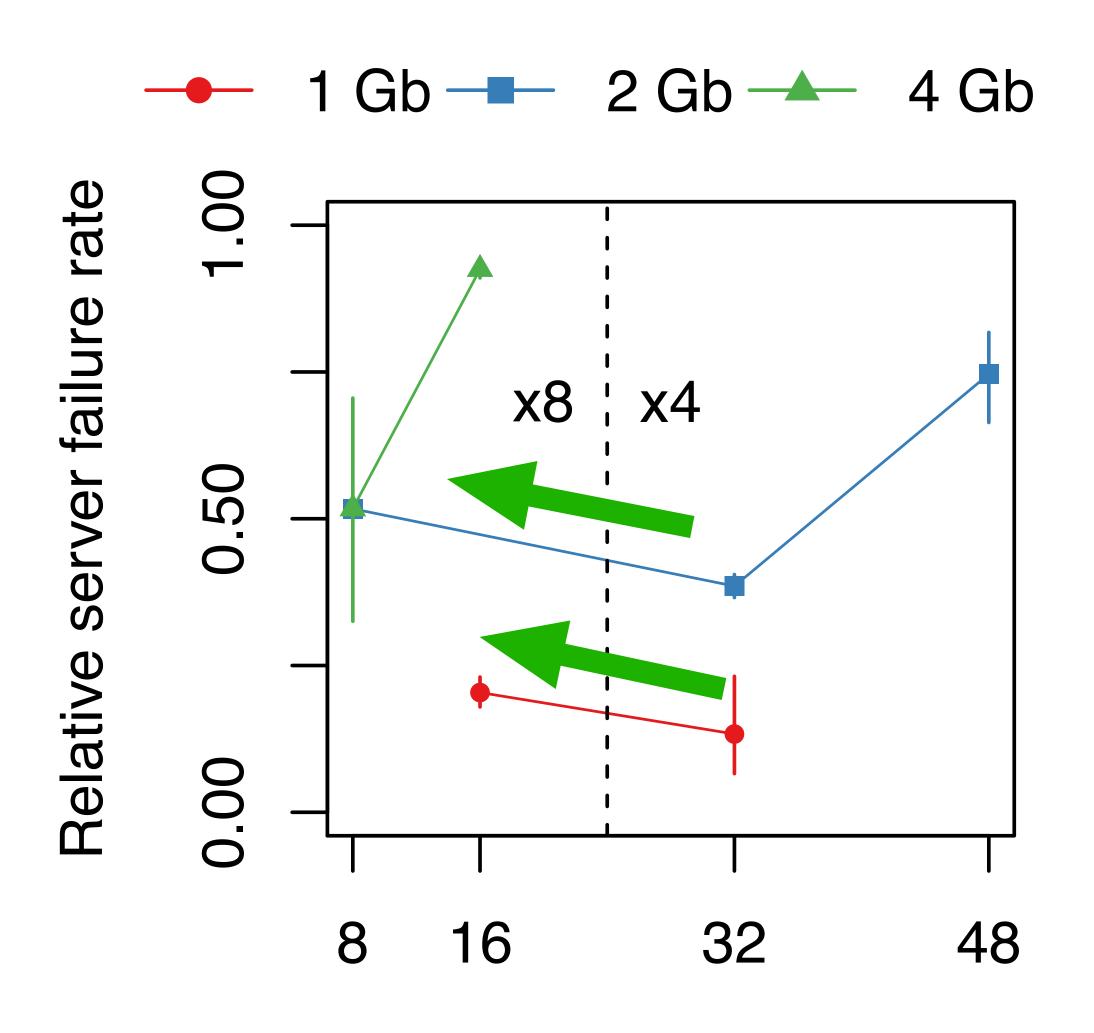
ARCHITECTURAL EFFECTS



- For the <u>same transfer width</u>:
- More chips = more failures

Data chips per DIMM

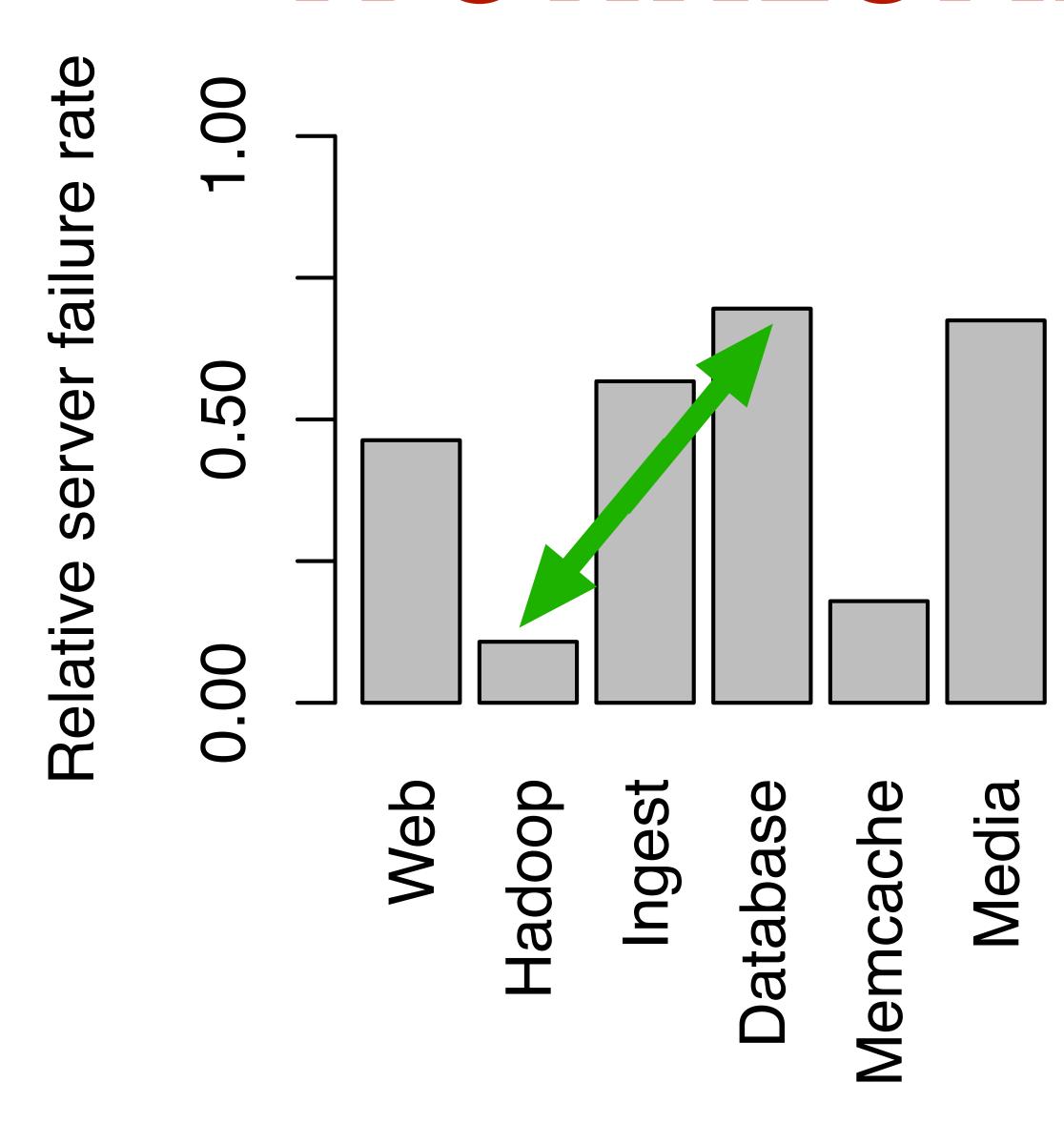
ARCHITECTURAL EFFECTS



Data chips per DIMM

- For the <u>same transfer width</u>:
- More chips = more failures
- For different transfer widths:
- More bits = more failures
 - Likely related to electrical noise

WORKLOAD INFLUENCE

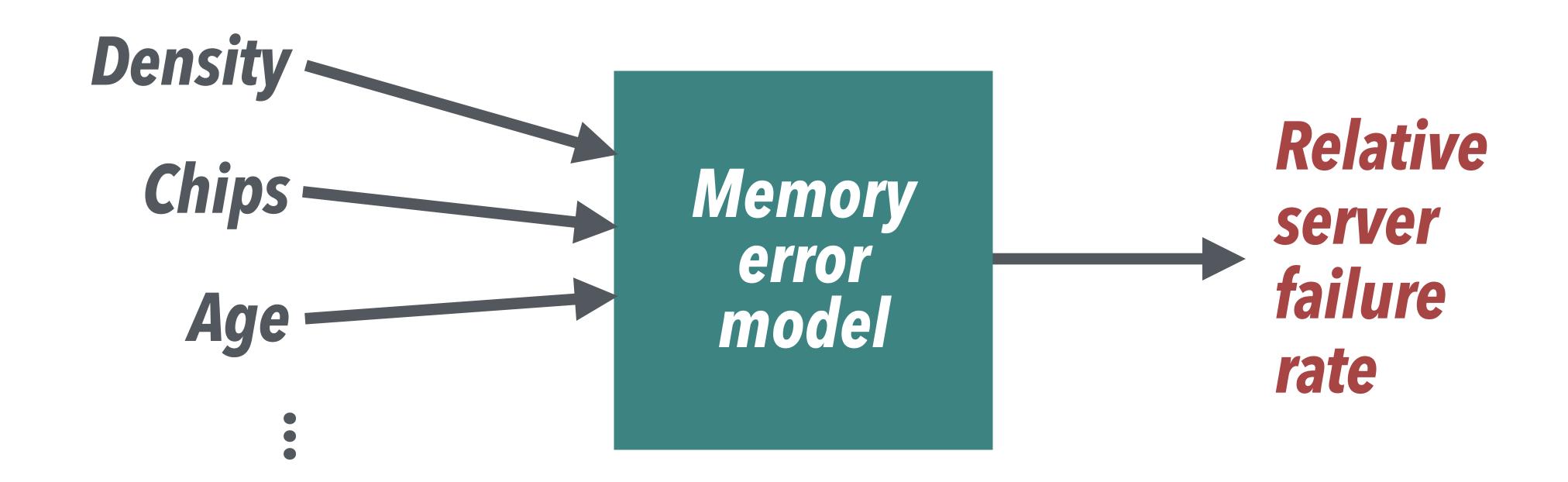


- No consistent trends across
 CPU and memory utilization
- But workload varies by ~6X
 - May be due to distribution for read/write behavior

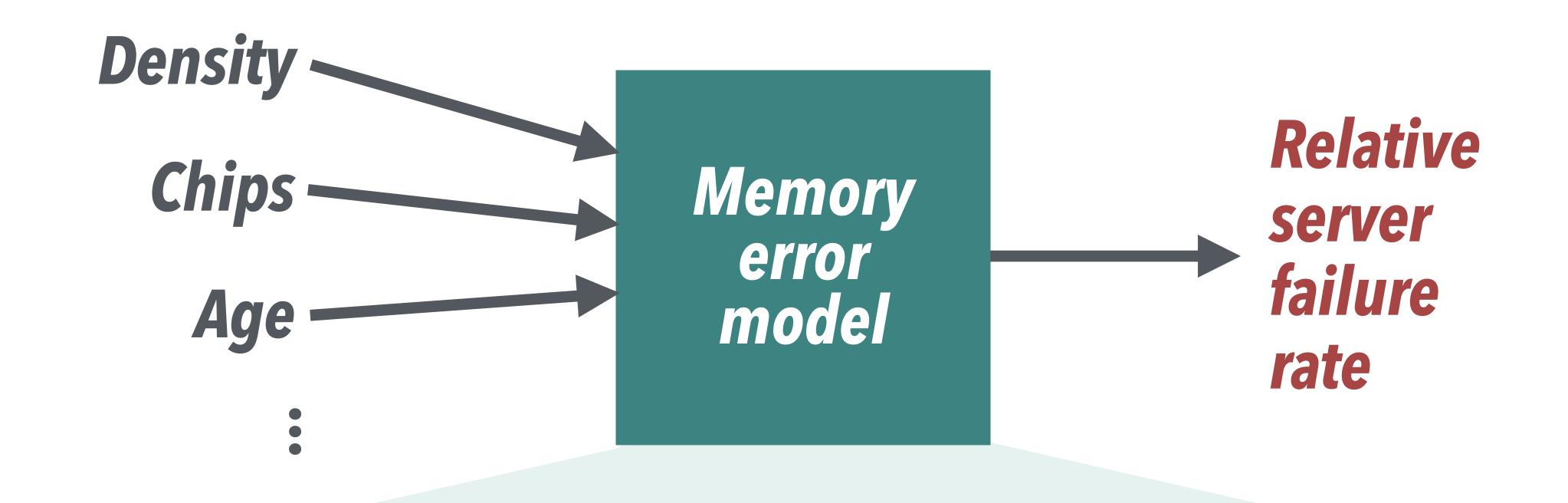
MODELING MEMORY FAILURES

- Use statistical regression model
 - Compare control group versus error group
 - Logistic (linear) regression in R
 - Trained using data from analysis
- Enable exploratory analysis

MODELING MEMORY FAILURES



MODELING MEMORY FAILURES



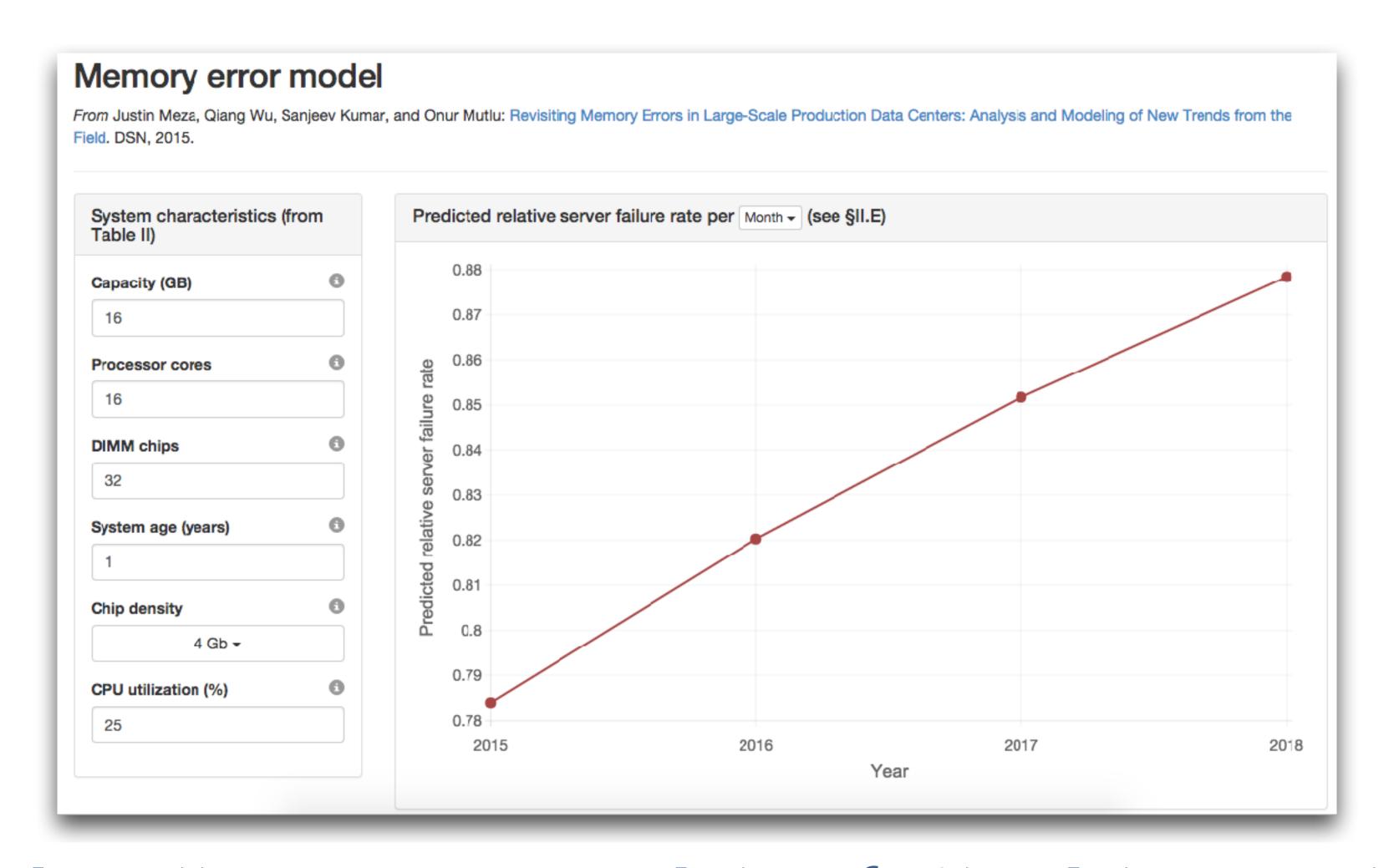
$$\ln \left[\mathcal{F}/(1-\mathcal{F}) \right] = \beta_{Intercept} + \left(Capacity \cdot \beta_{Capacity} \right) + \left(Density2Gb \cdot \beta_{Density2Gb} \right) + \left(Density4Gb \cdot \beta_{Density4Gb} \right) + \left(Chips \cdot \beta_{Chips} \right) + \left(CPU\% \cdot \beta_{CPU\%} \right) + \left(Age \cdot \beta_{Age} \right) + \left(CPUs \cdot \beta_{CPUs} \right)$$

EXPLORATORY ANALYSIS

Factor	Low-end	High-end (HE)	
Capacity	4 GB	16 GB	
Density2Gb	1	0	
Density4Gb	0	1	
Chips	16	32	Input
CPU%	50%	25%	
Age	1	1	
CPUs	8	16	
Predicted relative failure rate	0.12	0.78	Outpu

6.5X difference in yearly failures

TOOLAVAILABLE ONLINE

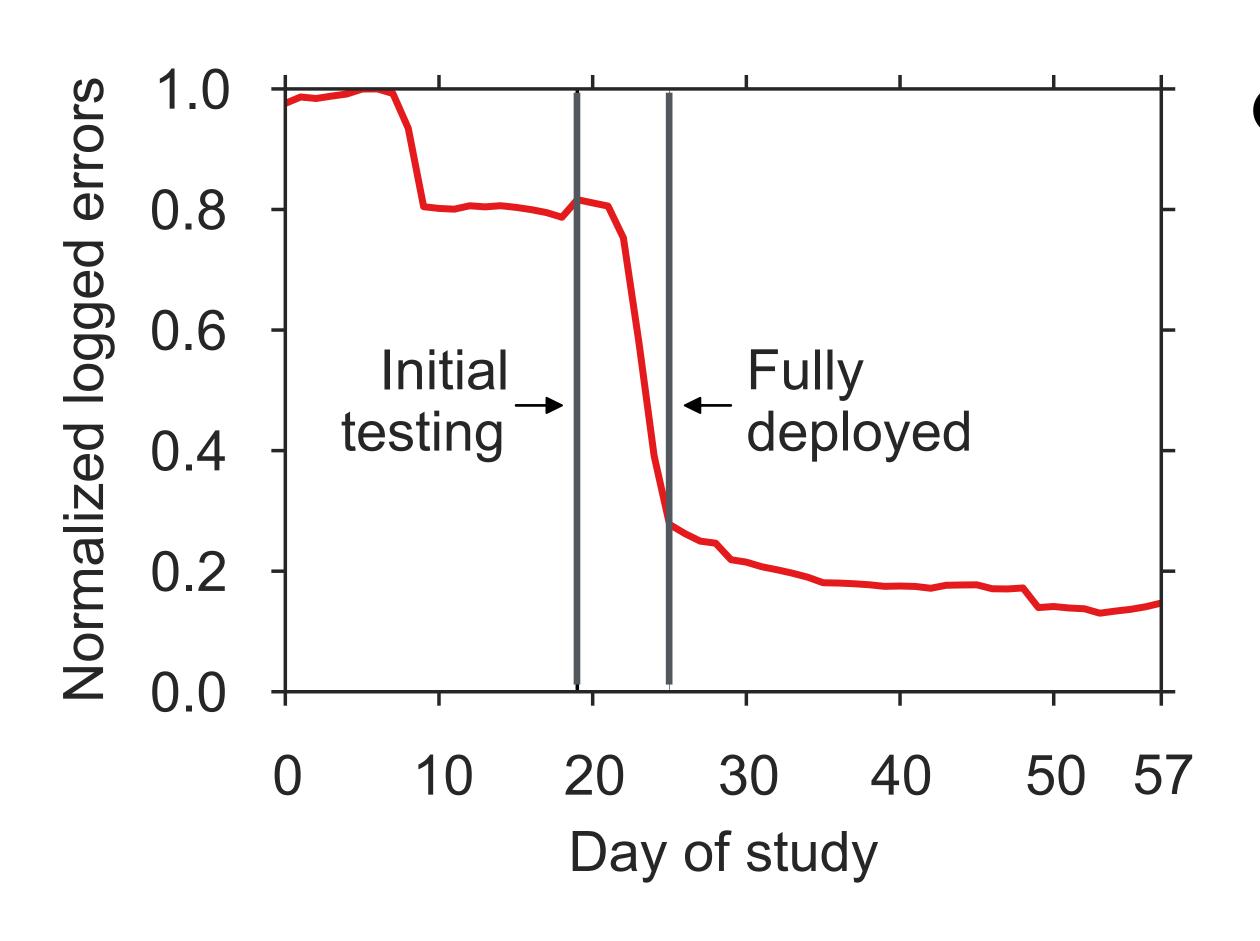


http://www.ece.cmu.edu/~safari/tools/memerr/

Page offlining

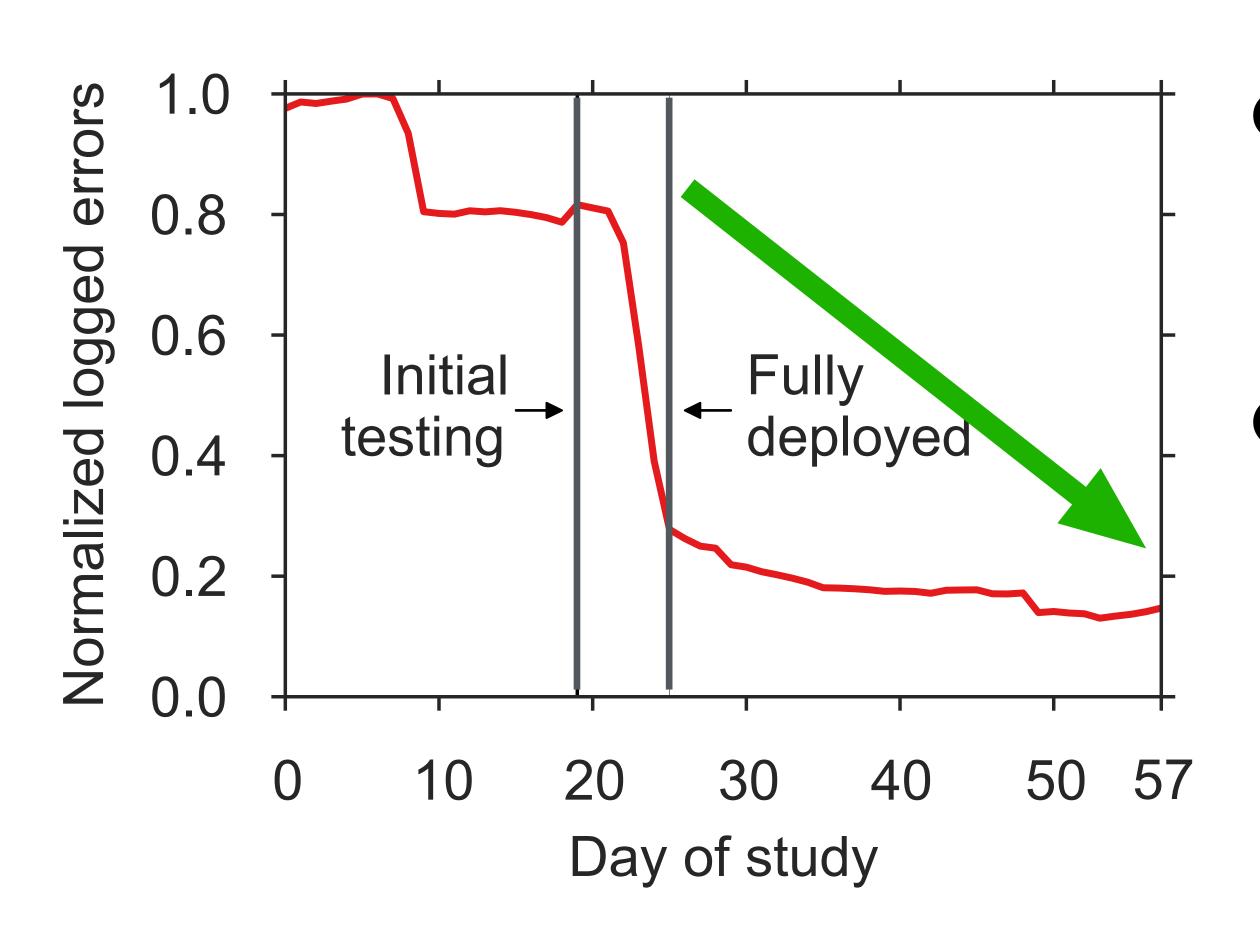
- System-level technique to reduce errors
- When a page has an error, take the page offline
 - Copy its contents to a new location
 - *Poison* the page to prevent allocation

PAGE OFFLINING AT SCALE



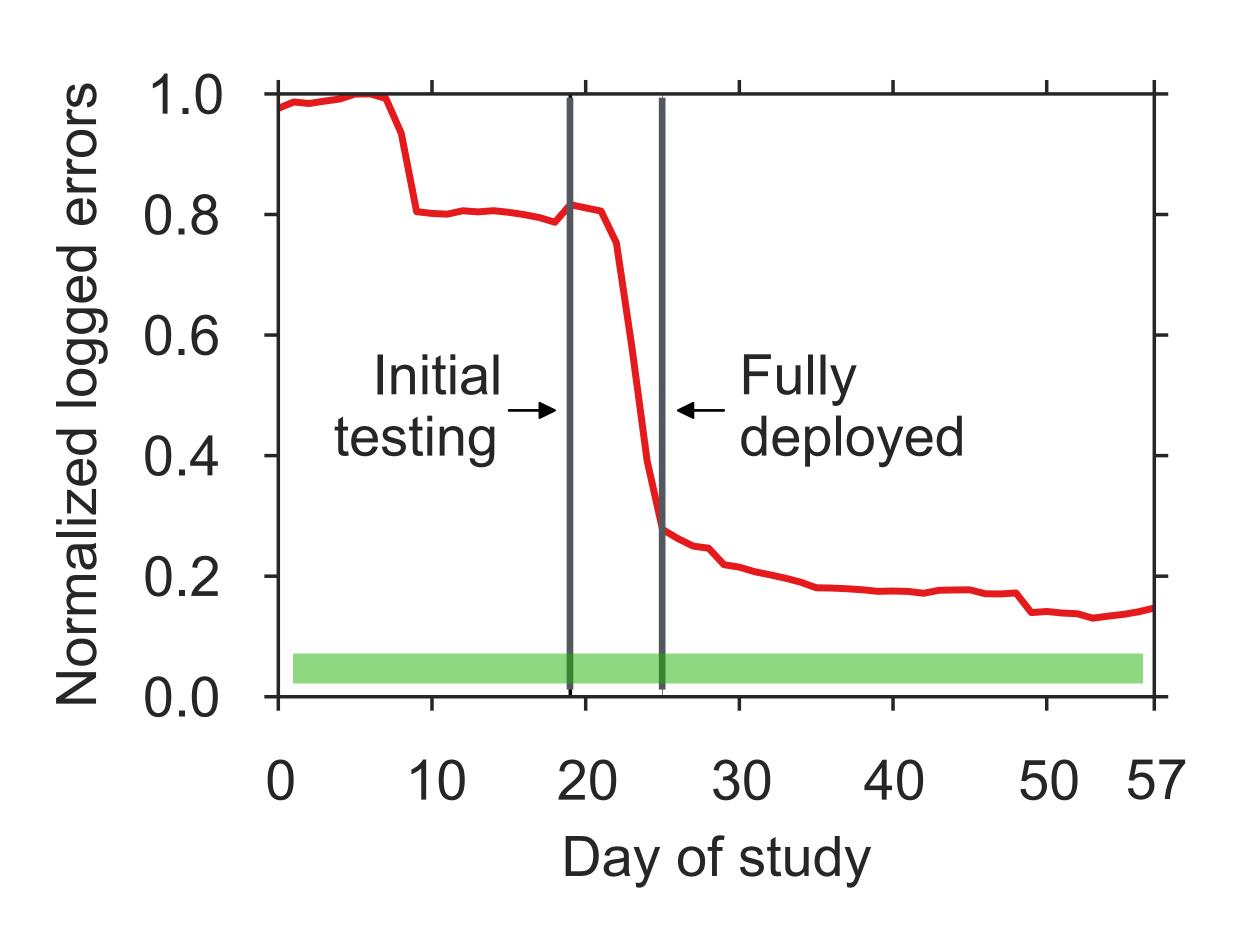
- First study at large scale
 - Cluster of 12,276 servers

PAGE OFFLINING AT SCALE



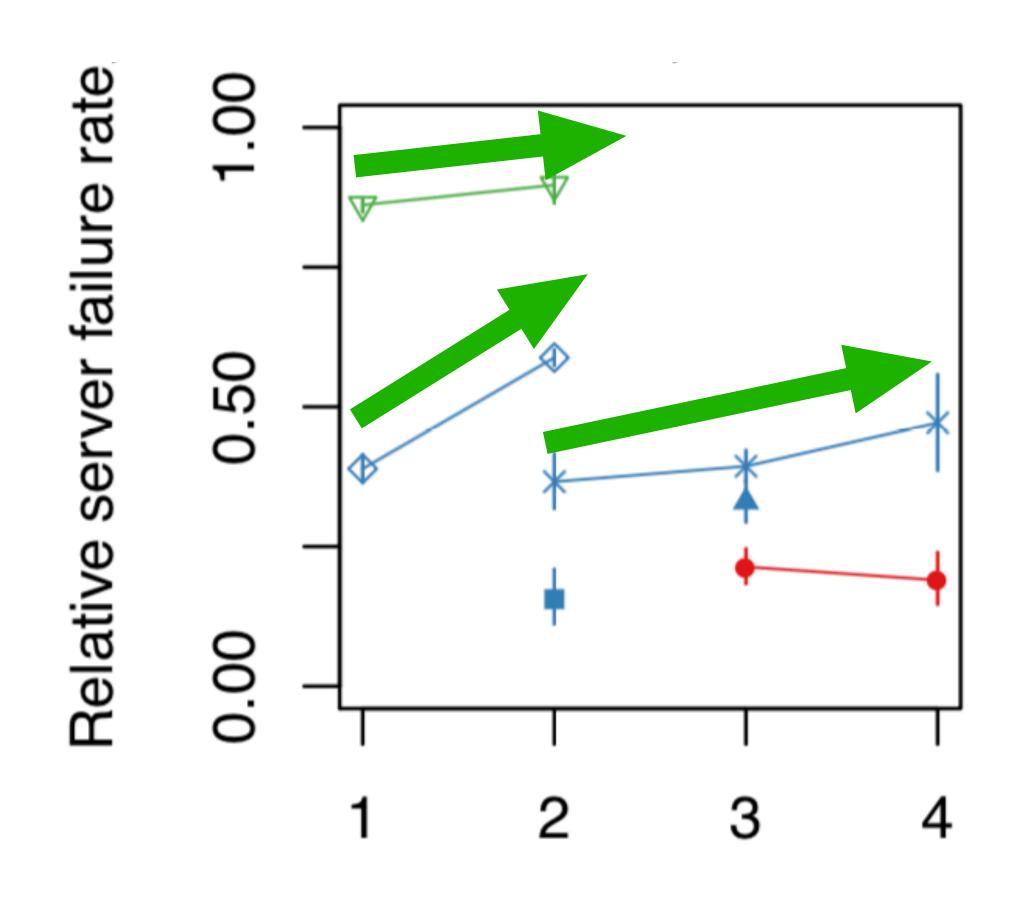
- First study at large scale
 - Cluster of 12,276 servers
- Reduced error rate by 67%

PAGE OFFLINING AT SCALE



- First study at large scale
 - Cluster of 12,276 servers
- Reduced error rate by 67%
- Prior simulations: 86 to 94%
 - Did not account for OS failures to lock page

DRAM WEAROUT IN THE FIELD



- DRAM shows signs of wear
- Idea: What if we performed wear leveling in DRAM?
 - Can be done in OS without modifying hardware

Server age (years)

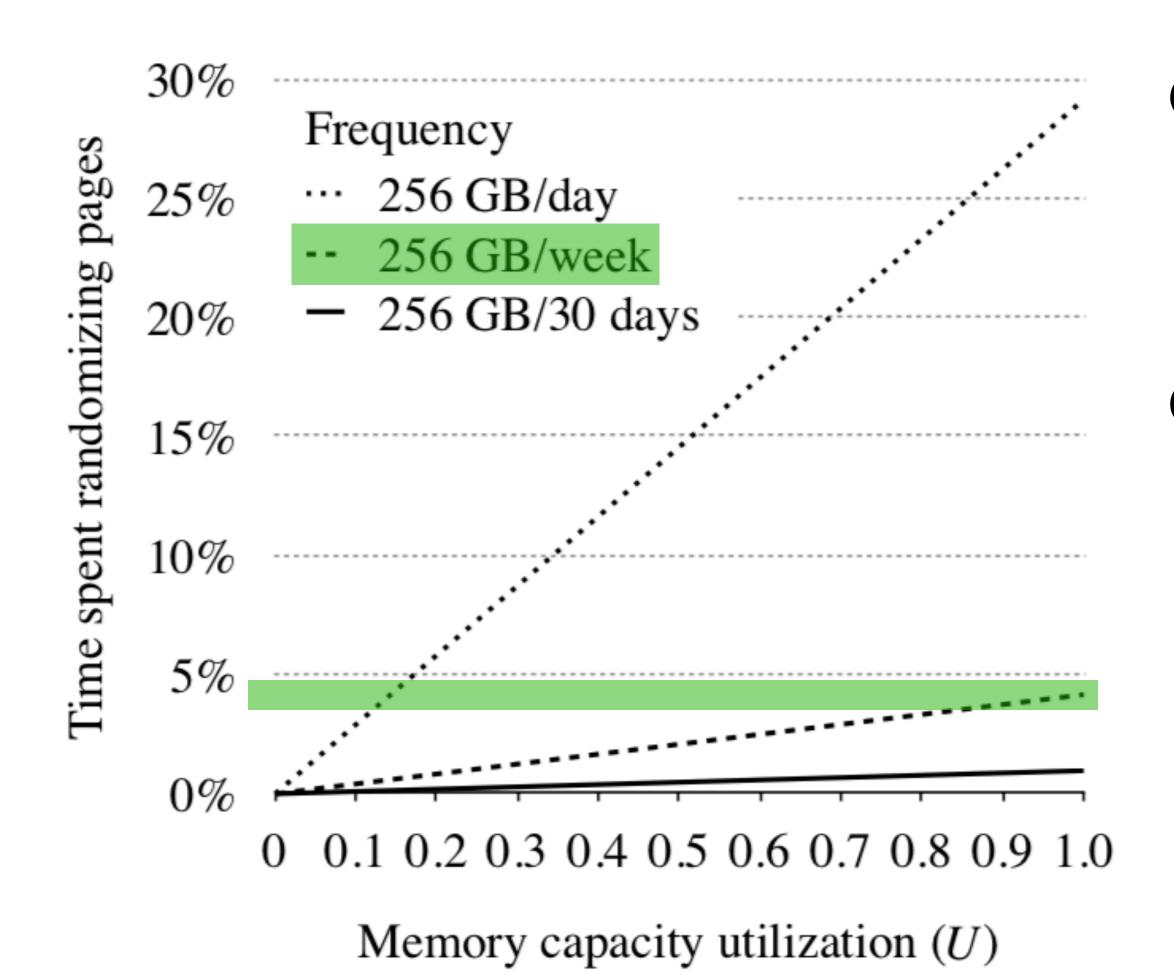
PAGE RANDOMIZATION

Input: The address of a physical page to randomize.

- 1 Lock the page.
- Flush any pending updates to the page.
- Randomly select a new free page to allocate.
- 4 Migrate the contents of the old page to the new page.
- 5 Update the page table mappings and remove any stale TLB entires.
- 6 Unlock the page.

Prototype implemented in Debian 6.0.7 kernel

PAGE RANDOMIZATION



- Can perform with low overhead (< 5%)
- Can fine-tune desired rate of randomization

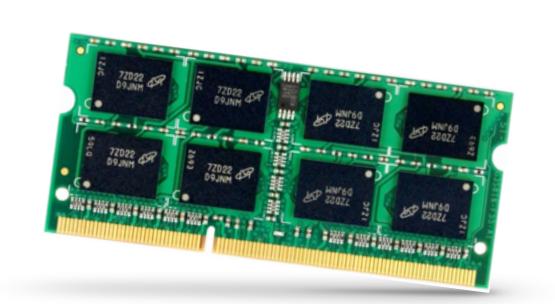
KEY DRAM CONTRIBUTIONS

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- Denial of service due to socket/channel
- Higher density = more failures
- Architectural effects on reliability
- Workload influence on failures
- Model, page-offlining, page randomization

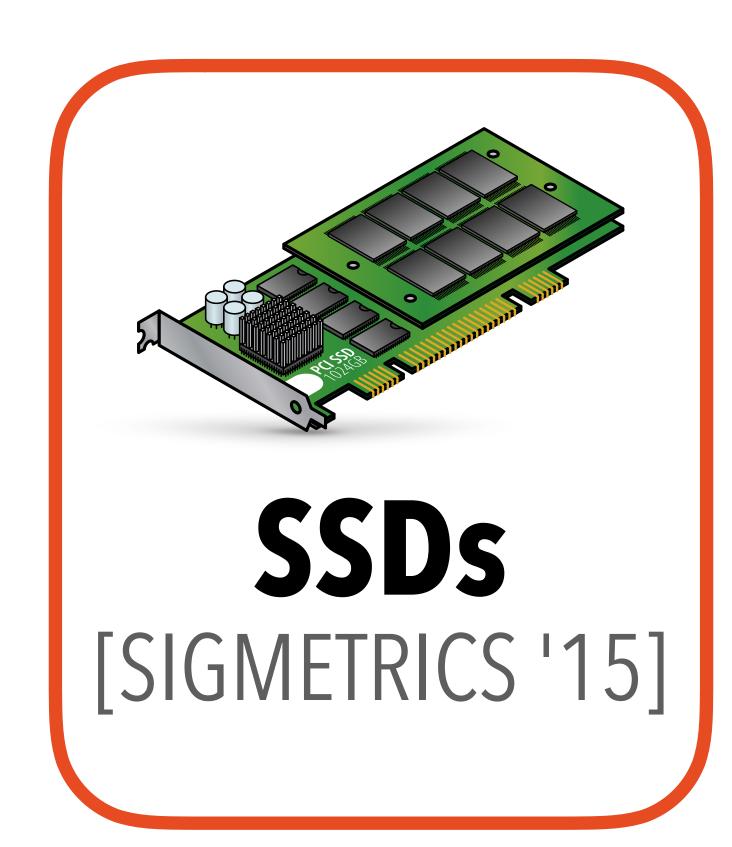
RELATED WORK

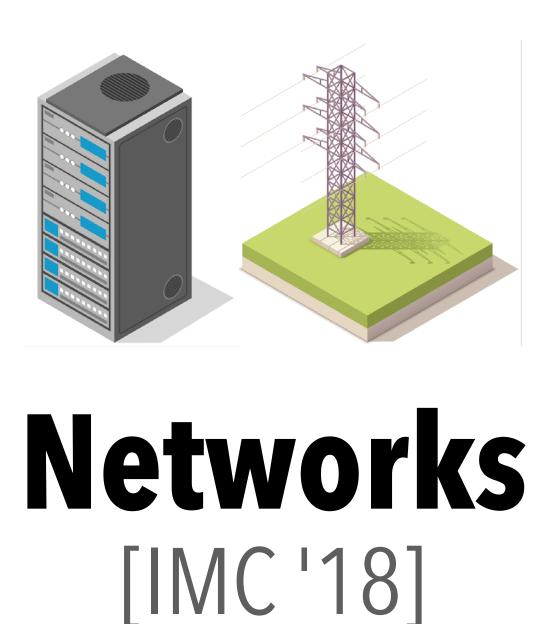
- DRAM errors at Google
 [Schroeder+ SIGMETRICS'09]
- Component failures + simulated page offlining [Hwang+ ASPLOS'12]
- *Error correction, location, multi-DIMM errors* [Sridharan+ SC'12, SC'13; DeBardeleben+ SELSE'14]

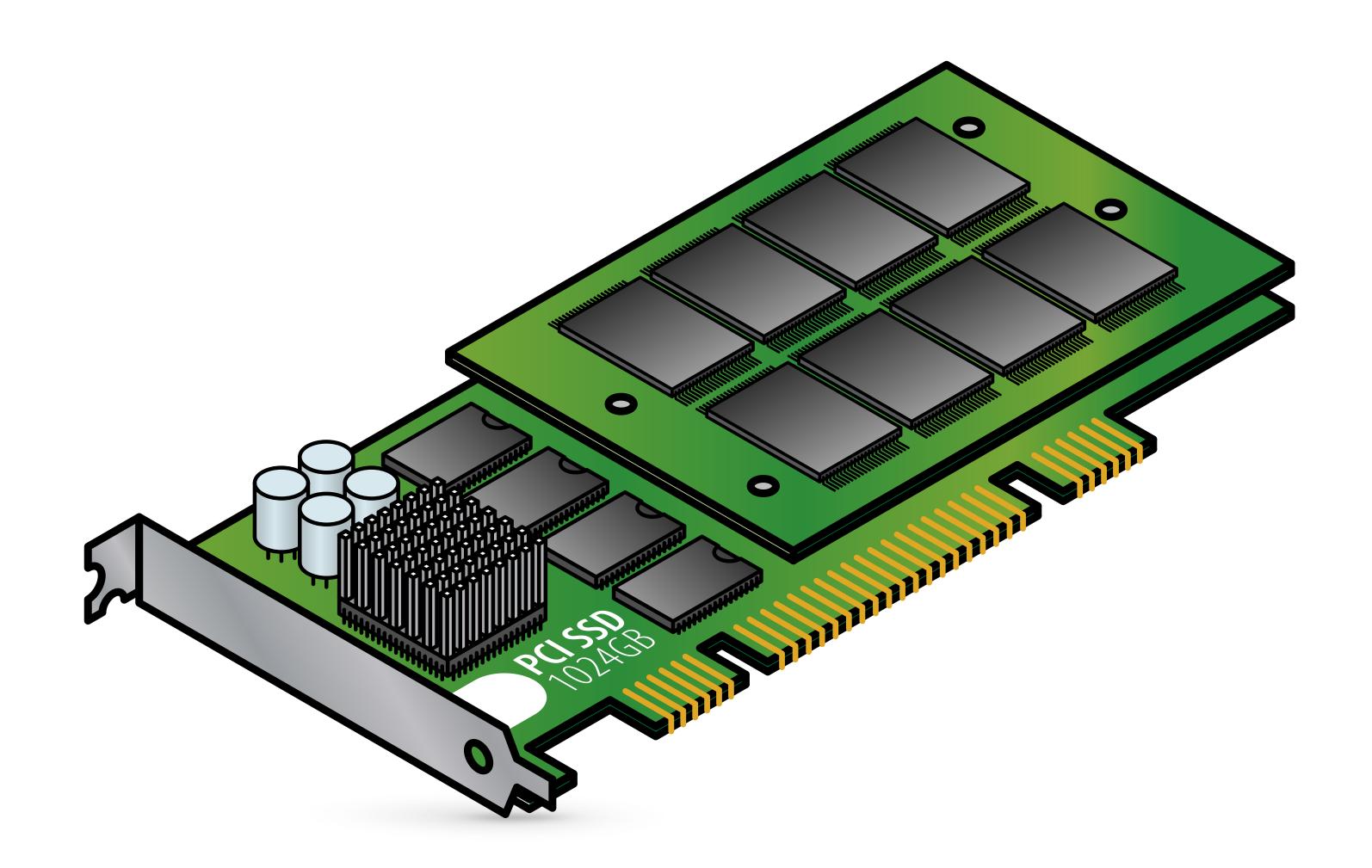
LARGE SCALE STUDIES

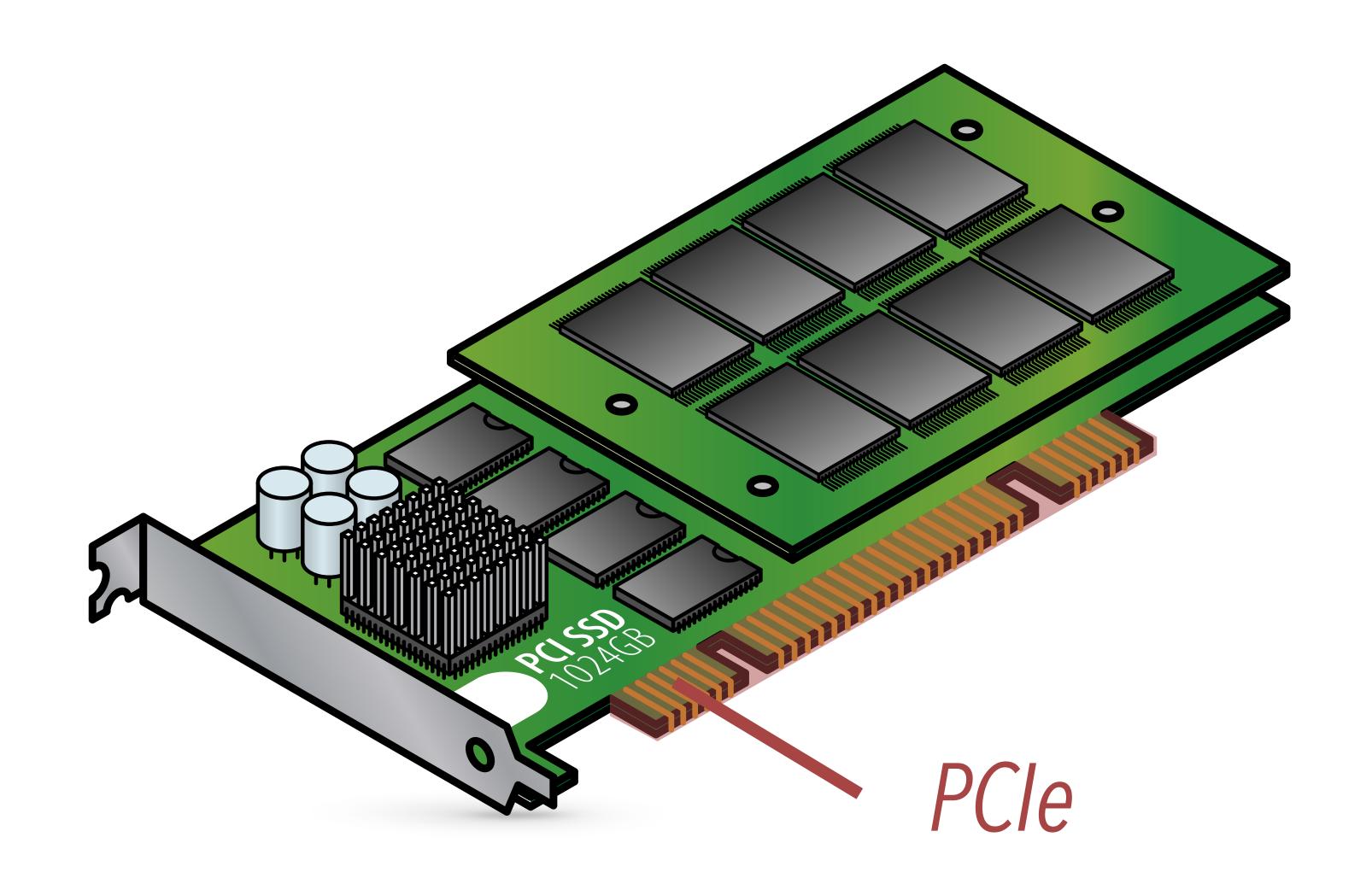


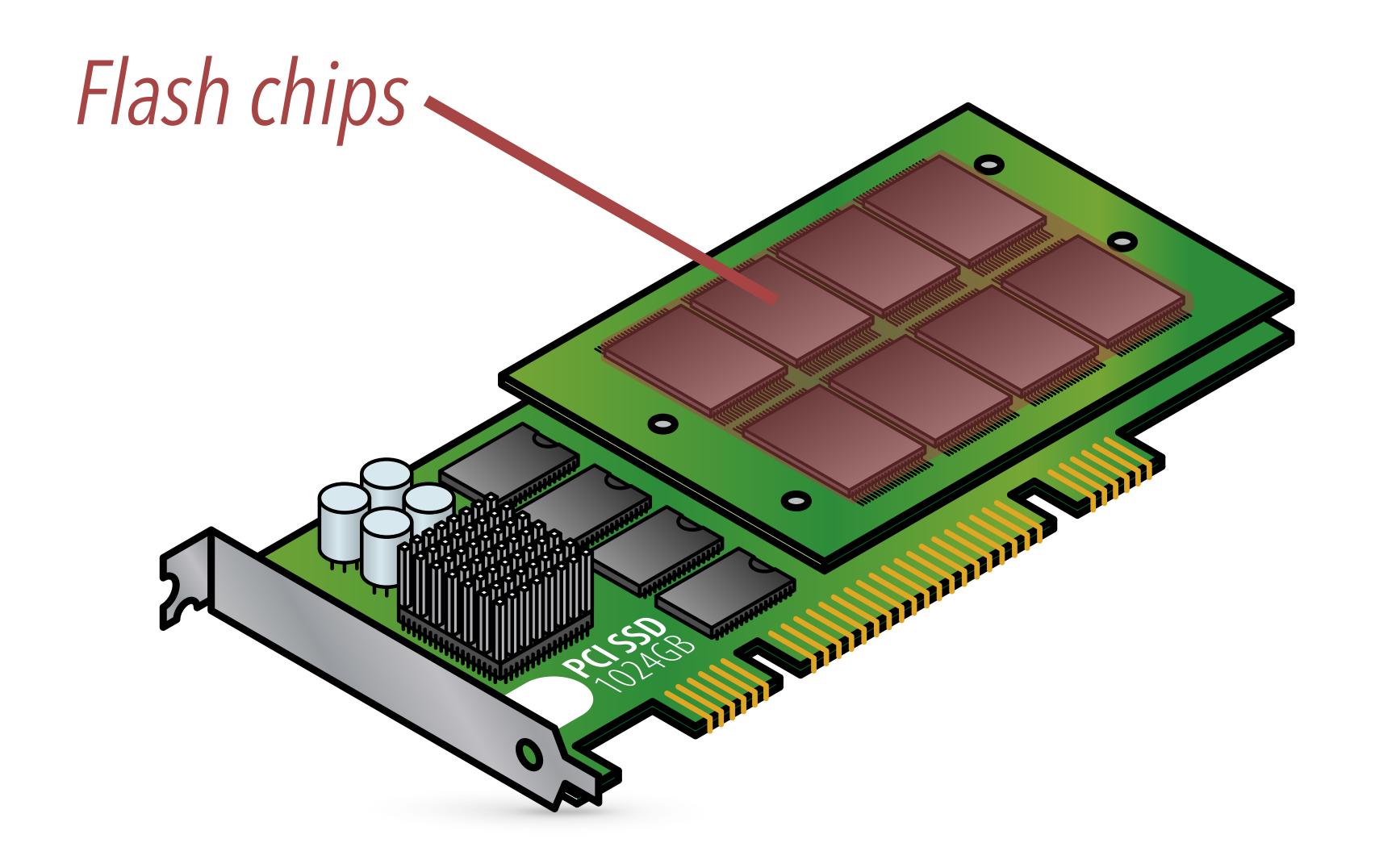
DRAM
[DSN '15]



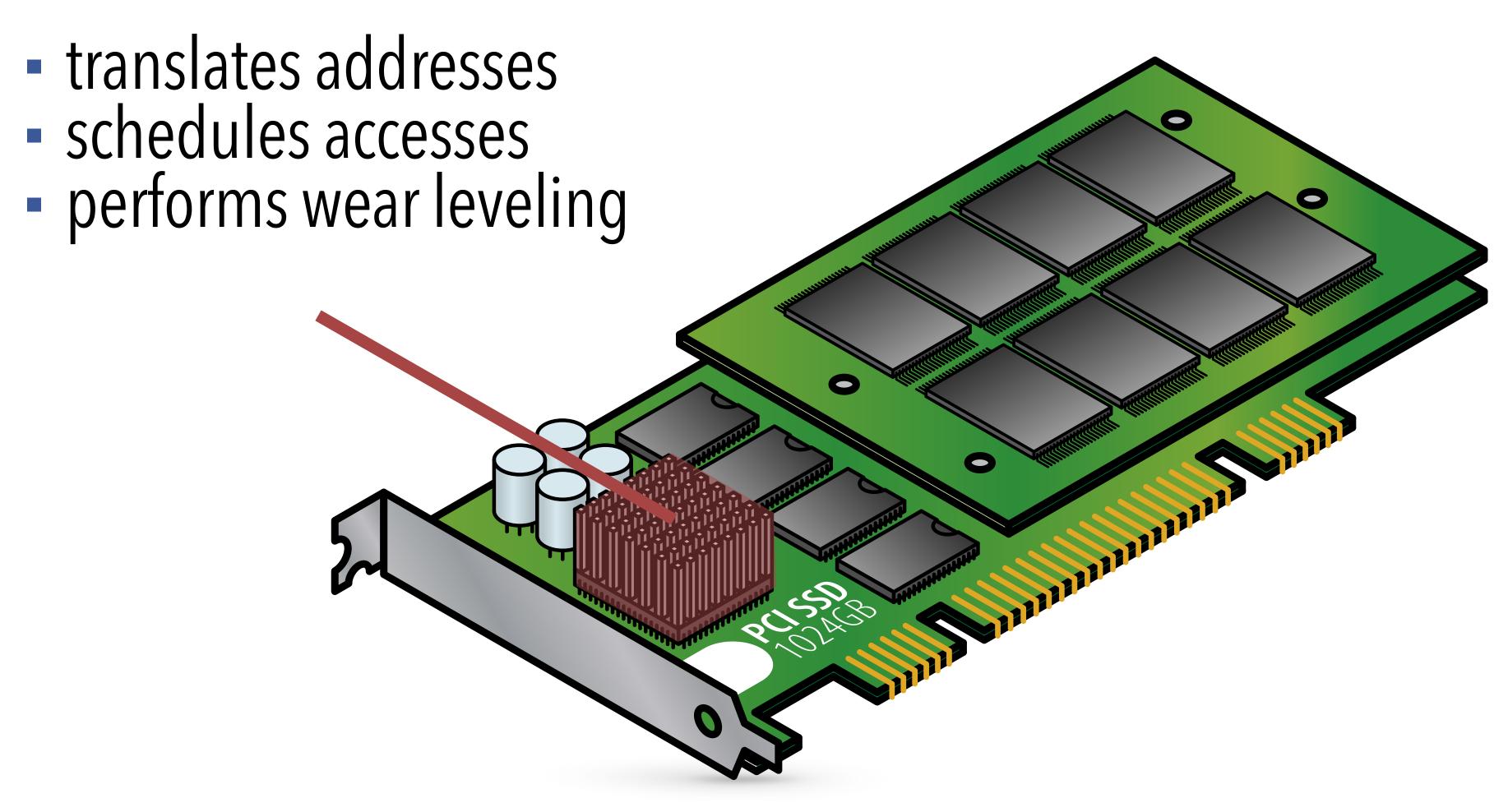


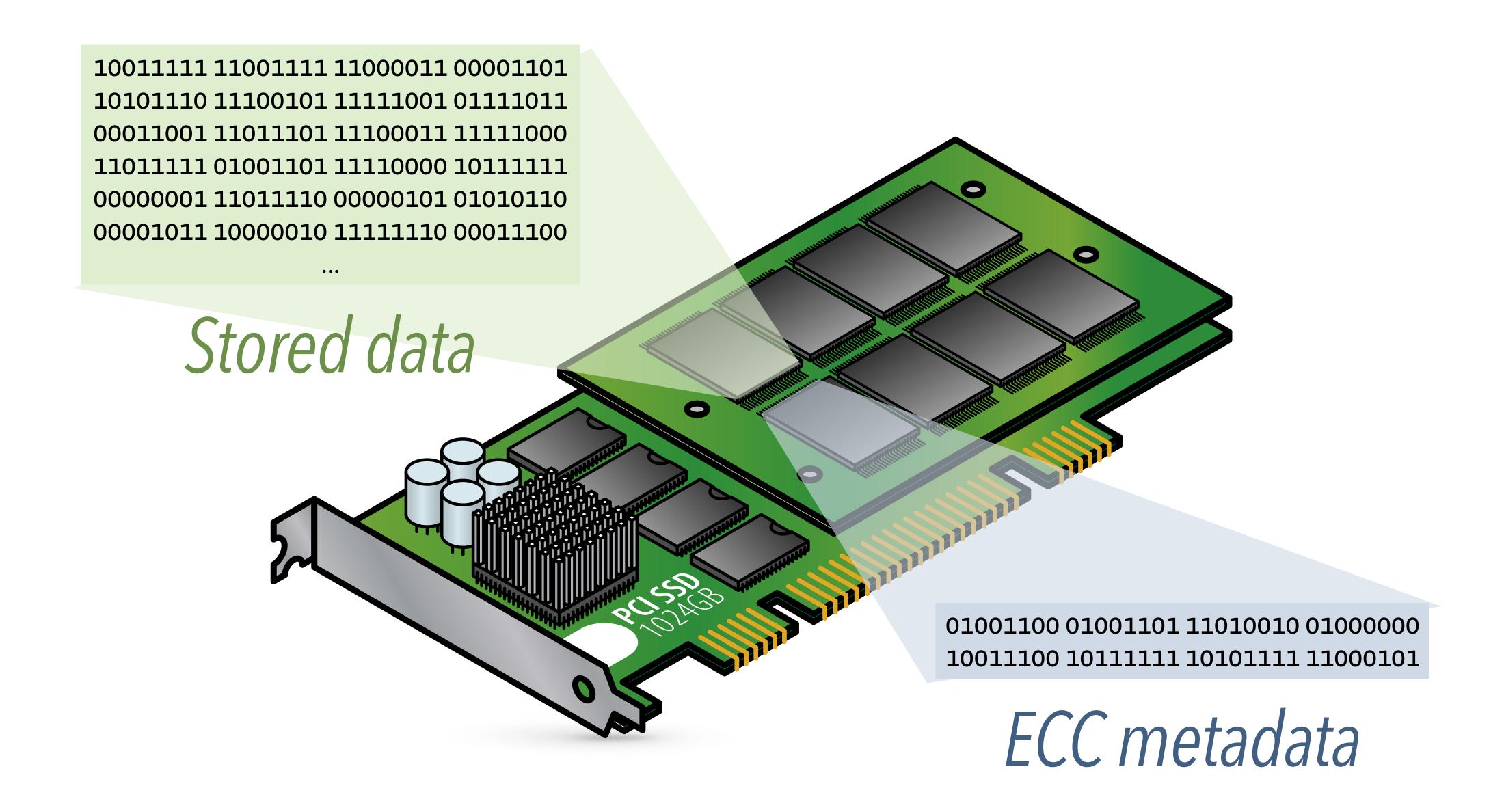






SSD controller





TYPES OF SSD FAILURES

Ones that cause SMALL ERRORS

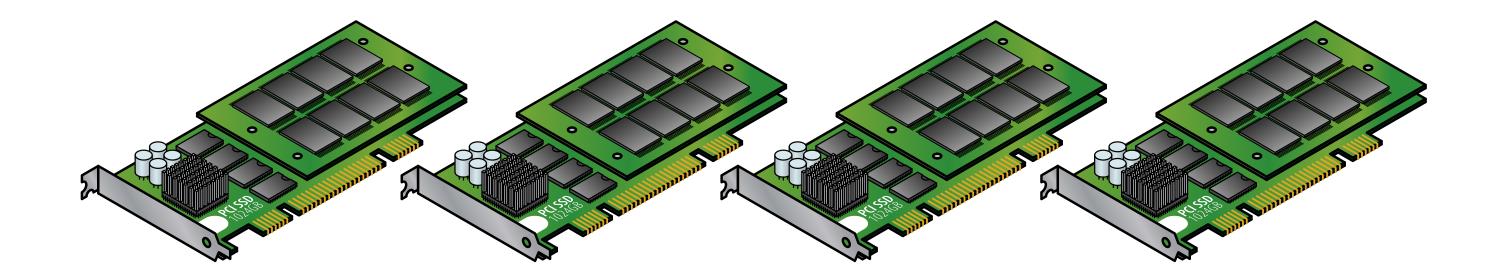
- 10's of flipped bits per KB
- Silently corrected by SSD controller

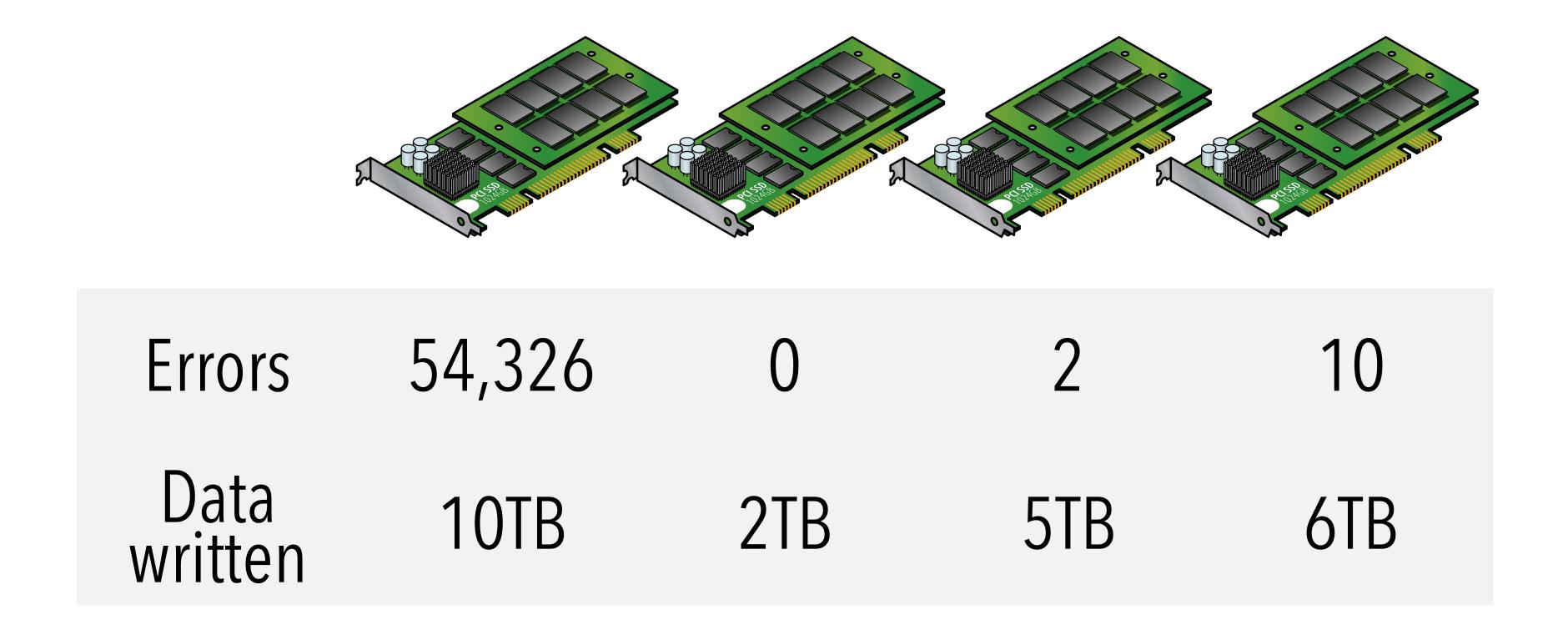
Ones that cause LARGE ERRORS

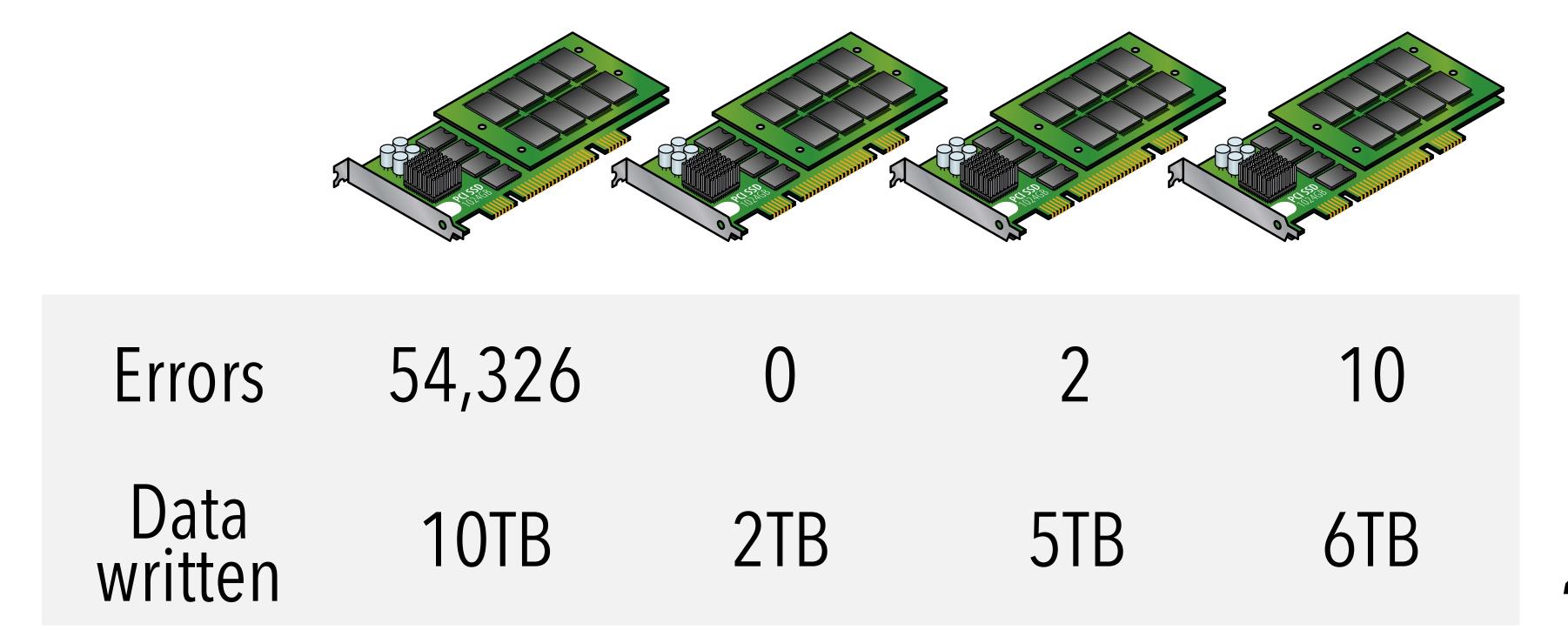
- 100's of flipped bits per KB
- Corrected by host using driver
- Referred to as SSD failure

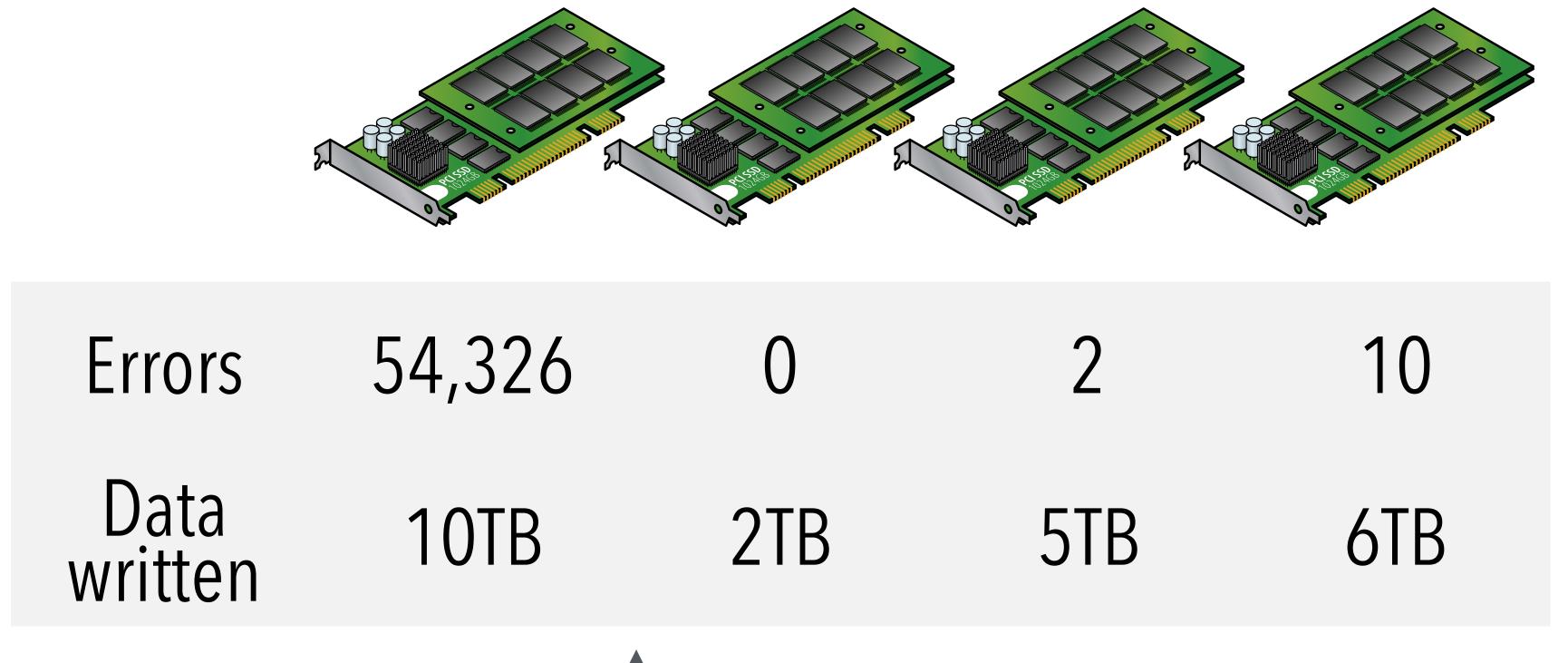
MEASURING SSD FAILURES

- Examined lifetime hardware counters
 - Across Facebook's fleet
 - Devices deployed between 6 months and 4 years
 - 15 TB to 50 TB read and written
 - Planar, Multi-Level Cell (MLC)
- Snapshot-based analysis

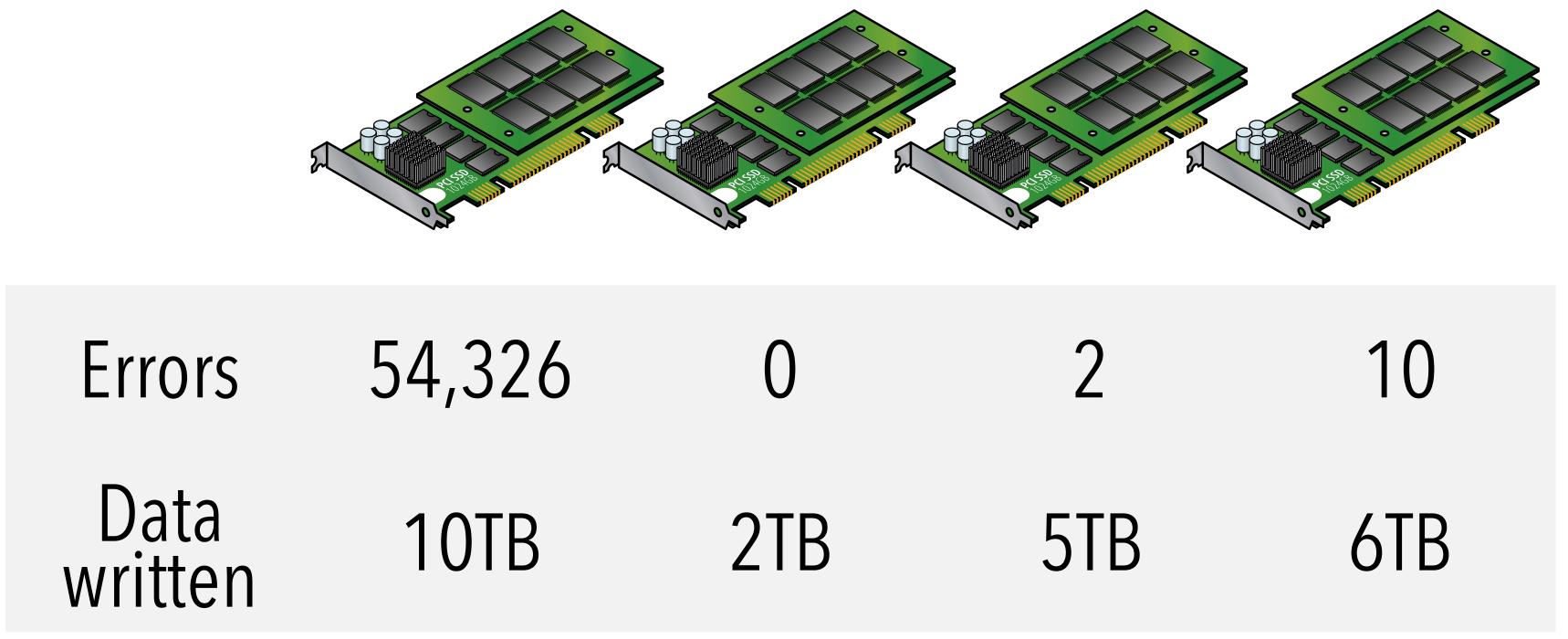


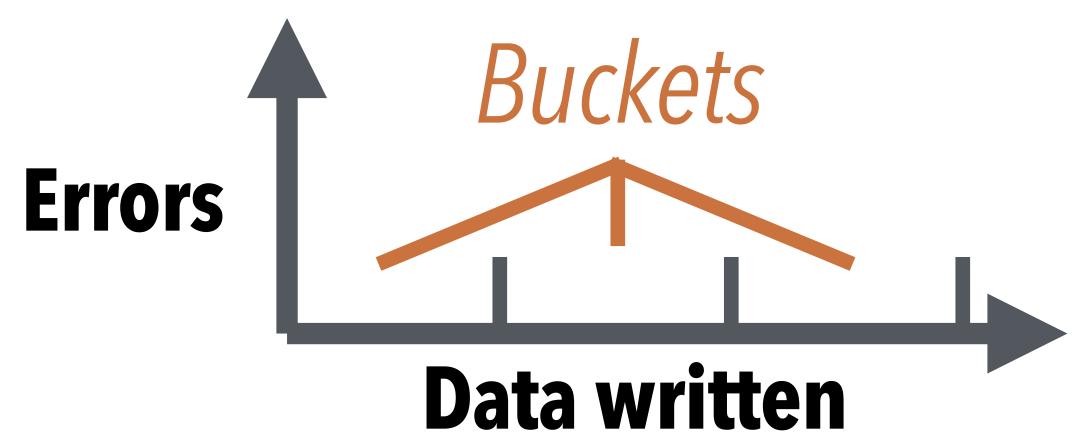


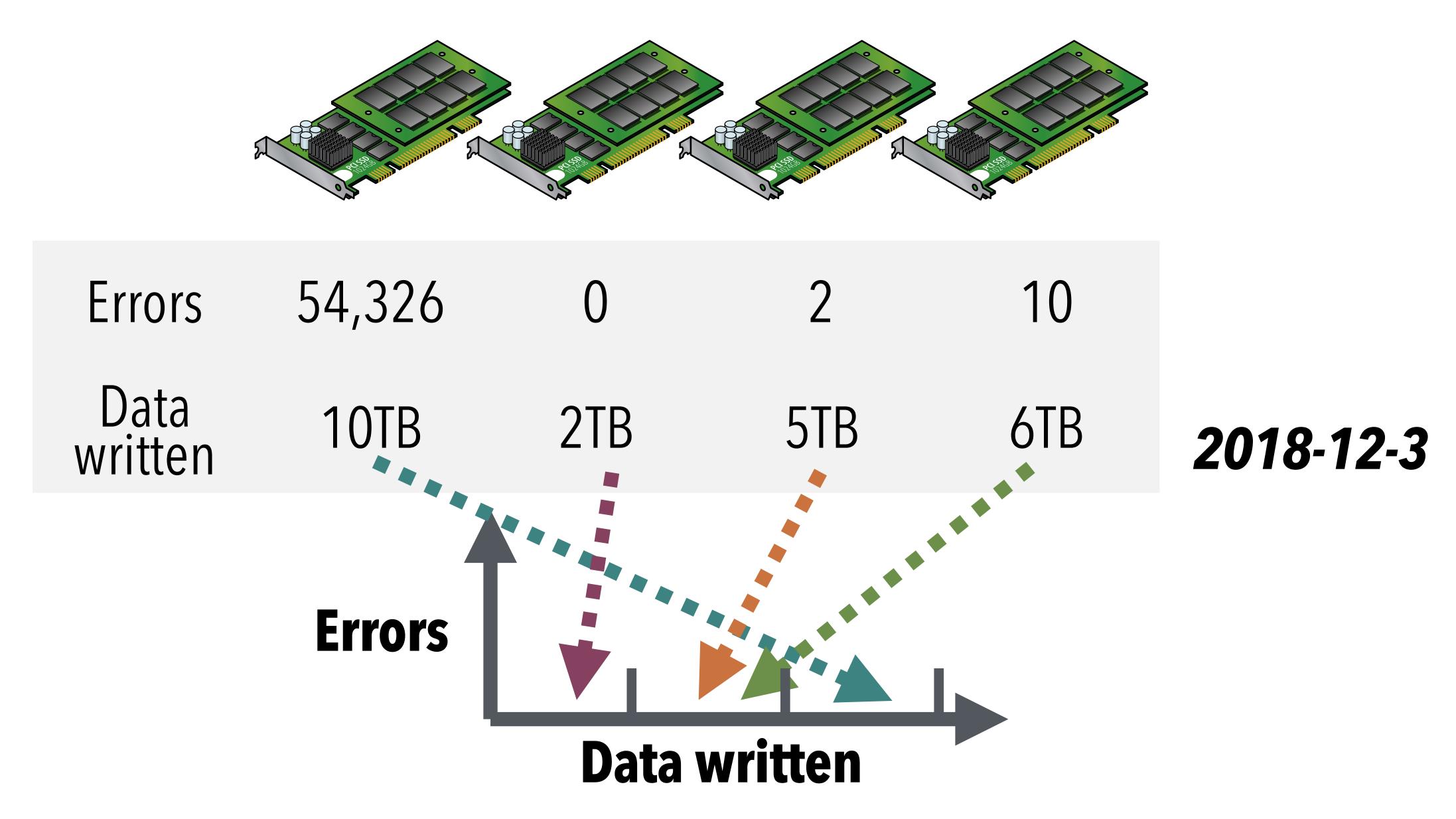


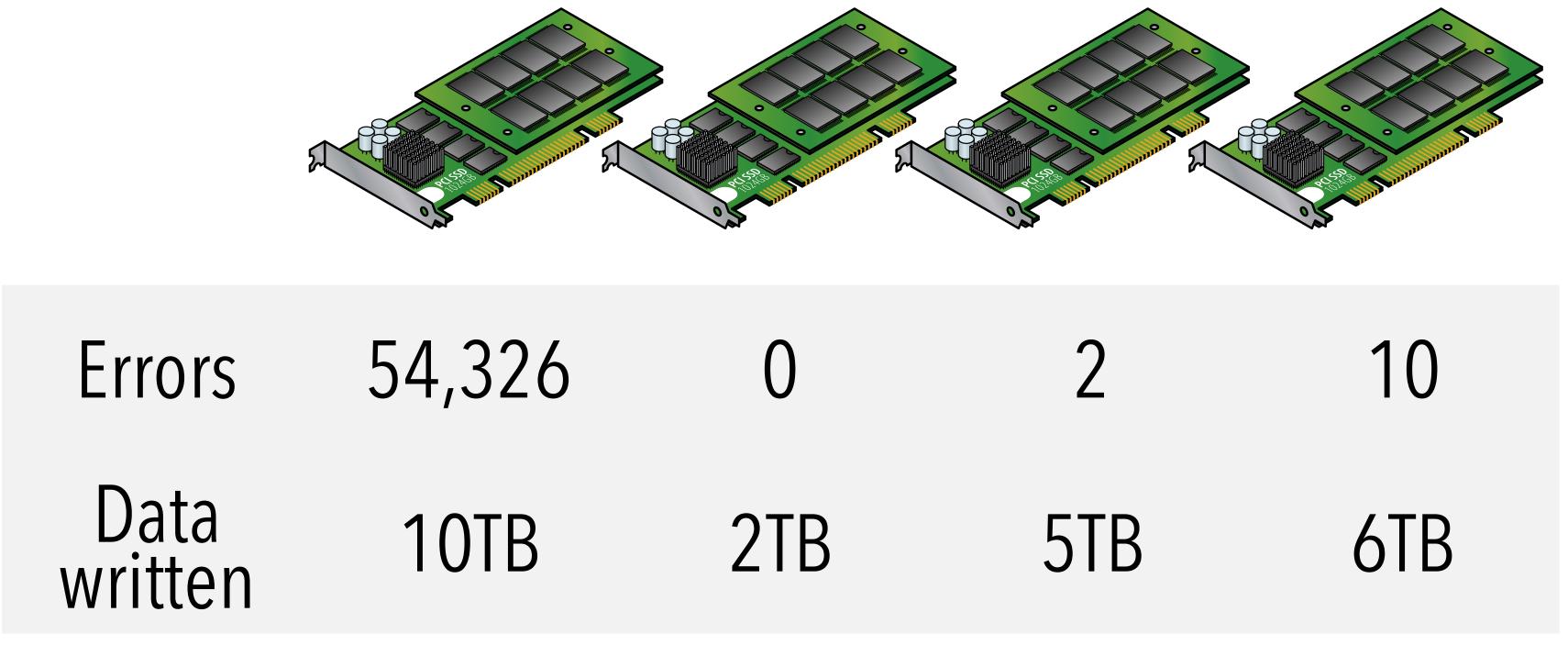










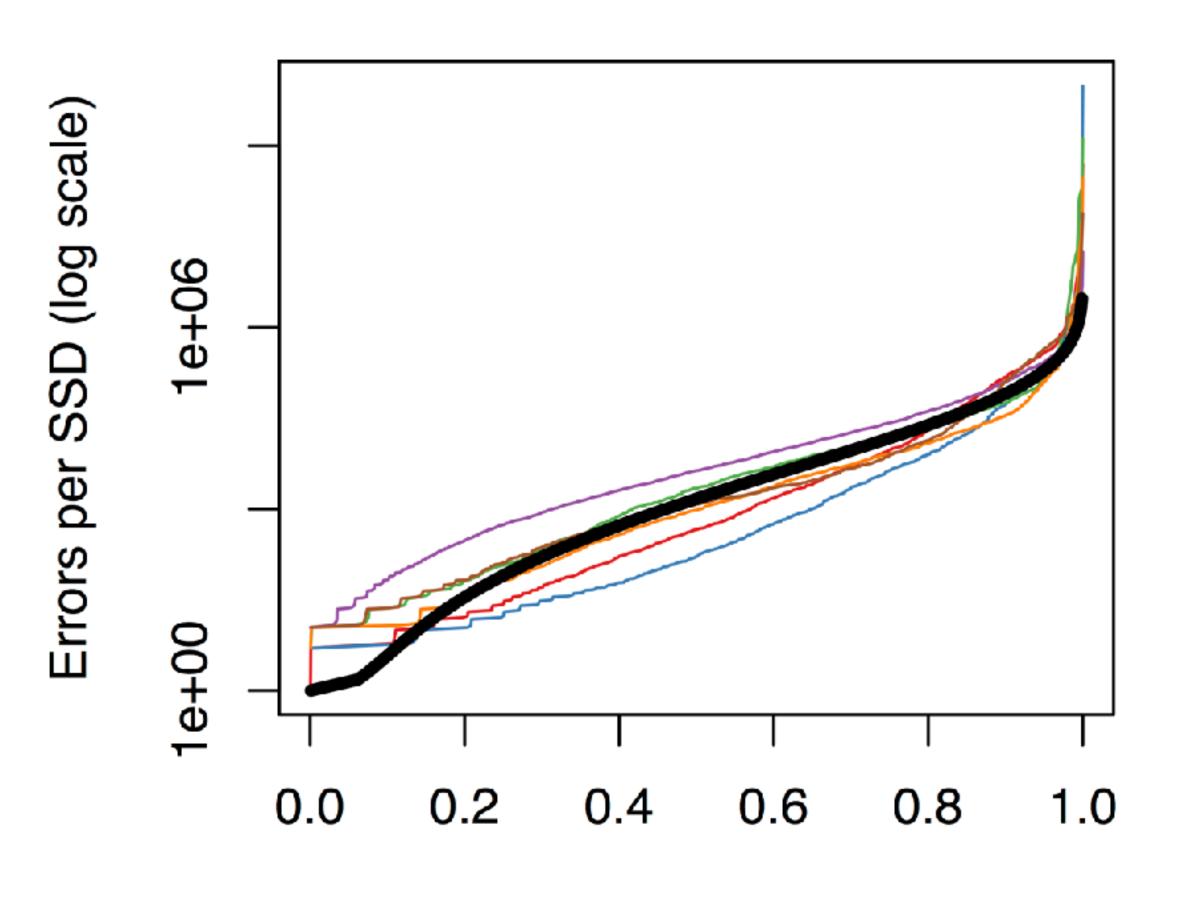




KEY SSD CONTRIBUTIONS

- Distinct lifecycle periods
- Read disturbance not prevalent in the field
- Higher temperatures cause more failures
- Amount of data written by OS is misleading
- Write amplification trends from the field

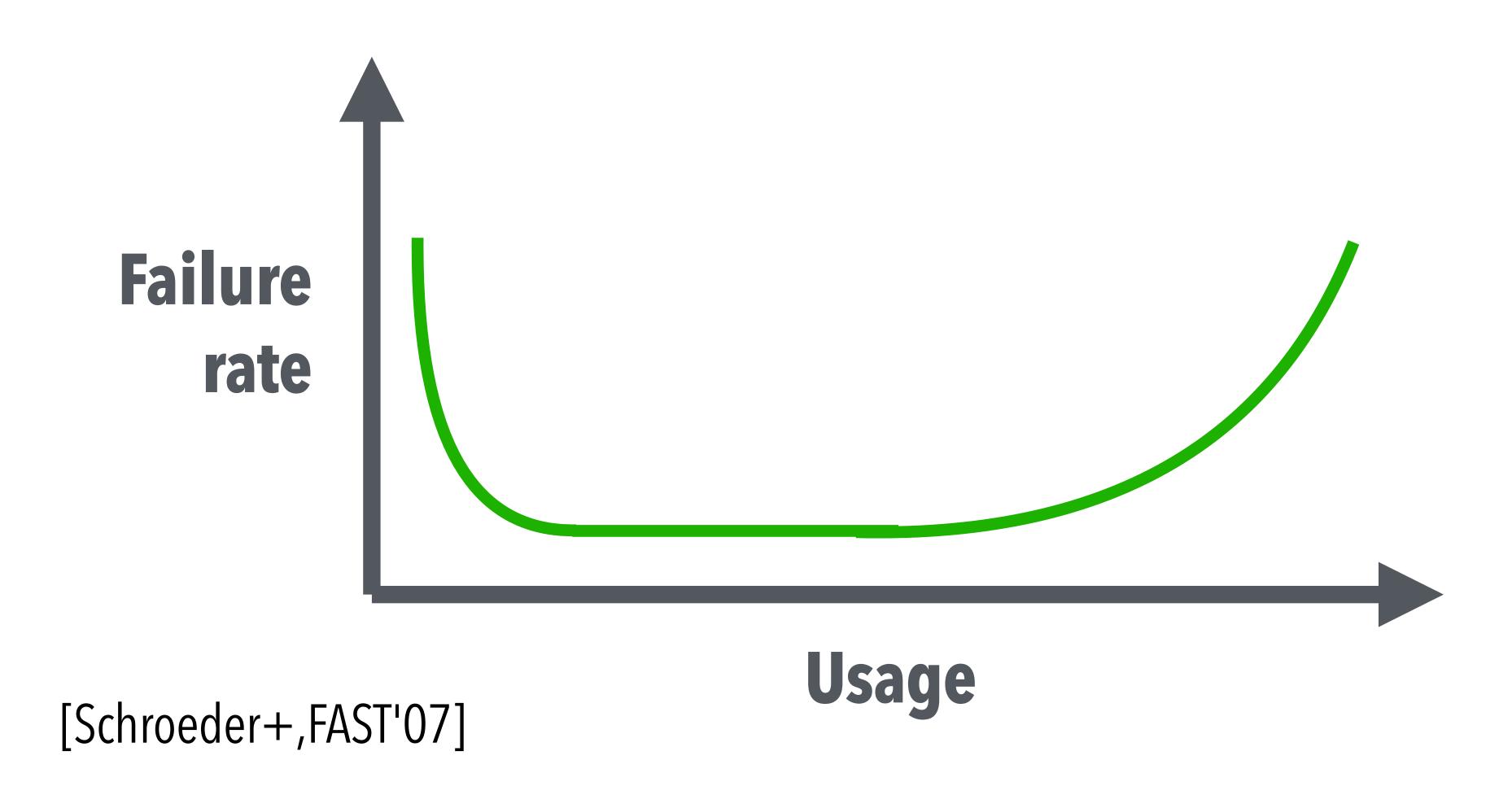
FAILURE MODELING



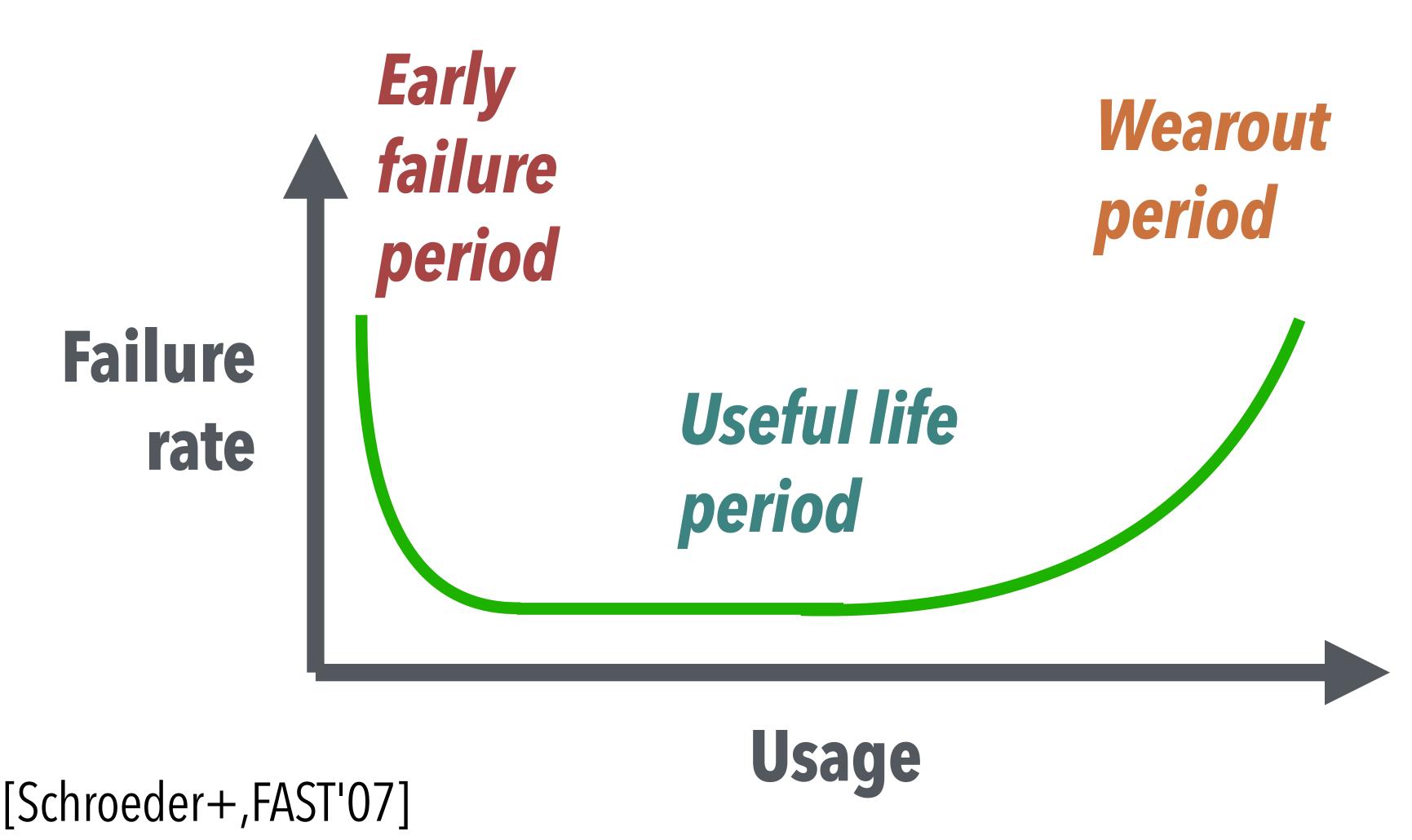
- Built a model across 6 SSD server configurations
- Weibull (0.3, 5e3)
- Most errors are from a small set of SSDs

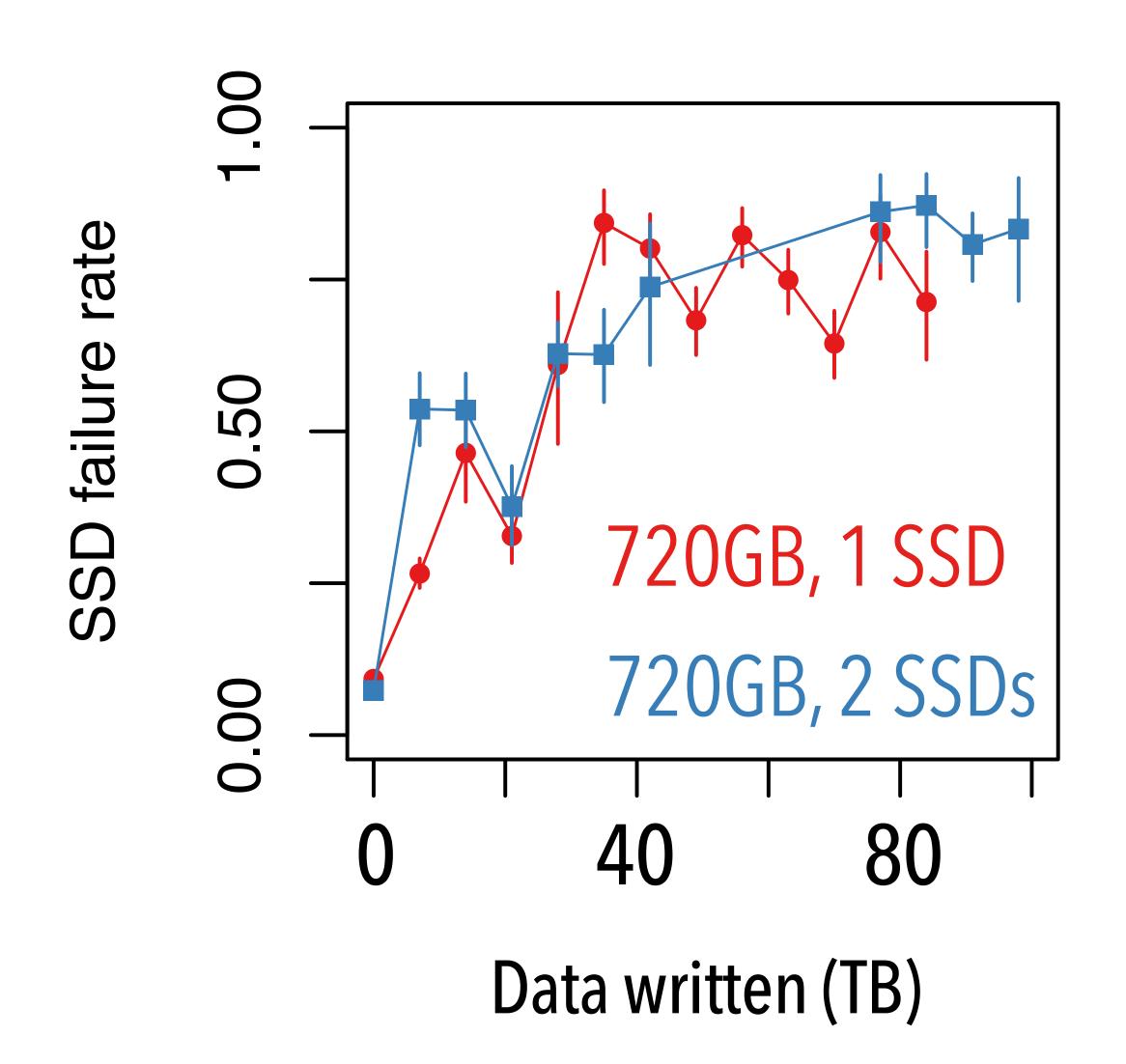
Normalized SSD number

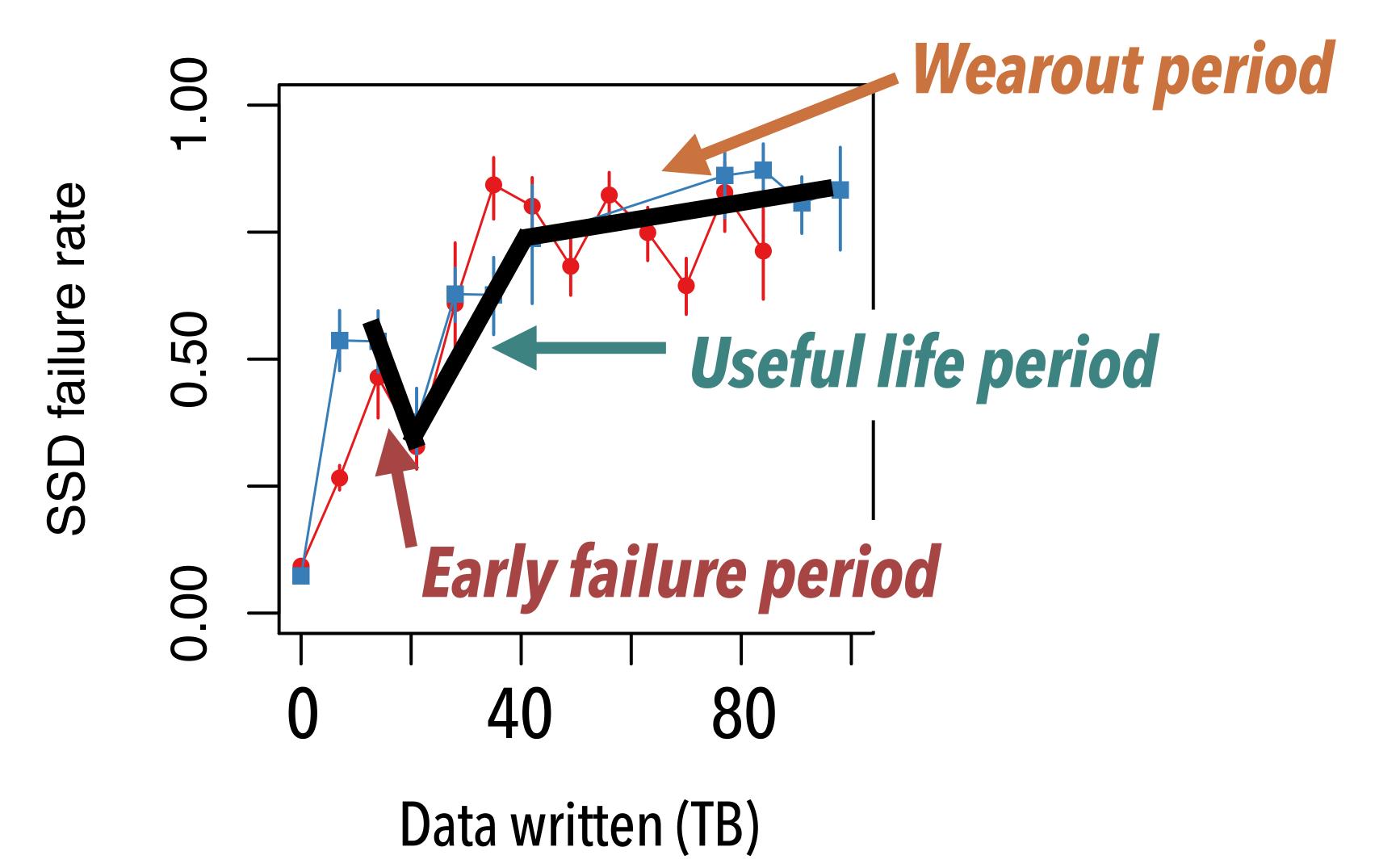
Storage lifecycle background: the bathtub curve for disk drives

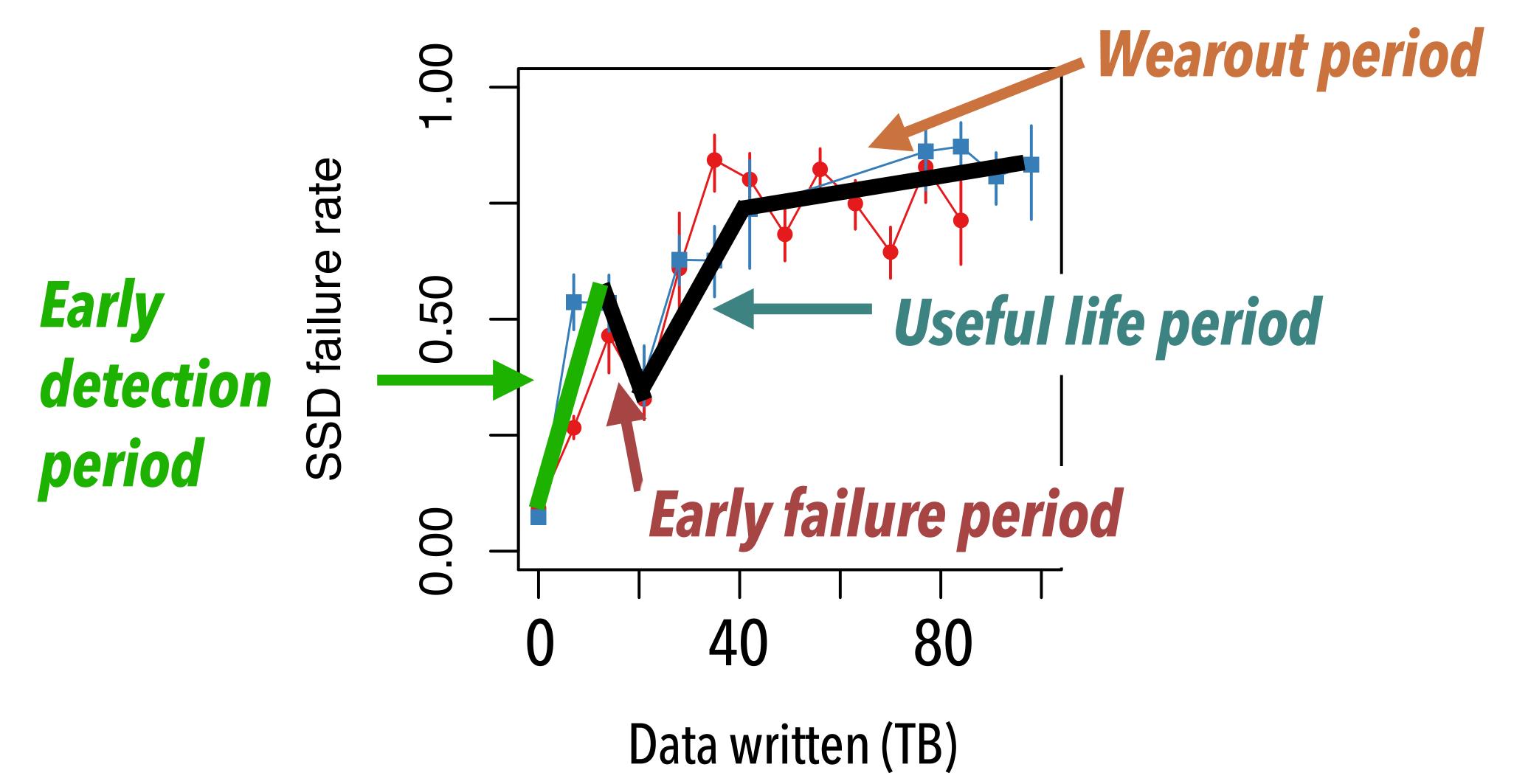


Storage lifecycle background: the bathtub curve for disk drives







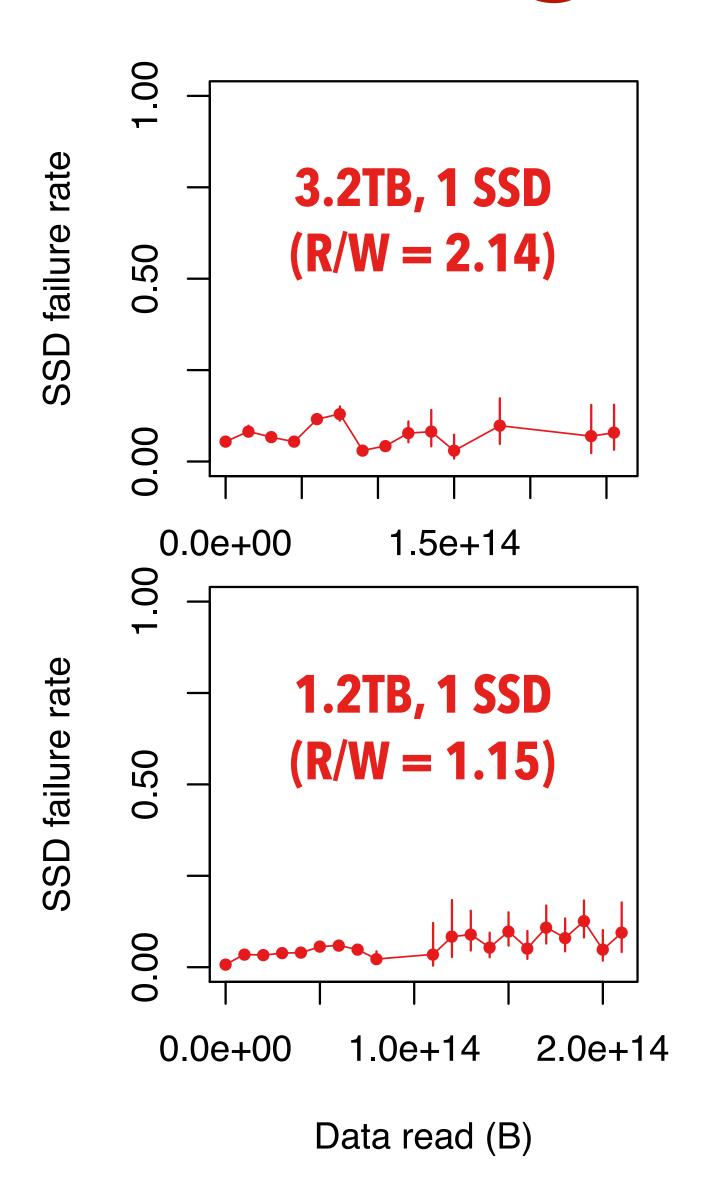


- We believe there are two distinct pools of flash cells
 - The "weak" pool fails first, during early detection
 - The "strong" pool follows the bathtub curve
- Burn-in testing is important to help the SSD identify the weak pool of cells

Read disturbance errors

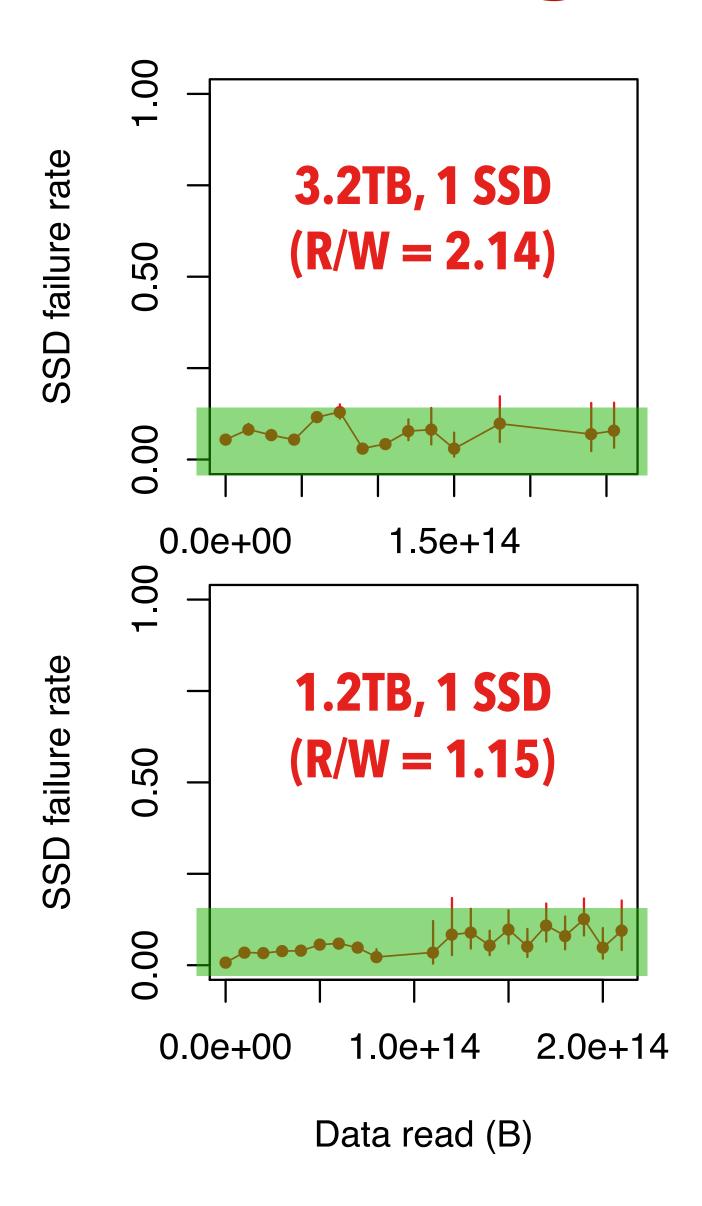
- Charge drift from reads to neighboring cells
- Documented in prior controlled studies on chips

READ DISTURBANCE ERRORS



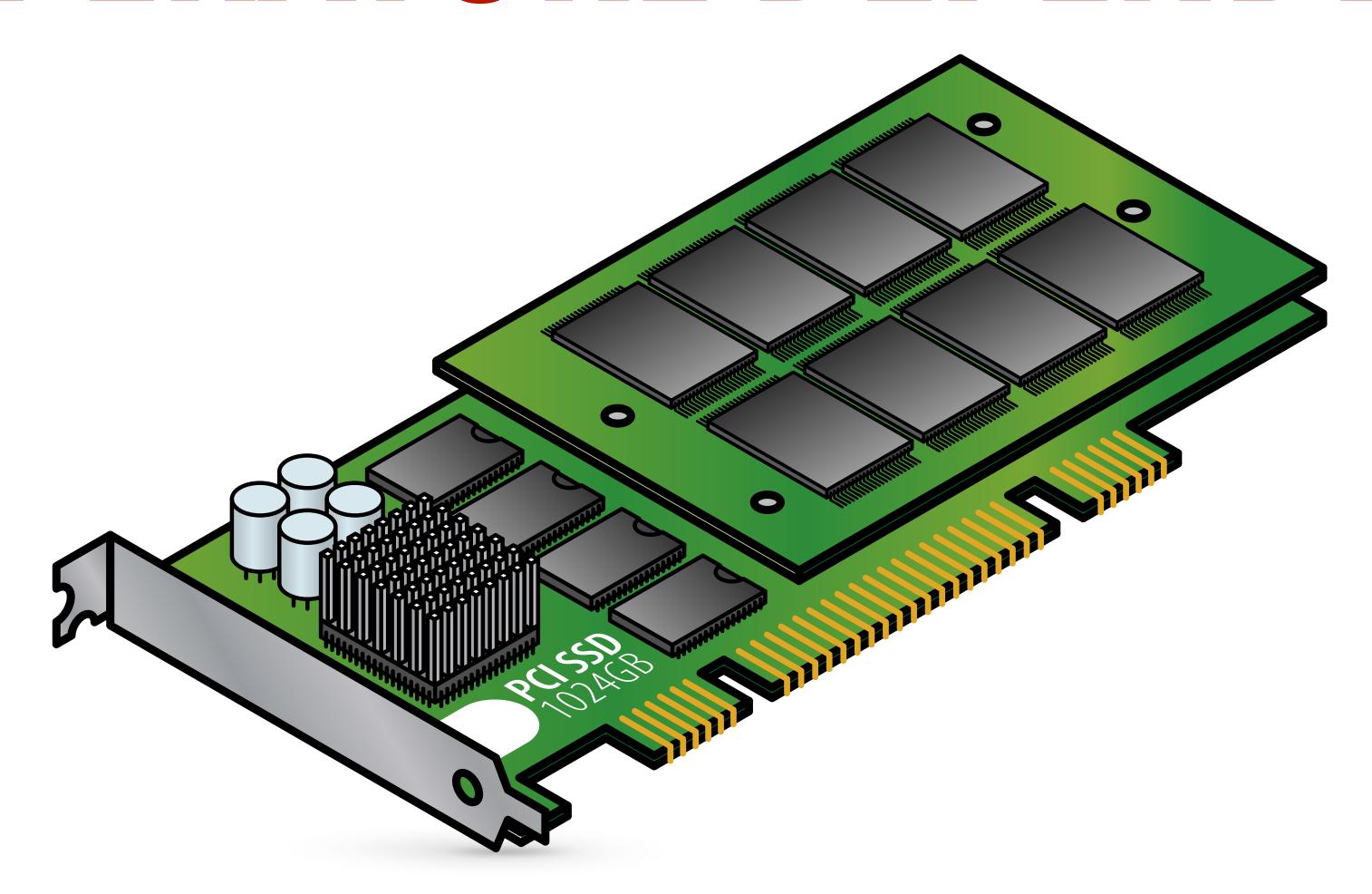
SSDs with the most reads

READ DISTURBANCE ERRORS

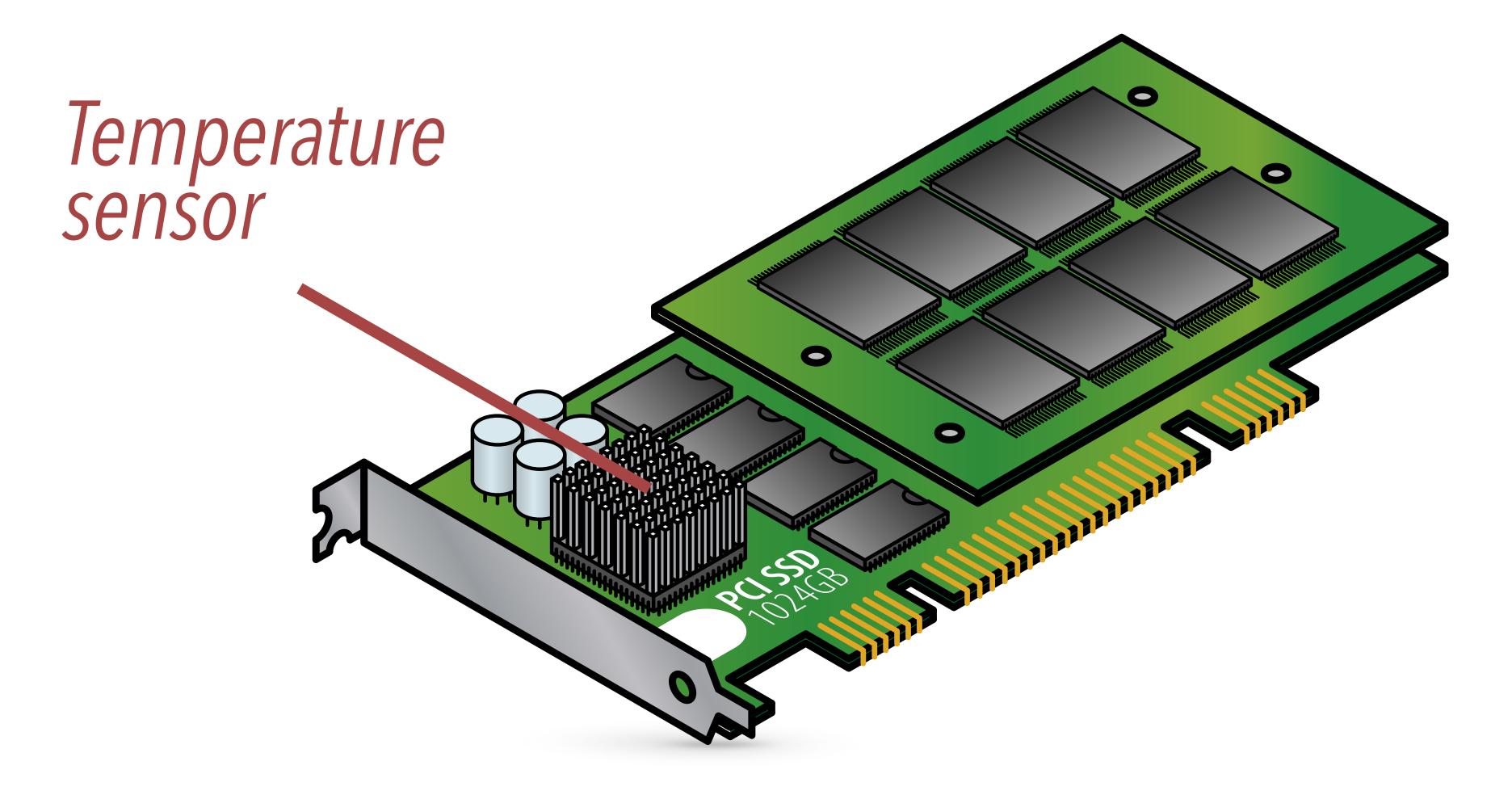


- SSDs with the most reads
- No statistically significant difference at low data read versus high data read

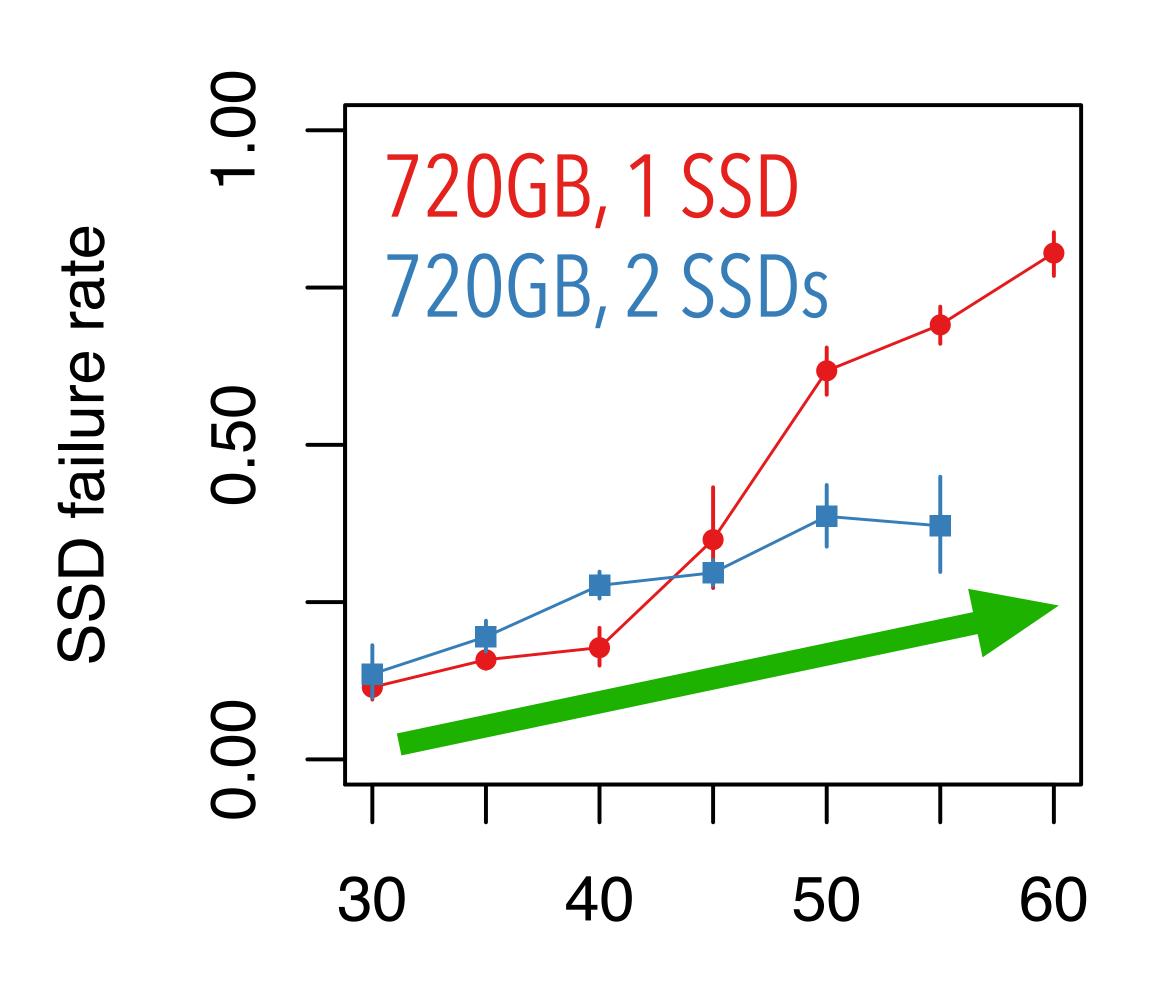
TEMPERATURE DEPENDENCE



TEMPERATURE DEPENDENCE



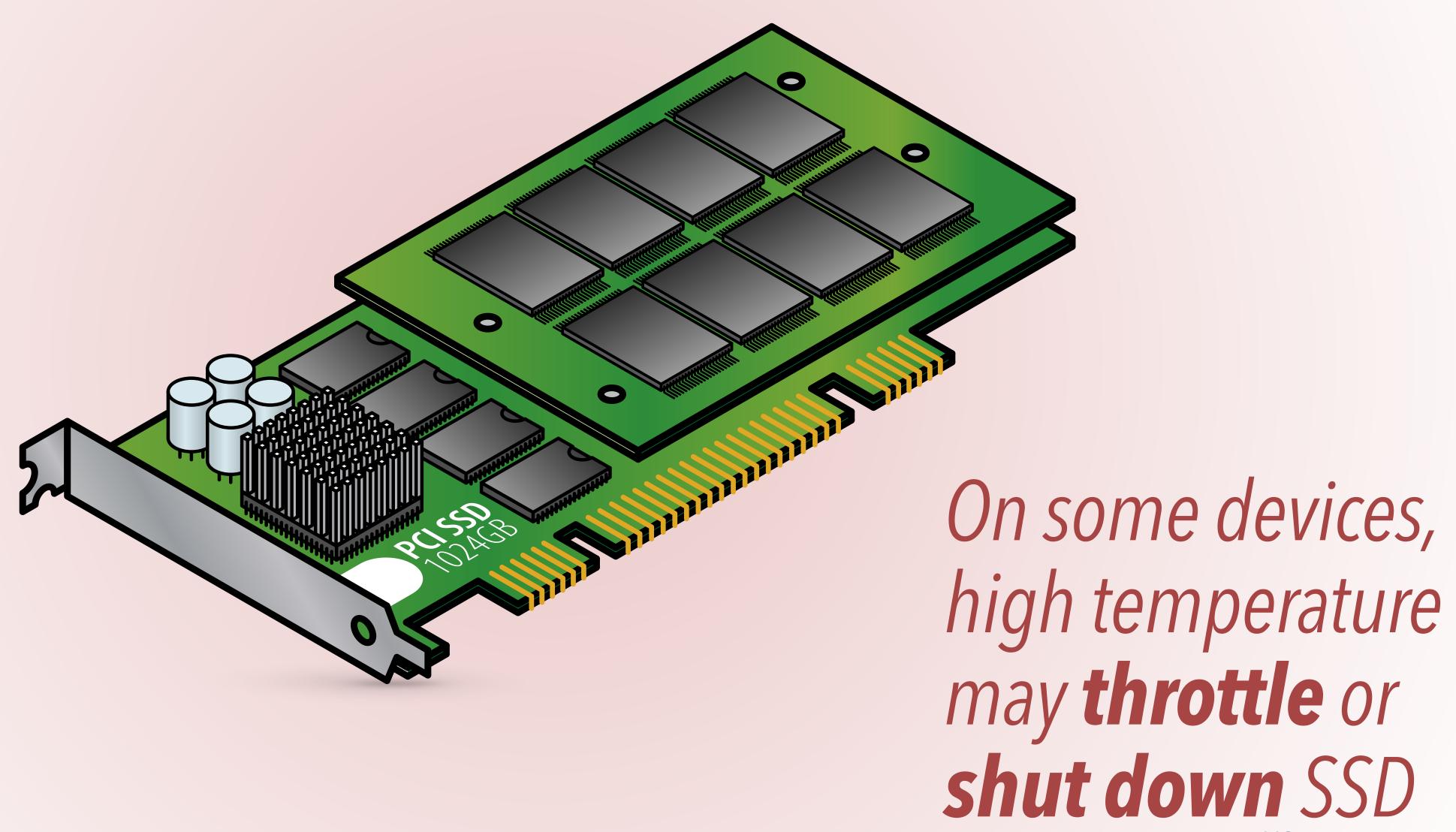
TEMPERATURE DEPENDENCE



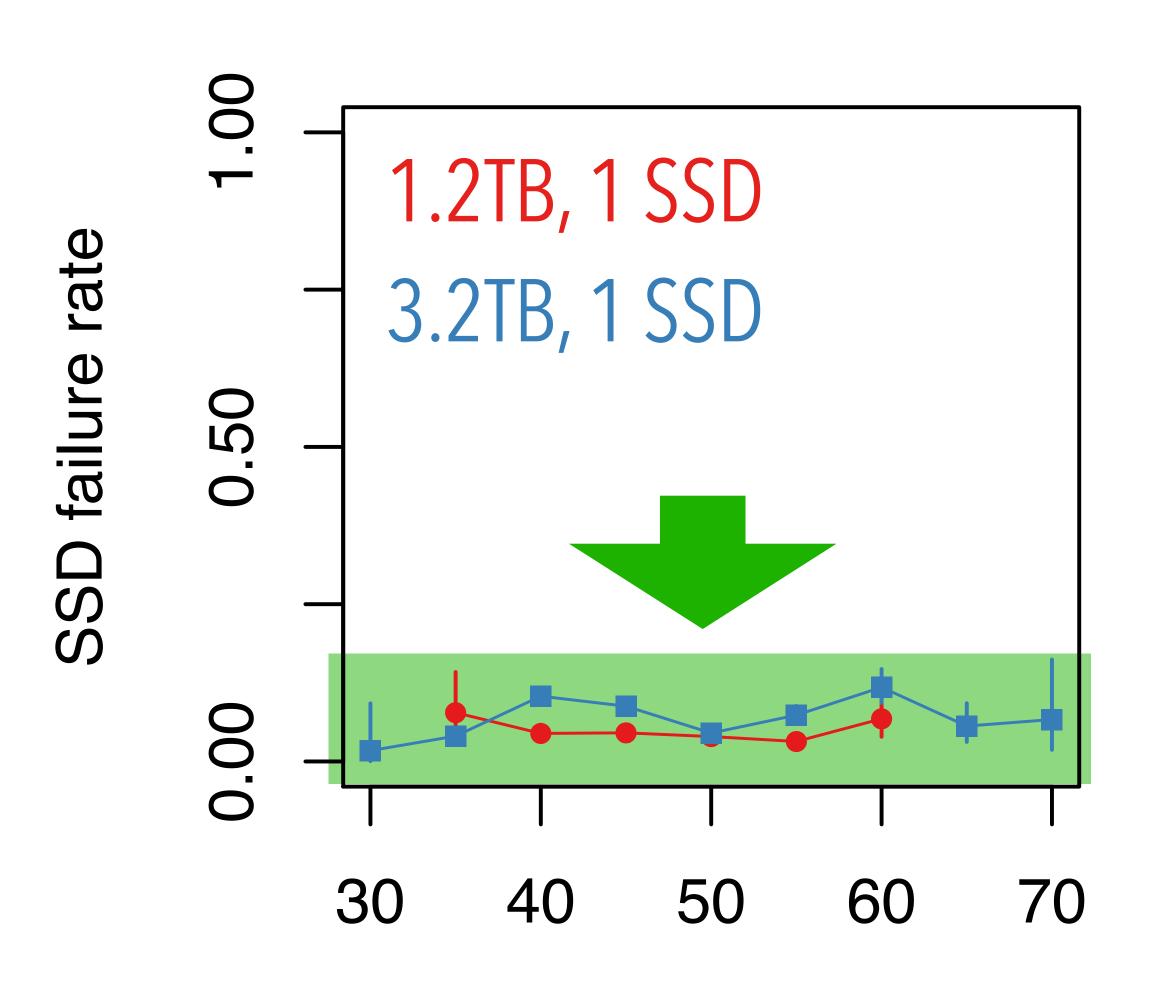
Higher temperature =
 more failures

Average temperature (°C)

TEMPERATURE DEPENDENCE



TEMPERATURE DEPENDENCE



- Throttling is an effective technique to reduce failures
- Potentially decreases device performance, however

Average temperature (°C)

Access patterns and SSD writes

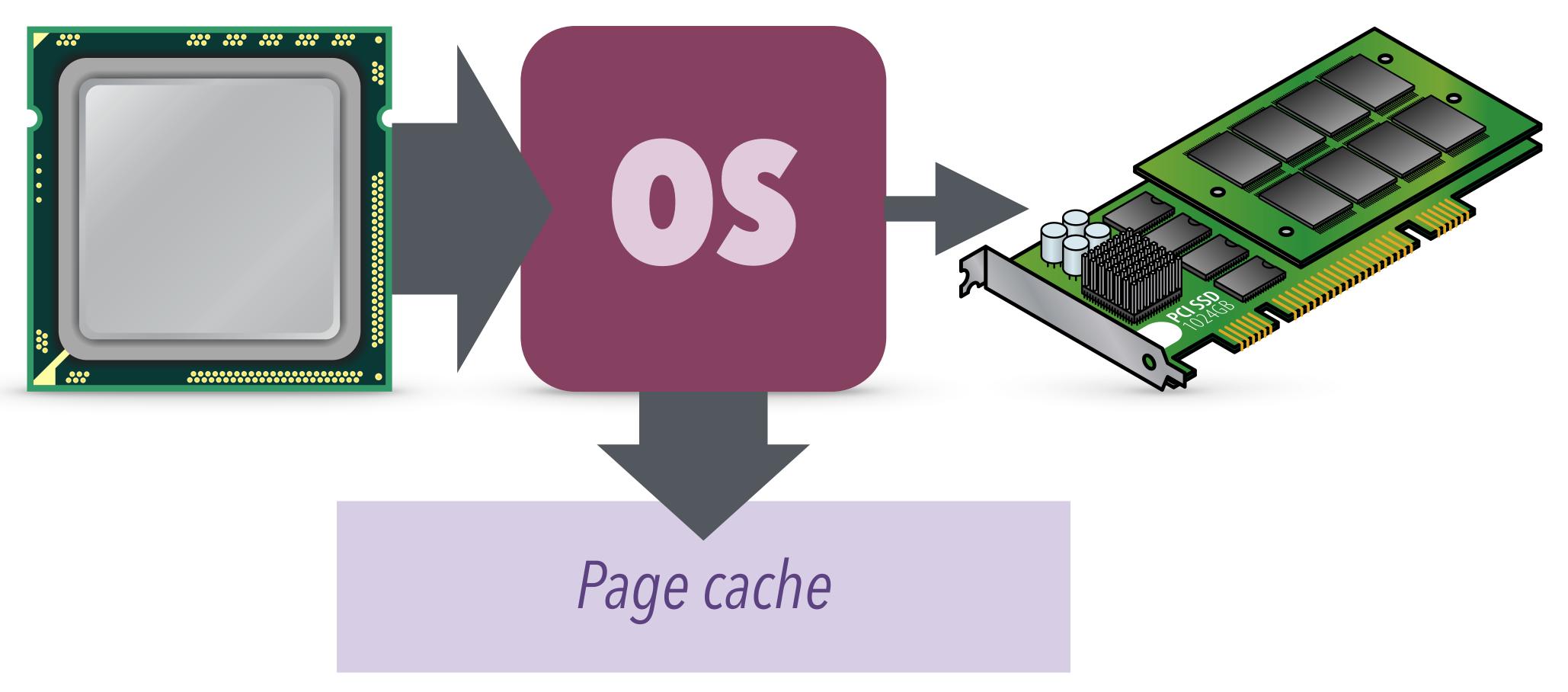
System buffering

- Data served from OS caches
- Decreases SSD usage

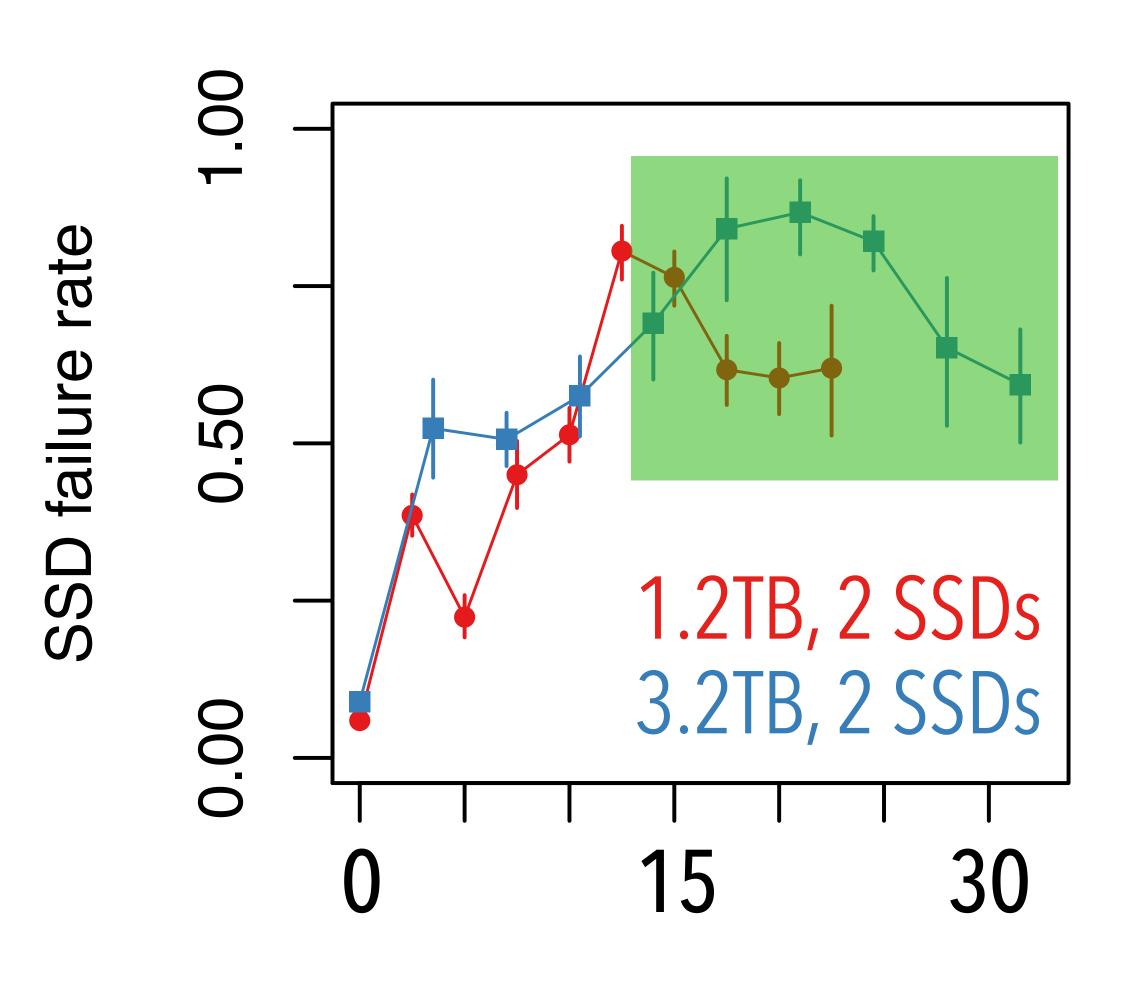
Write amplification

- Updates to small amounts of data
- Increases erasing and copying

System caching reduces the impact of SSD writes



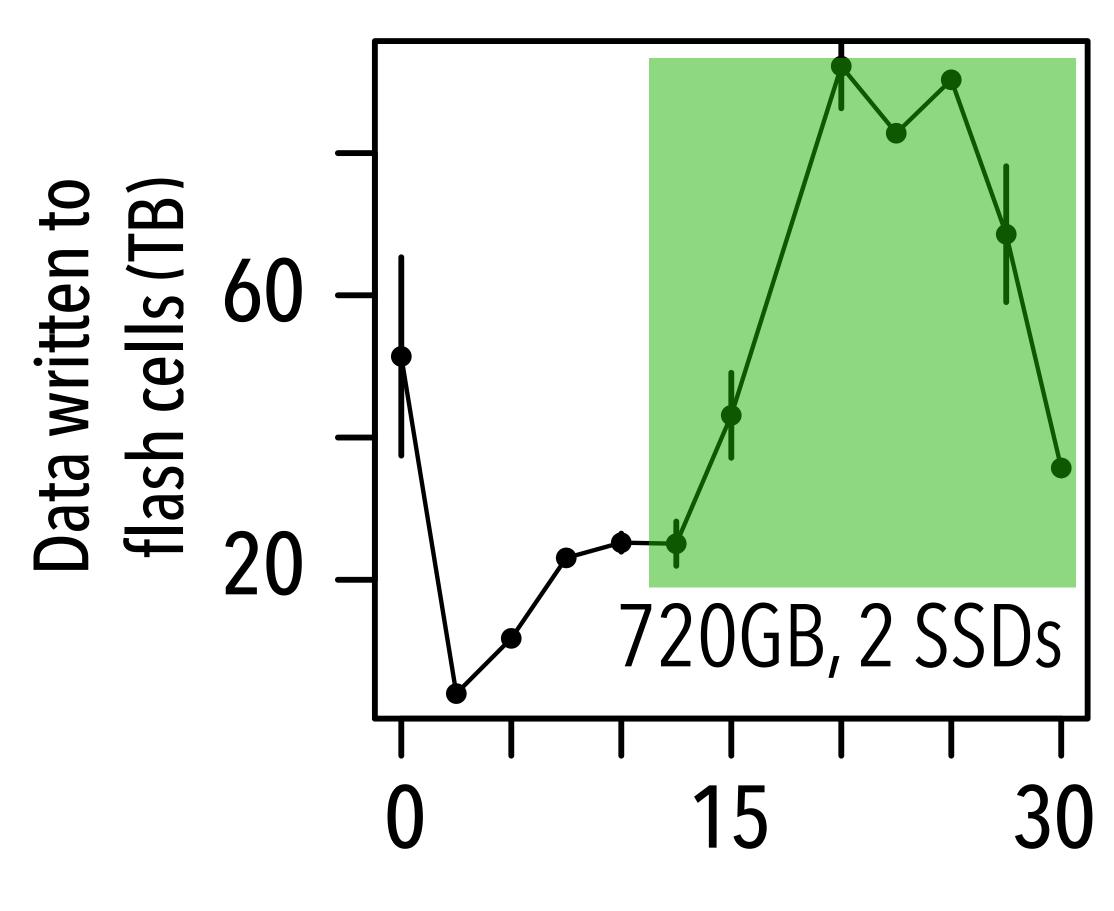
OS WRITES MISLEADING



 No statistically significant correlation with failures at high write volume

Data written to OS (TB)

OS WRITES MISLEADING



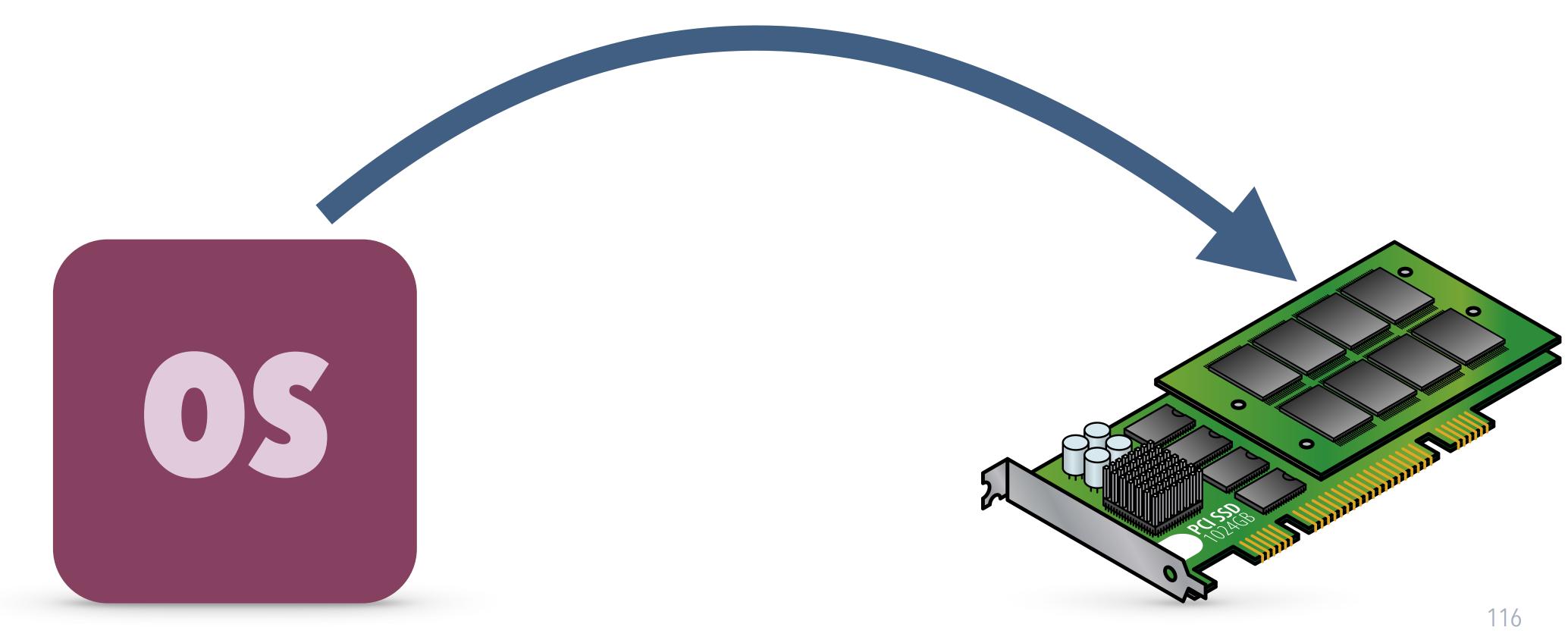
Data written to OS (TB)

- No statistically significant correlation with failures at high write volume
- Data written to OS versus
 SSD is not correlated for high write volume

Flash devices use a

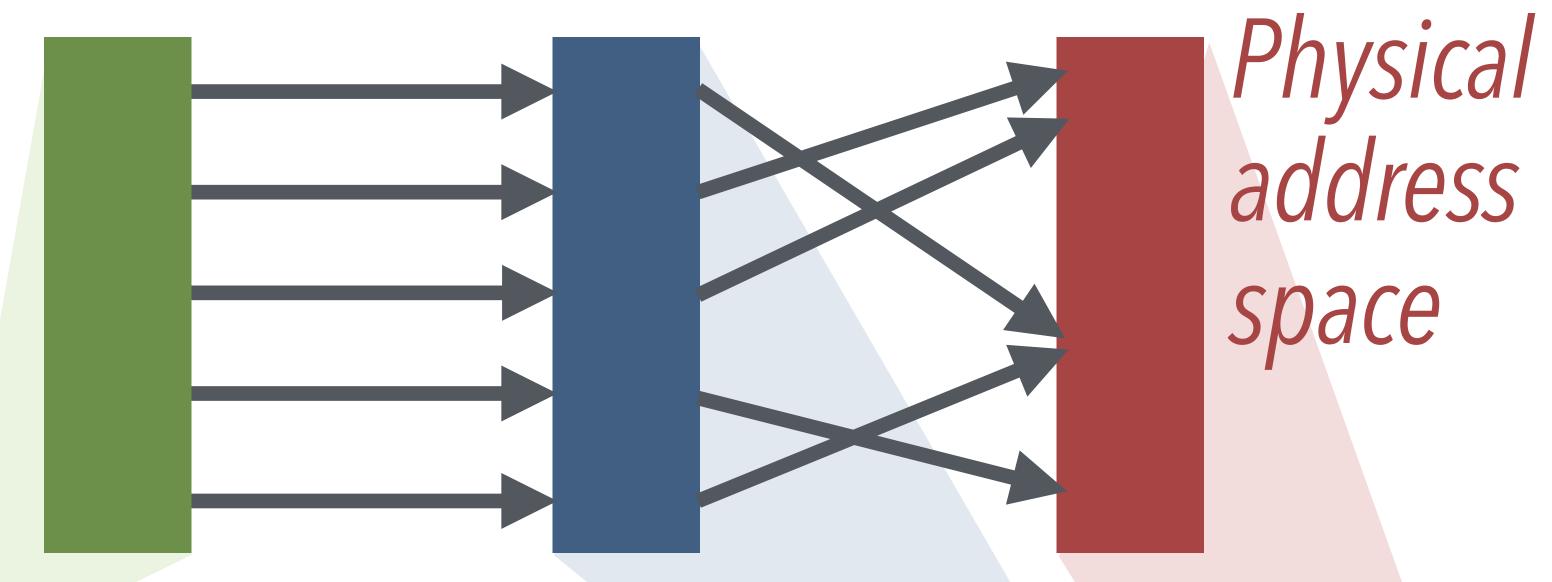
translation layer

to locate data



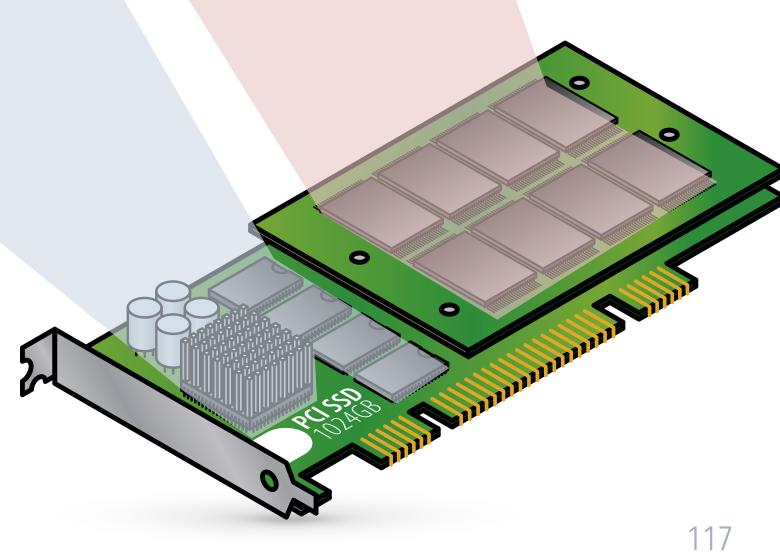
Translation layer

Logical address
Space



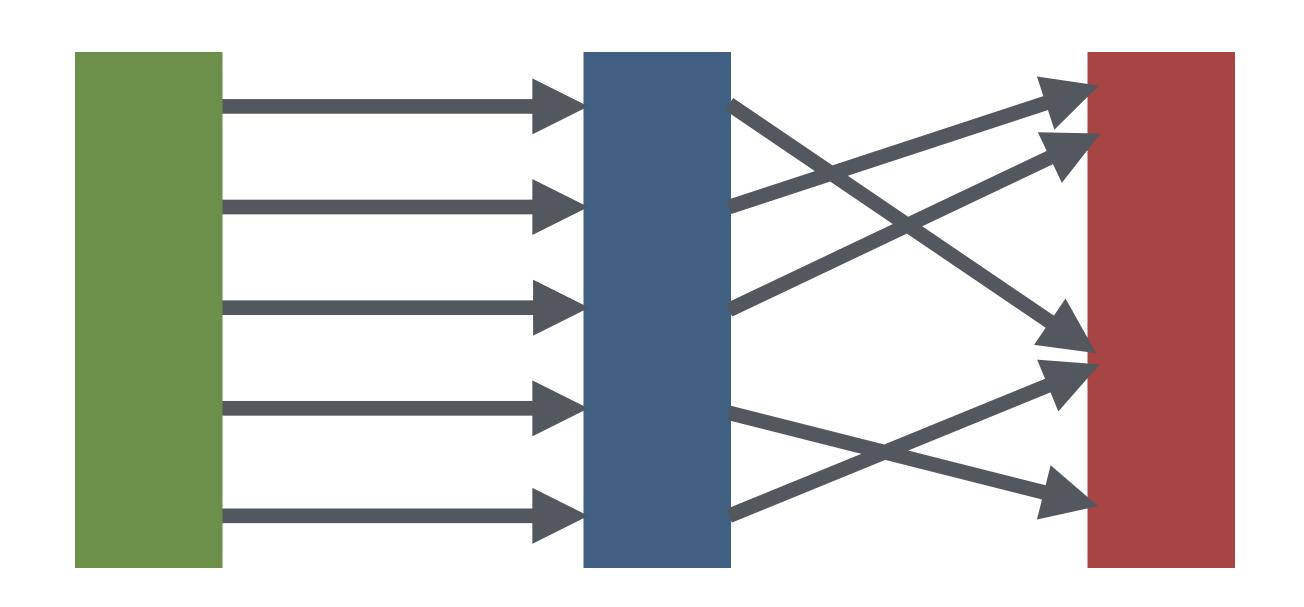


<offset₁, size₁>
<offset₂, size₂>
...



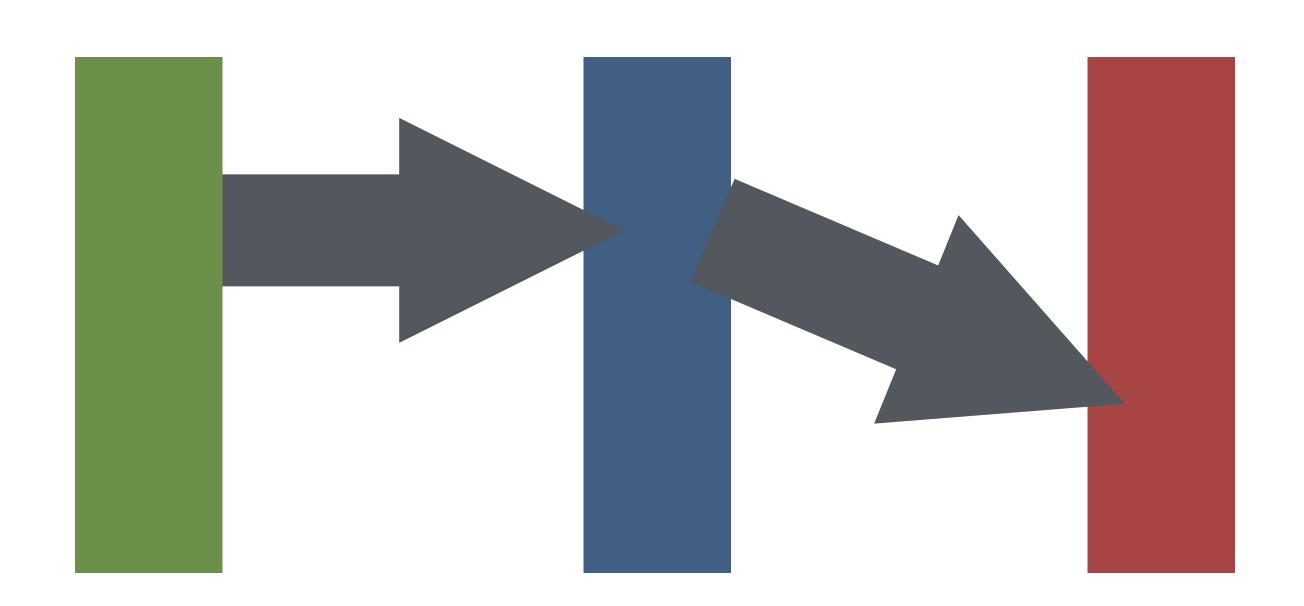
Sparse data layout

more translation metadata potential for higher write amplification

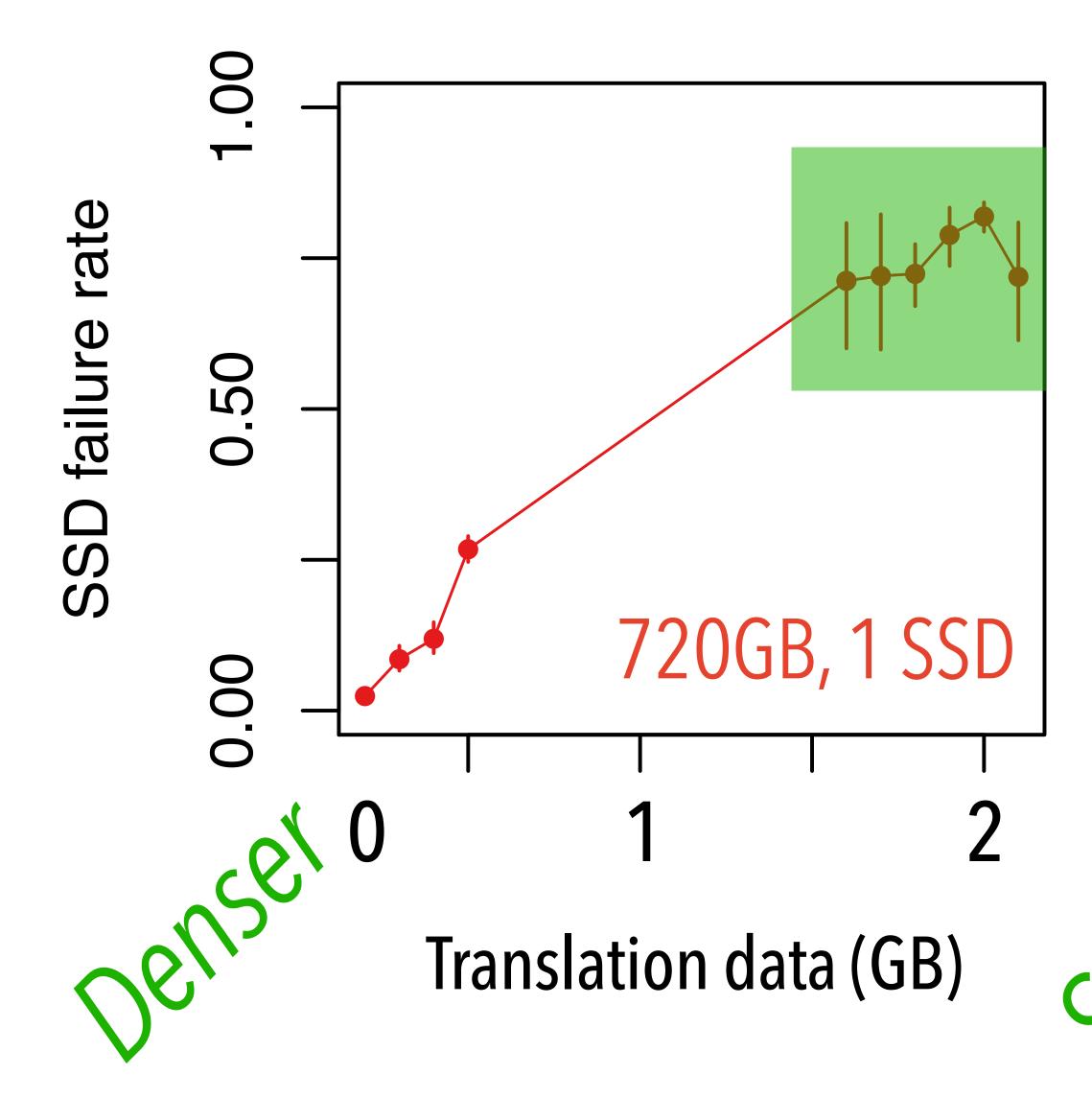


Dense data layout

less translation metadata potential for *lower* write amplification



WRITEAMPLIFICATION



- Sparse data shows signs of higher failure rates
- Likely due to write amplification

KEY SSD CONTRIBUTIONS

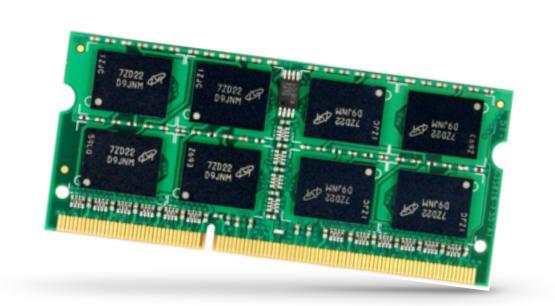
- Distinct lifecycle periods
- Read disturbance not prevalent in the field
- Higher temperatures cause more failures
- Amount of data written by OS is misleading
- Write amplification trends from the field

RELATED WORK

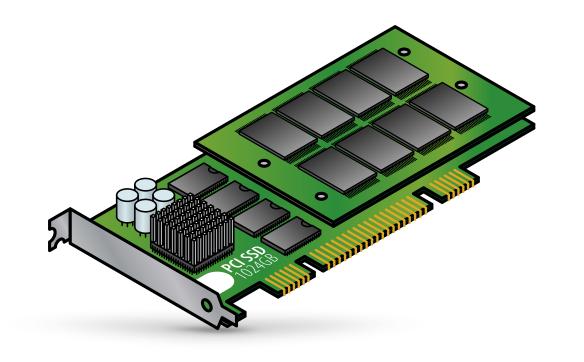
- Examined chip-level failures

 E.g., [Cai+ DATE'12, ICCD'12, DATE'13, ICCD'13, DSN'15, HPCA'17]
- Examined a simulated SSD controller with 45 flash chips [Grupp+ FAST'12]
- Reliability of SSD controllers (NOT chips)
 [Ouyang+ ASPLOS'14]
- Microsoft and Google SSDs over multiple years
 [Narayanan+ SYSTOR'16, Schroeder+ FAST'16]

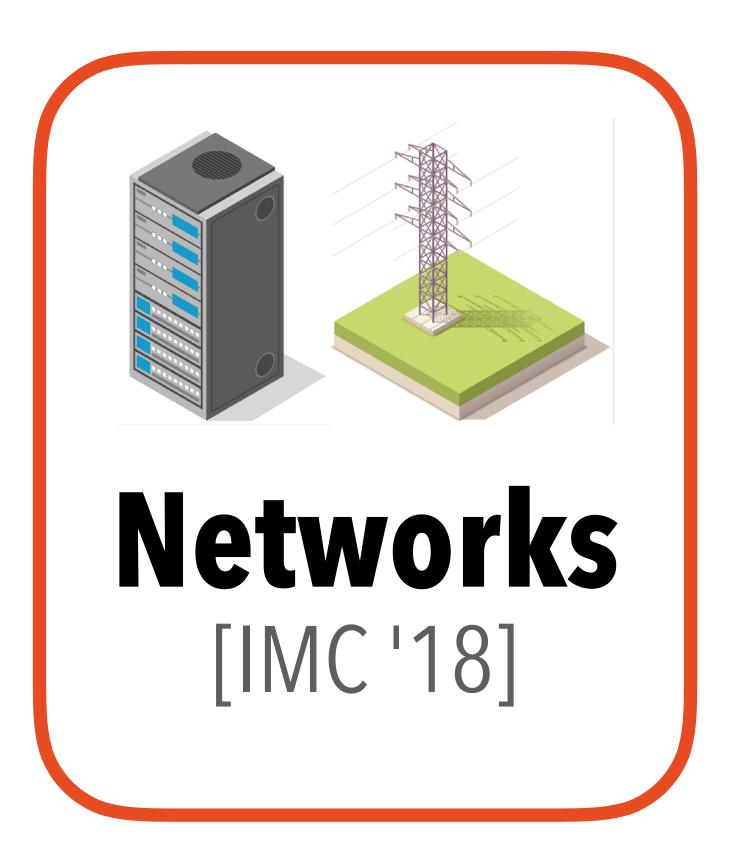
LARGE SCALE STUDIES

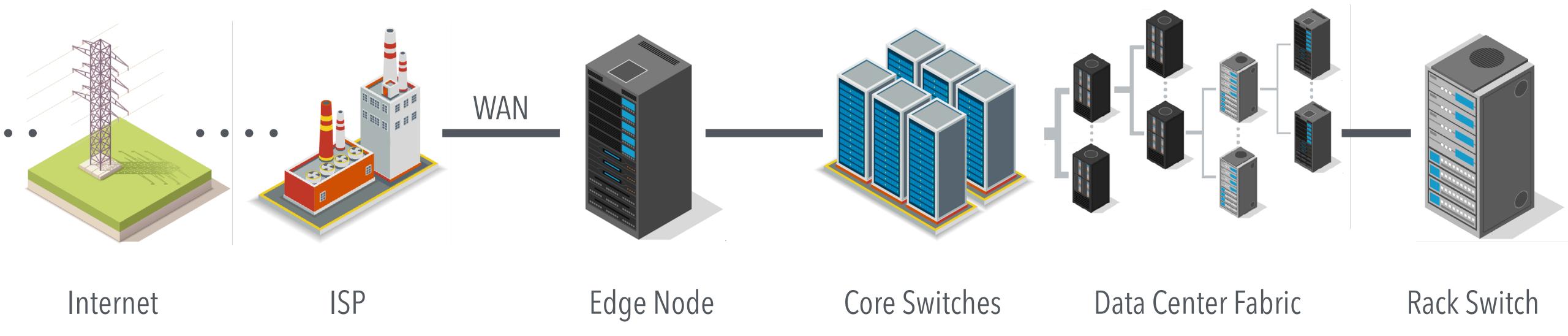


DRAM
[DSN '15]



SSDS
[SIGMETRICS '15]



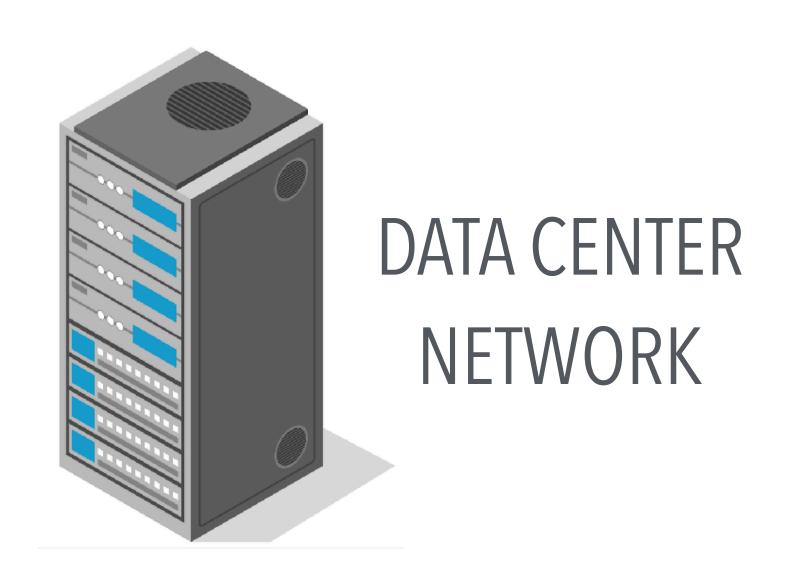


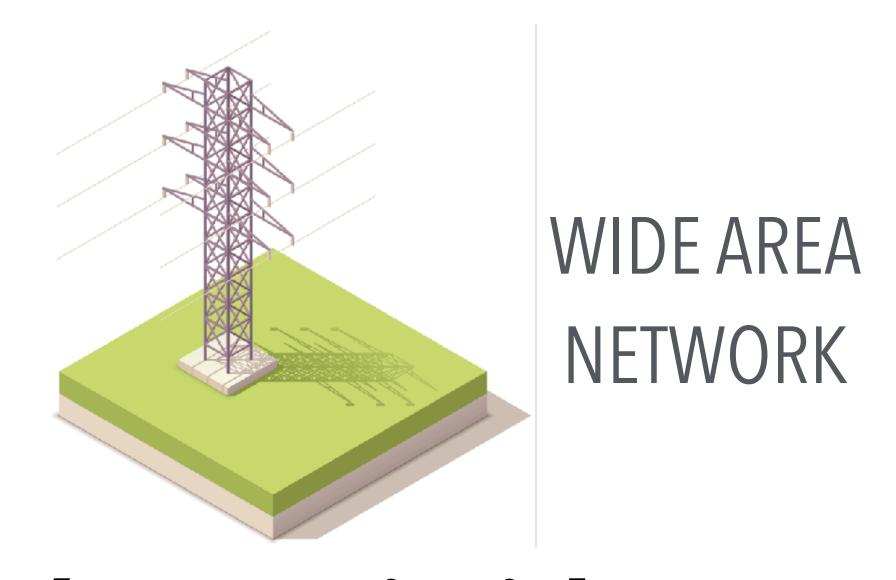
SOFTWARE-AIDED NETWORKS

- Simple, custom switches
- Software-based fabric networks
- Automated repair of common failures



MEASURING NETWORK FAILURE





• Incident reports

- Across Facebook's fleet
- Over 7 years
- Details on faulty device, severity, ...
 Details on location, timing, ...

• Vendor repair tickets

- Across Facebook's fleet
- Over 14 months

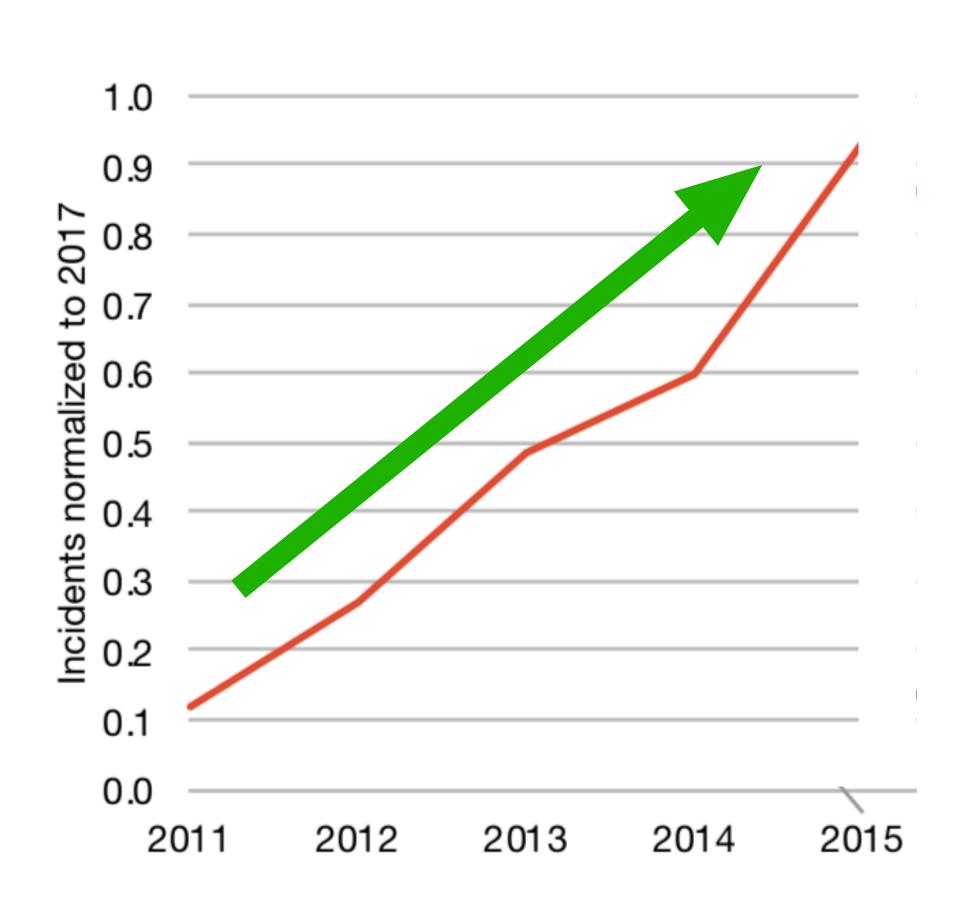
INCIDENT REPORTS

Switch Failures cause Software Failures that result in Incidents (with reports)

KEY NETWORK CONTRIBUTIONS

- Software-aided networks greatly reduce errors
- High bandwidth switches cause more incidents
- Rack switches are a bottleneck for reliability
- Data center WAN reliability models

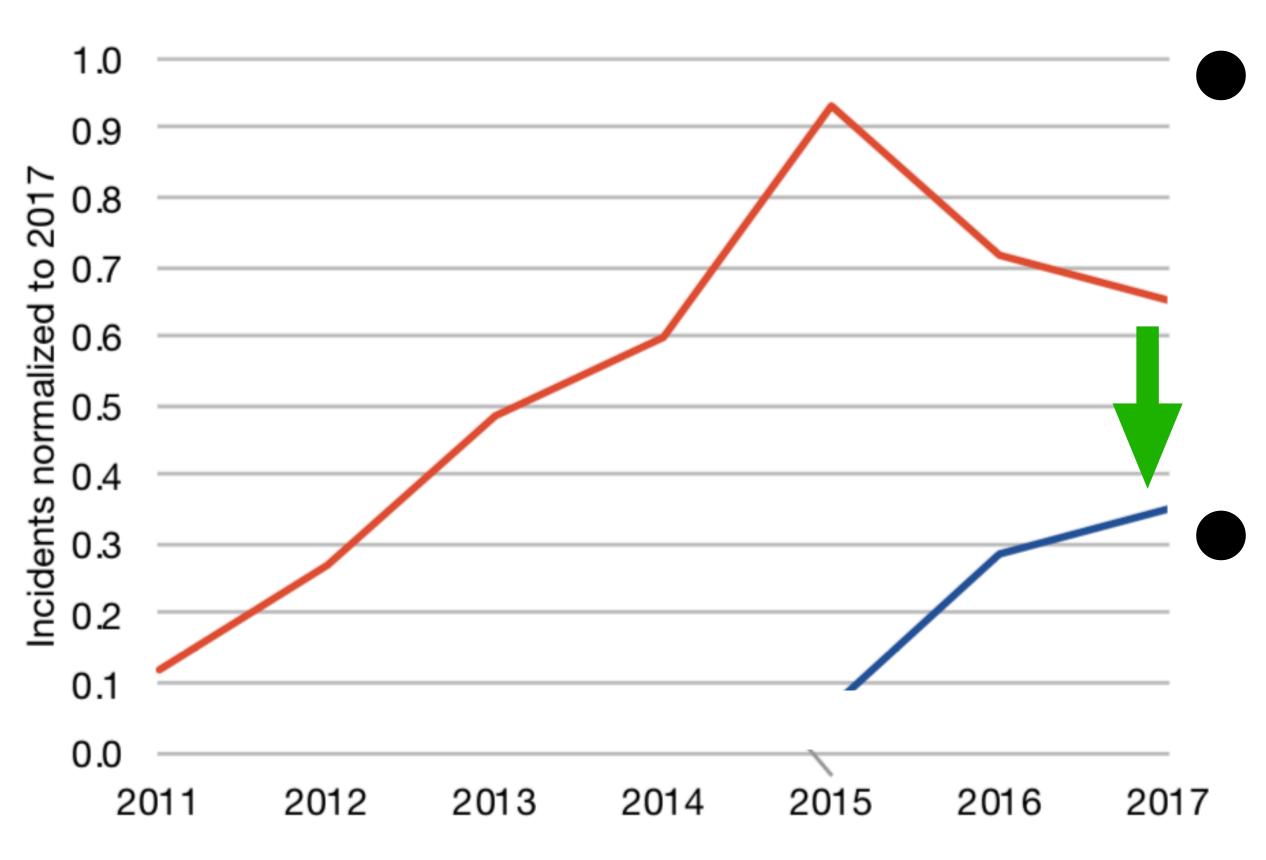
NETWORK DESIGN TRENDS



- Older hard-wired networks
 - 9X incident increase over 4 years

Hard-wired network

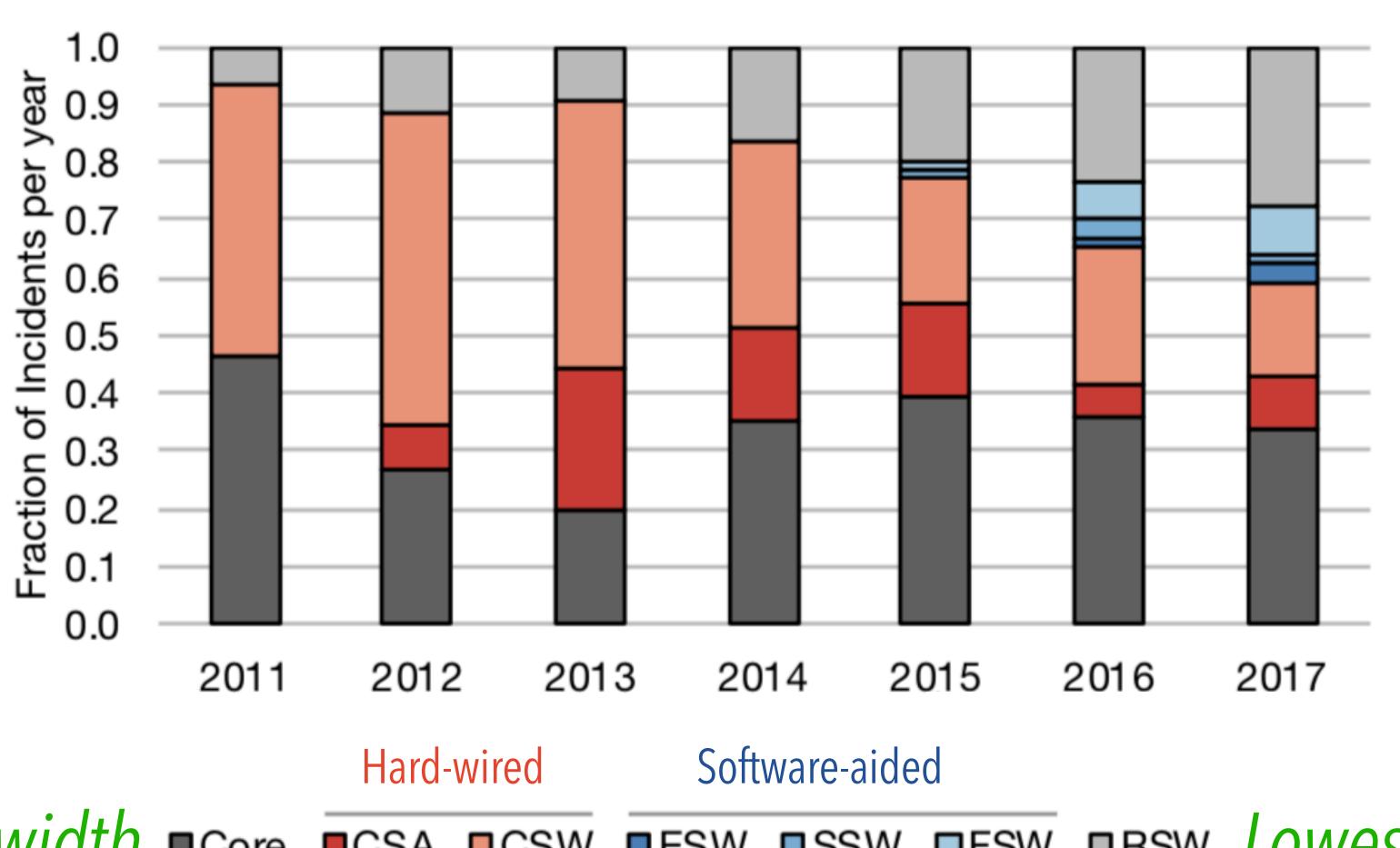
NETWORK DESIGN TRENDS



- Older hard-wired networks
 - 9X incident increase over 4 years
 - Newer software-aided designs
 - 2X fewer incidents
 - 2.8X on a per-device basis

Hard-wired network Software-aided network

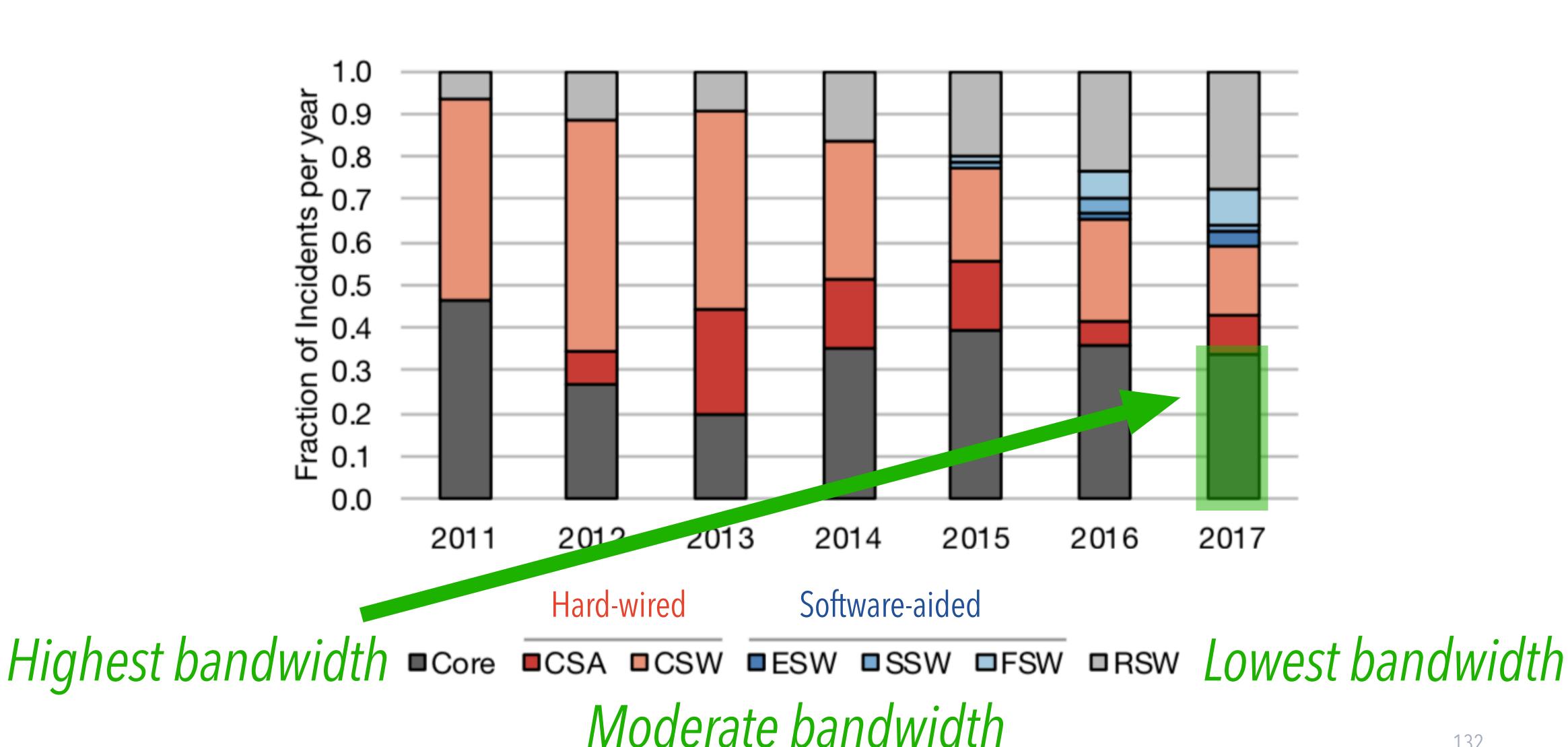
SWITCH TYPE TRENDS



Highest bandwidth •core •csa •csw •ssw •ssw •ssw •ssw Lowest bandwidth

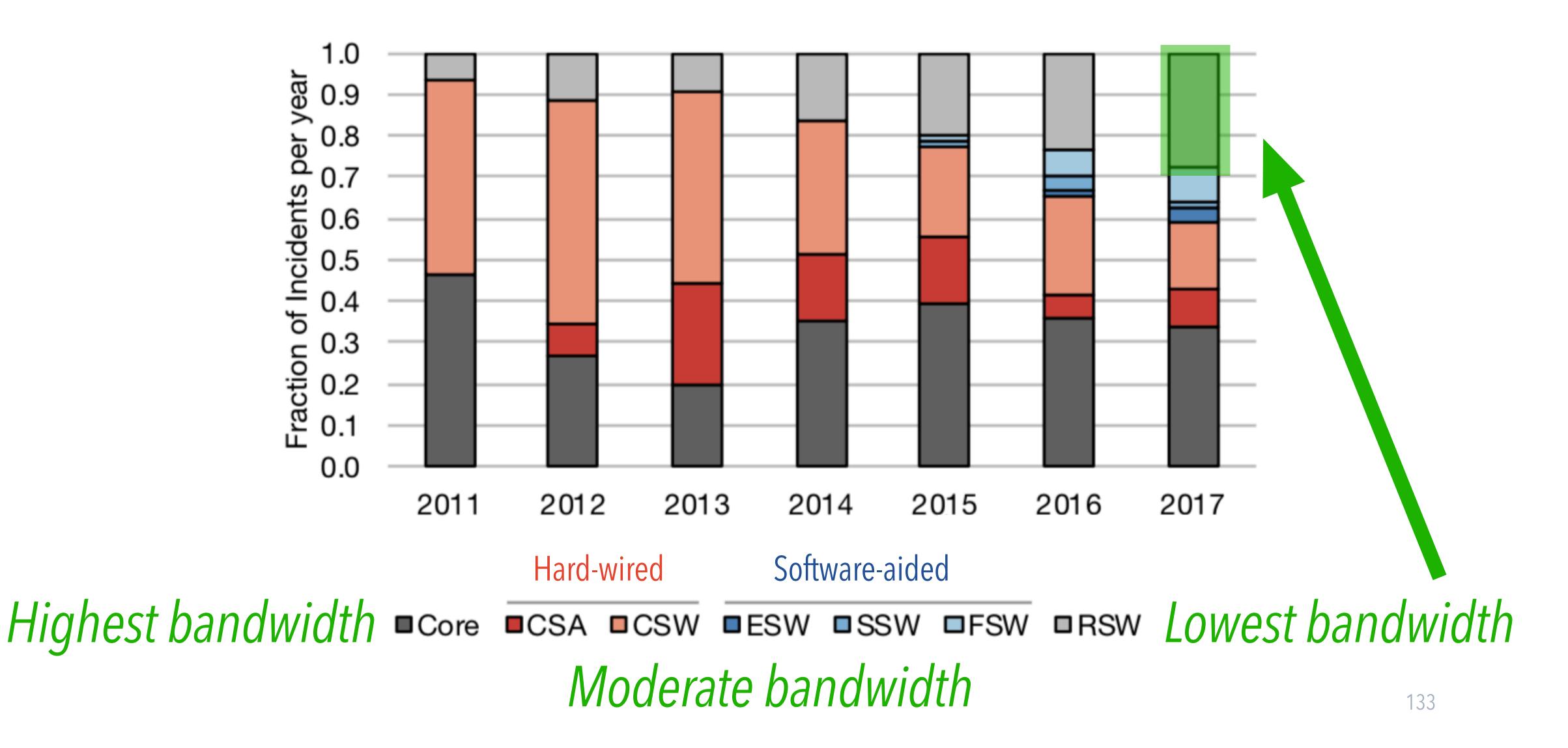
Moderate bandwidth

SWITCH TYPE TRENDS



132

SWITCH TYPE TRENDS



Rack switches make up 82% of network devices

WAN architecture

Edge nodes

- Route requests across different network paths
- Connected by multiple links

Links

Optical fiber cables that connect edges

MODELING WAN RELIABILITY

Failure rate

Repair rate

Edge

Link

MODELING WAN RELIABILITY

Failure rate

Repair rate

Edge

O(months)

O(hours)

Link

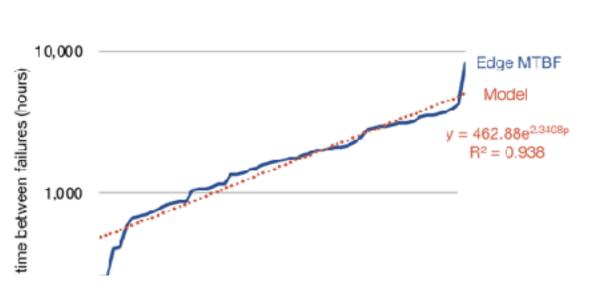
O(months)

O(days)

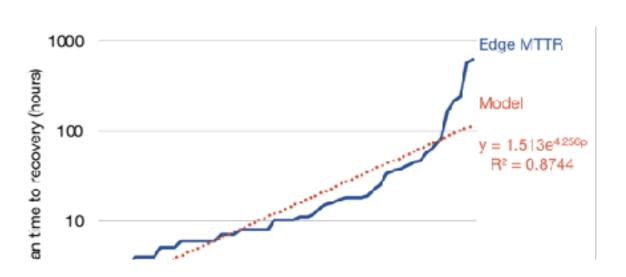
MODELING WAN RELIABILITY

Edge

Failure rate

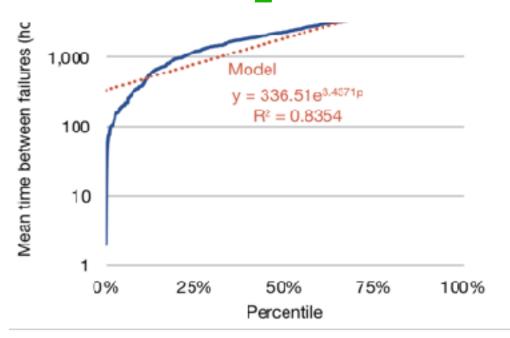


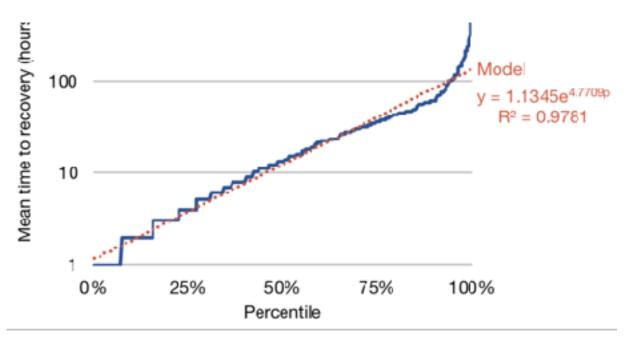
Repair rate



We provide open models —

Link





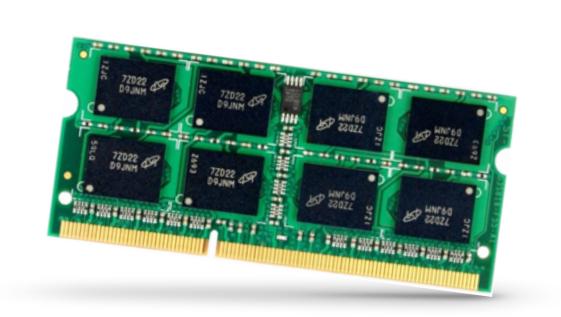
KEY NETWORK CONTRIBUTIONS

- Software-aided networks greatly reduce errors
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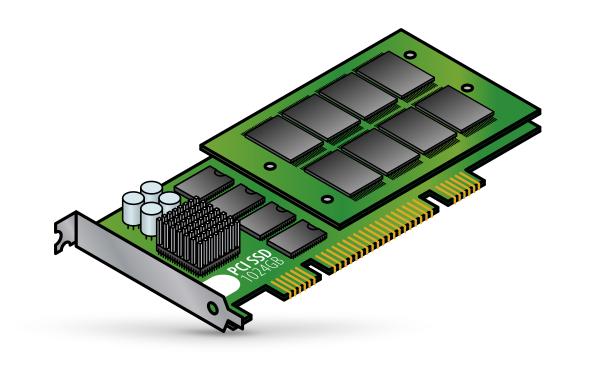
RELATED WORK

- Identify network incidents as leading cause
 [Barroso+ DCaaC, Gunawi+ SoCC'6, Oppenheimer+ USITS'03, Brewer Google Tech. Rep. '17, Wang+ DSN'17]
- Hard-wired network studies
 [Zhuo+ SIGCOMM'17, Gill+ SIGCOMM'11, Potharaju+ IMC'13]
- Complementary large scale works focused on device trends
 [Potharaju+ SoCC'13, Turner+ SIGCOMM'10,
 Govindan+ SIGCOMM'16]

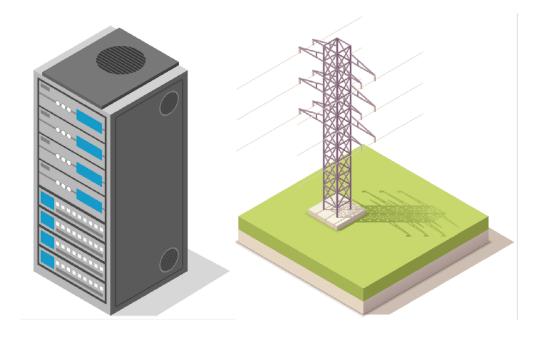
LARGE SCALE STUDIES



DRAM
[DSN '15]



SSDS
[SIGMETRICS '15]



Networks
[IMC '18]

THESIS STATEMENT

If we **measure** the device failures in modern data centers, then we can learn the reasons why devices fail, develop **models** to predict device failures, and learn from failure trends to make **recommendations** to enable workloads to tolerate device failures.

CONCLUSION

The problem of understanding why data center devices fail can be solved by using the scale of modern data centers to observe failures and by building robust statistical models to understand the implications of the failure trends.

CONTRIBUTIONS

- 1. Large scale failure studies
 We shed new light on device trends from the field
- 2. Statistical failure models
 We enable the community to apply what we learn
 - 3. Evaluate best practices in the field We provide insight into how to tolerate failures

LIMITATIONS

Only examined one company's data centers

Do not consider combination of device effects

Do not consider silent data corruption

FUTURE RESEARCH

Further field study based analysis

Other devices, statistical techniques, environments

HW/SW cooperative techniques

Use learnings to inform design decisions

Introspective fault monitoring and reduction

Systems that can identify and adapt their behavior

THESIS PUBLICATIONS

Large scale reliability studies

- DRAM [Meza+ DSN'15]
- SSDs [Meza+ SIGMETRICS'15]
- Network [Meza+IMC'18]

OTHER PhD PUBLICATIONS

Non-volatile memory

- DRAM + NVM [Meza+ CAL'12]
- Persistent Memory [Meza+ WEED'13]
- Multi-Level Cell [Yoon+TACO'14]
- Row Buffers Locality [Yoon+ICCD'15]
- Row Buffer Sizes [Meza+ ICCD'12]

Main memory architecture

- Bit Flips [Luo+ DSN'14]
- Overview [Mutlu+KIISE'15]

Datacenter Energy

Sustainable DC Design
 [Chang+ASPLOS'12]

EARLIER PUBLICATIONS

Energy efficiency studies

- JouleSort [Rivoire+ Computer'07]
- DB Energy [Harizopoulos+ CIDR'09]
- OLTP Energy [Meza+ ISLPED'09]
- Sustainable DC Design [Meza+ IMCE'10]
- Sustainable Server Design [Chang+ HotPower'10]

FACEBOOK PUBLICATIONS

Systems architecture + reliability

- Power Management [Wu+ISCA'16]
- Time Series DBs [Pelkonen+ VLDB'15]
- Load Testing [Veeraraghavan+ OSDI'16]
- Disaster Recovery [Veeraraghavan+ OSDI'18]

ACKNOWLEDGEMENTS

- My advisor, Onur, who had confidence in me even when I didn't
- My committee Greg, James, Kaushik who were always there to listen and guide me
- The SAFARI group at CMU for lifelong friendships
- Family, friends, and colleagues (too many to list!) who kept me going (Partha, Kim, Yee Jiun ...)

LARGE SCALE STUDIES OF MEMORY, STORAGE, AND NETWORK FAILURES IN A MODERN DATA CENTER

THESIS ORAL

JUSTIN MEZA

Committee

Prof. Onur Mutlu (Chair)

Prof. Greg Ganger

Prof. James Hoe

Dr. Kaushik Veeraraghavan (Facebook, Inc.)



BACKUP SLIDES

More Techniques?

- We believe our DRAM work provides a promising direction
 - Analyze failures, build models, design techniques
- At the same time, we wanted to focus on:
 - Instrumentation + analysis of new devices (SSDs)
 - Going more in depth in software-level effects (networks)
- We sketch how to extend our methodology in the thesis

Other Data Centers

- We tie our results to fundamental device properties
- We build models that control for data center specifics
 - E.g., DRAM: Workload has an effect, but our models can factor that in to other features (e.g., CPU util)
- We do see evidence of similarities to other data centers
 - E.g., Networks: Data center networks ≈ B4, WAN ≈ B2 in [Jain+SIGCOMM'13, Govindan+SIGCOMM'16]

How Widespread is the Impact?

- For DRAM and SSDs we observe fail-slow behavior
 - Slow devices can cause cascading failures [FAST'18]
- For Network devices, failure domain is large leading to widespread effects

Fail-Slow at Scale: Evidence of Hardware Performance Faults in Large Production Systems

Haryadi S. Gunawi¹, Riza O. Suminto¹, Russell Sears², Casey Golliher², Swaminathan Sundararaman³, Xing Lin⁴, Tim Emami⁴, Weiguang Sheng⁵, Nematollah Bidokhti⁵, Caitie McCaffrey⁶, Gary Grider⁷, Parks M. Fields⁷, Kevin Harms⁸, Robert B. Ross⁸, Andree Jacobson⁹, Robert Ricci¹⁰, Kirk Webb¹⁰, Peter Alvaro¹¹, H. Birali Runesha¹², Mingzhe Hao¹, and Huaicheng Li¹

¹University of Chicago, ²Pure Storage, ³Parallel Machines, ⁴NetApp, ⁵Huawei, ⁶Twitter, ¹⁰University of Utah, ¹¹University of California, Santa Cruz, and ¹²UChicago Research Computing Center

DRAM Failure Details

- Retention
 - Cells must be refreshed
 - Variable retention time complicates matters
- Disturbance
 - Bit flips due to charged particles
 - Data pattern disturbance & RowHammer effect
- Endurance
 - Wear out due to physical phemonena

SSD Failure Details

- Endurance
 - Cells wear out after many program-erase cycles
 - Floating gate loses ability to adequately store charge
- Temperature
 - Shrinks and expands boards and components
 - Arrhenius effect ages cells at accelerated rate
- Disturbance
 - Pass through voltage causes neighboring cell disturbance
- Program failures, retention failures

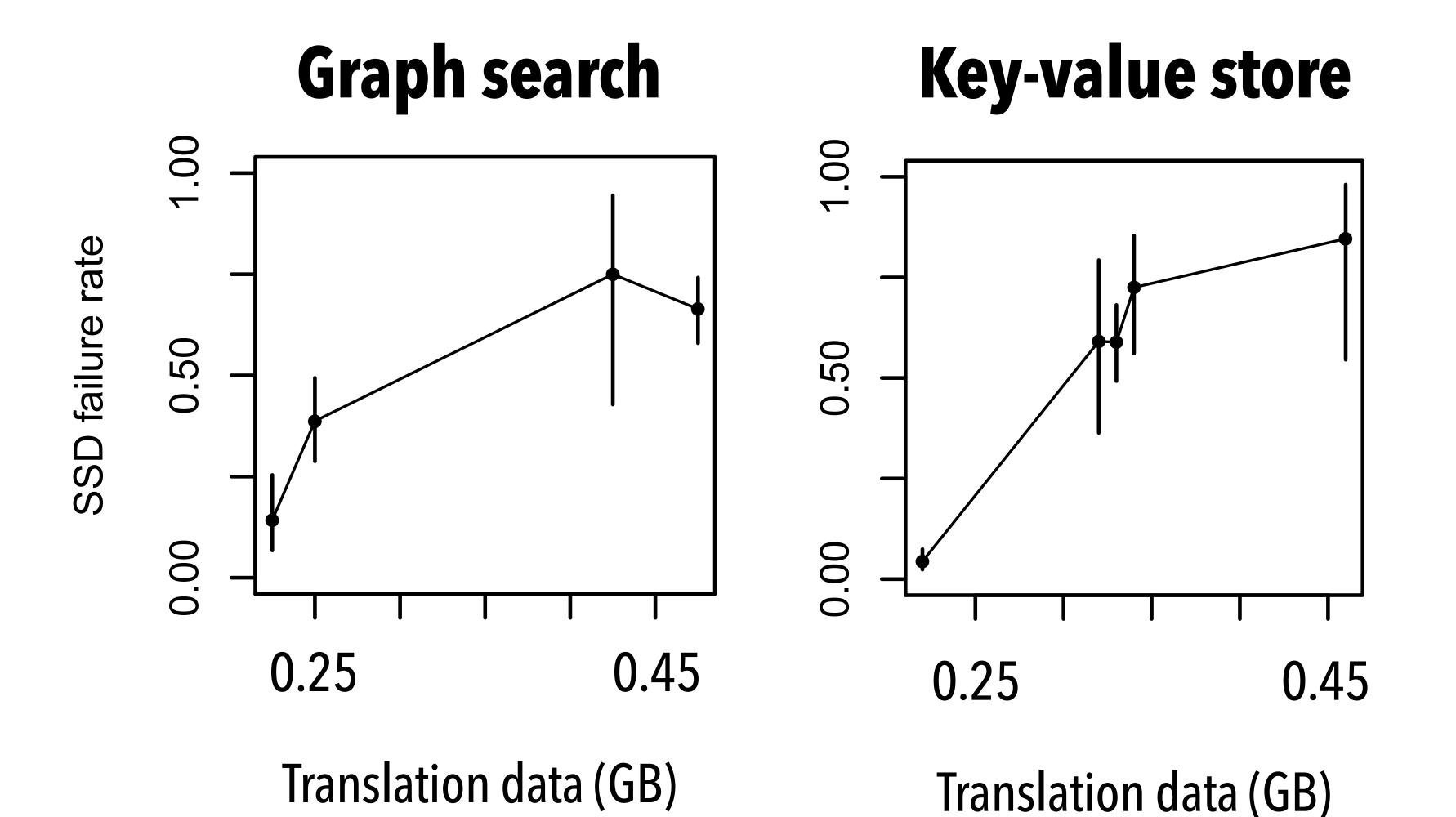
Network Failure Details

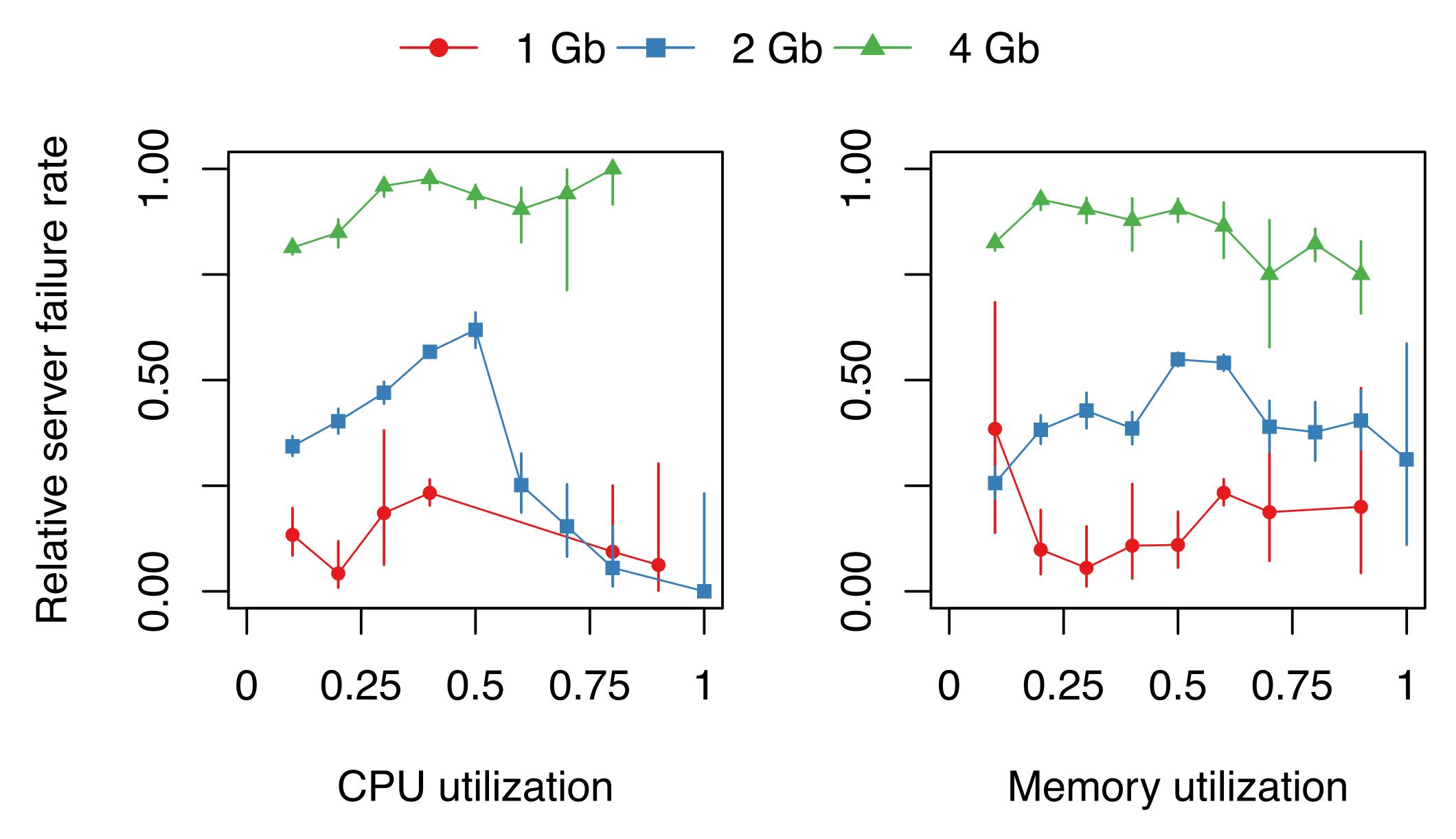
- Hardware (see DRAM and SSD failure details)
- Unplanned fiber cuts
 - Everything from anchors dragging to backhoes
- Bugs
 - Switches run a variety of software, can be buggy
- Operational mistakes
 - Attempting to repair a switch without turning it off

Exploratory analysis

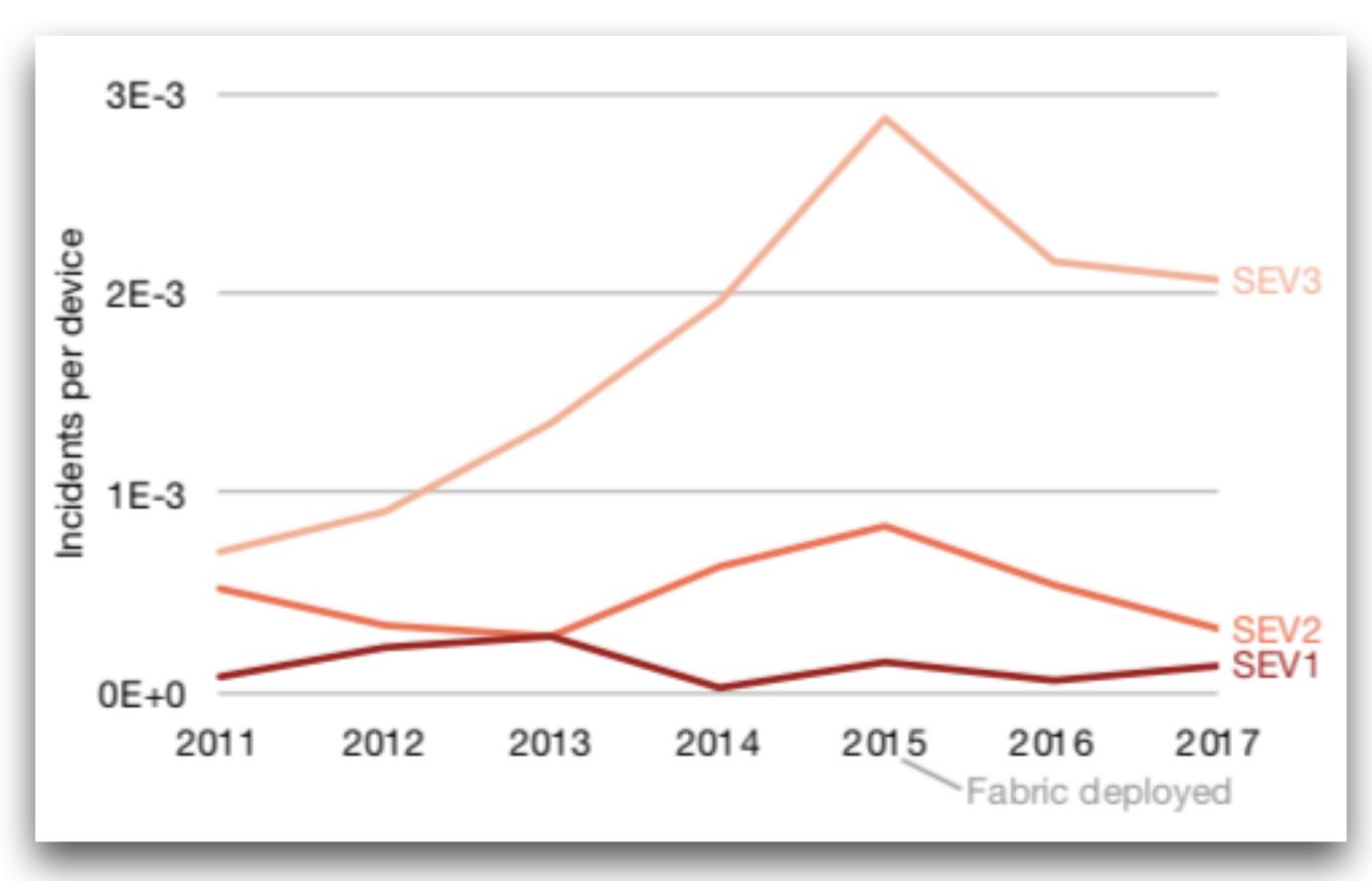
Factor	Low-end	High-end (HE)	HE/\density	HE/\CPUs
Capacity	4 GB	16 GB	4 GB	16 GB
Density2Gb	1	0	1	0
Density4Gb	0	1	0	1
Chips	16	32	16	32
CPU%	50%	25%	25%	50%
Age	1	1	1	1
CPUs	8	16	16	8
Predicted relative failure rate	0.12	0.78	0.33	0.51

WRITEAMPLIFICATION

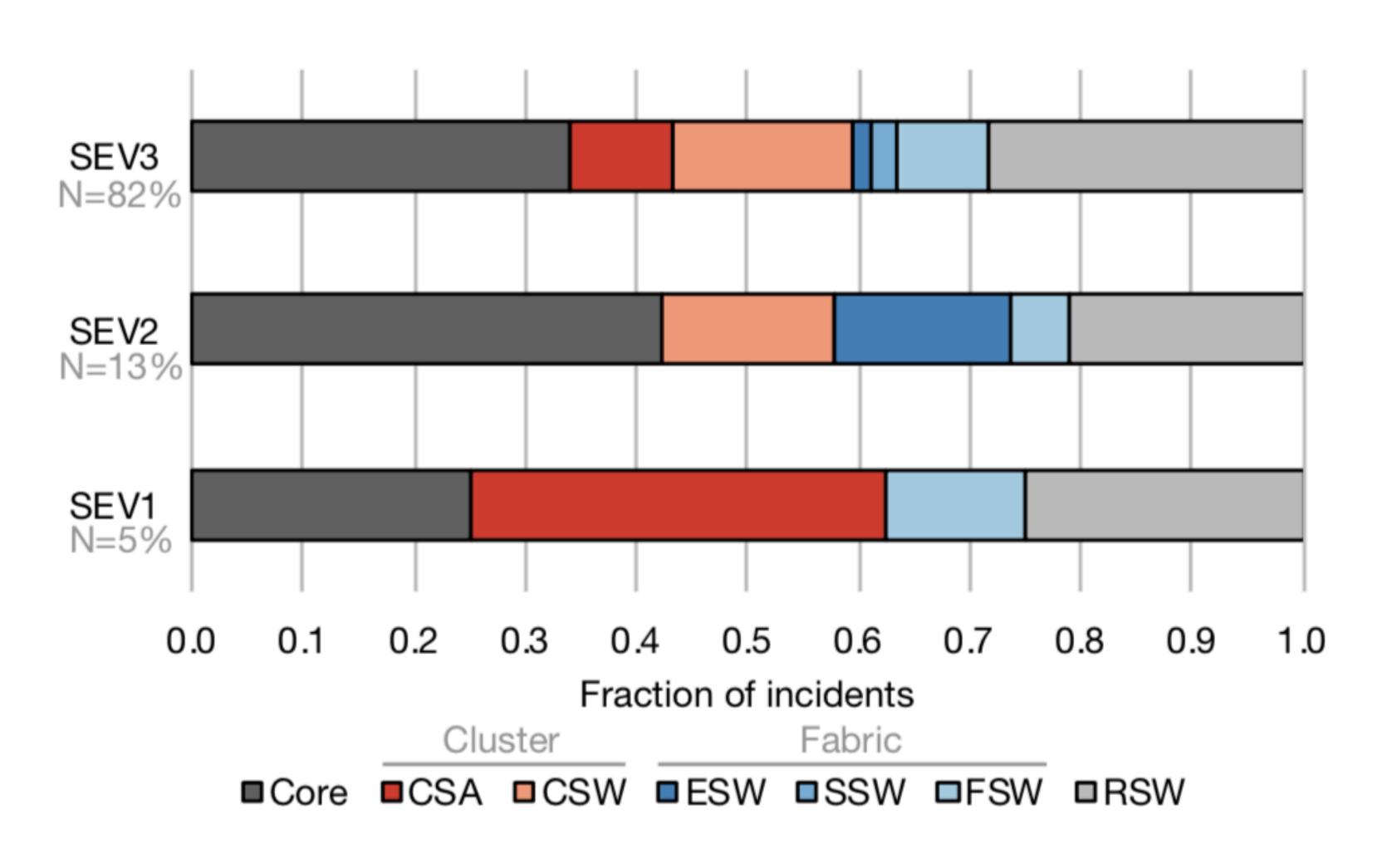




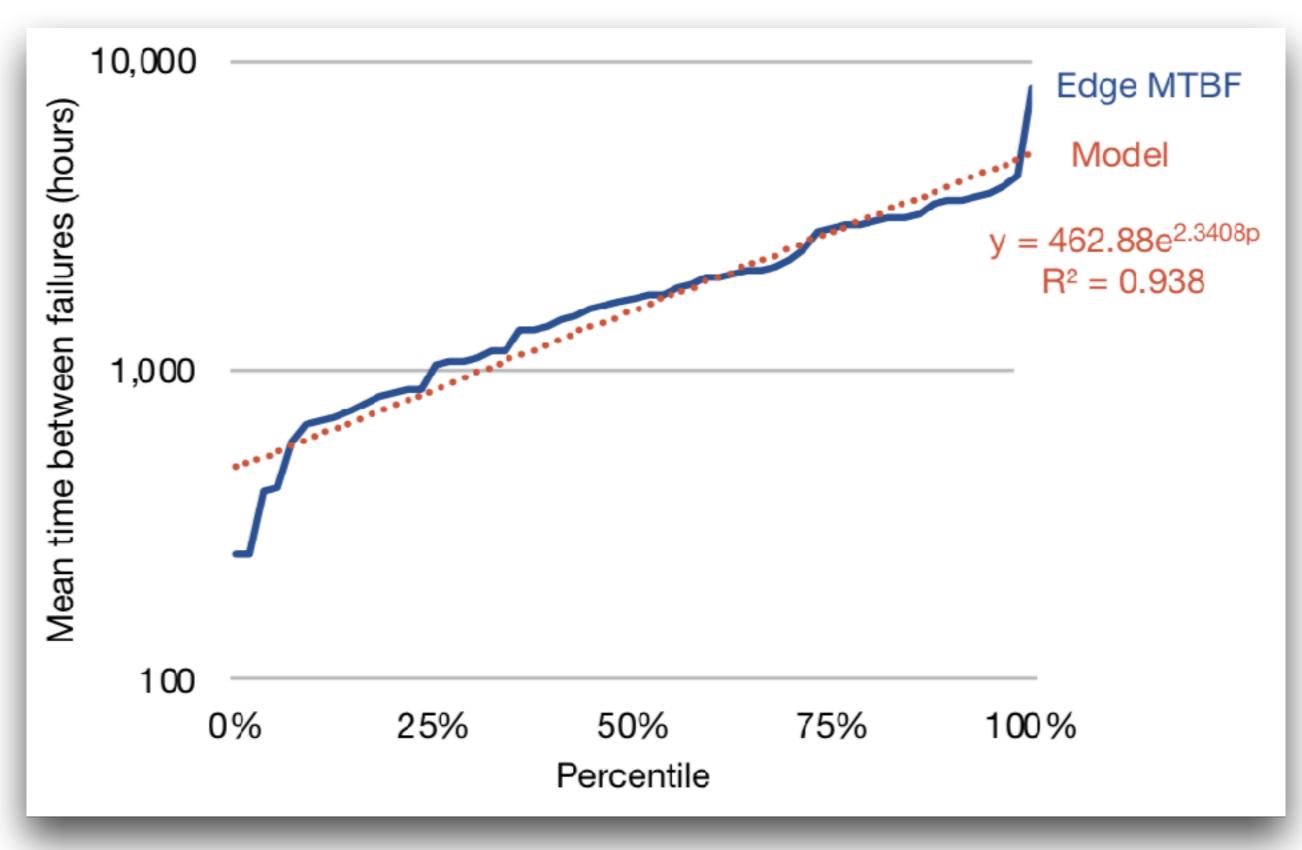
DC fabric has fewer incidents



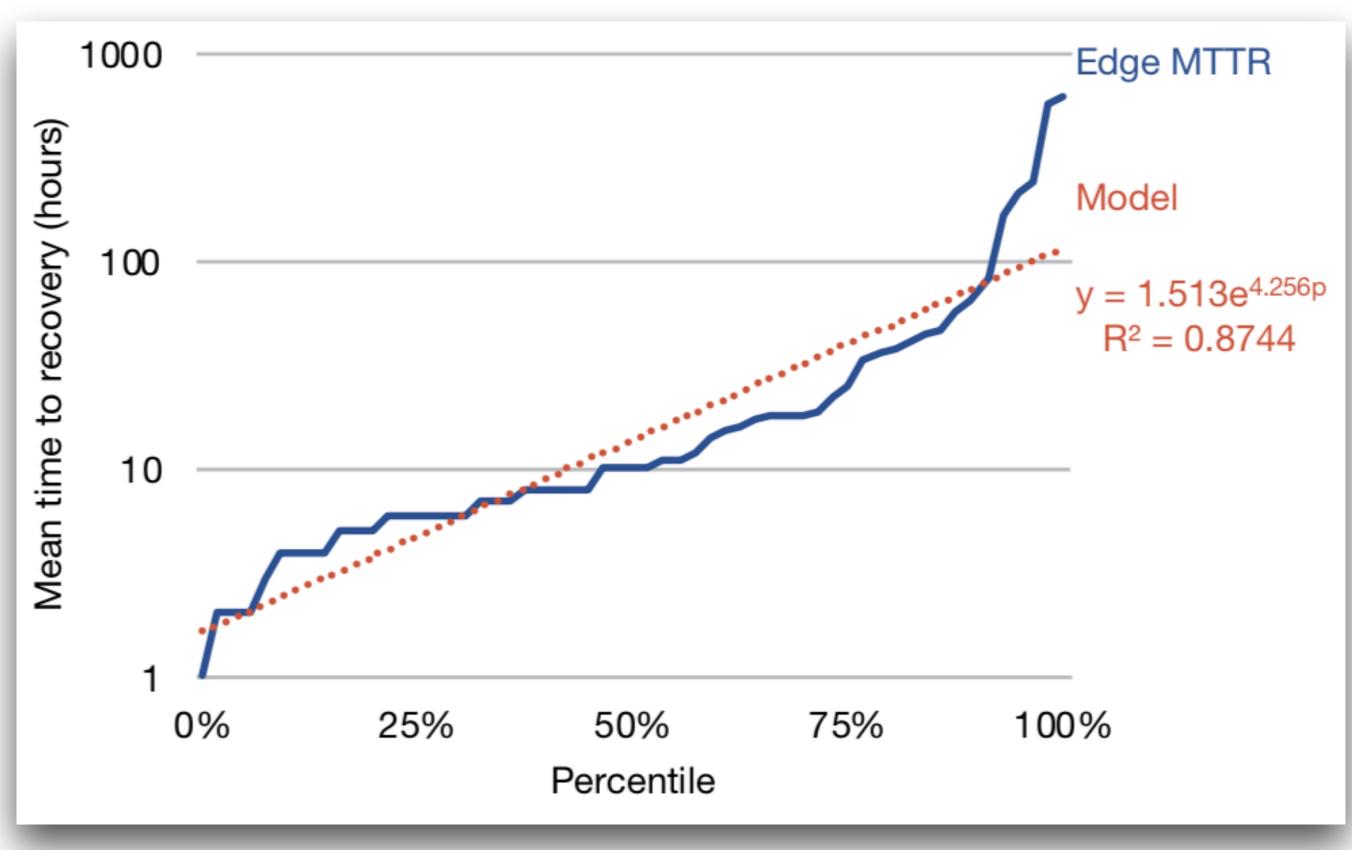
Main cause across all severities



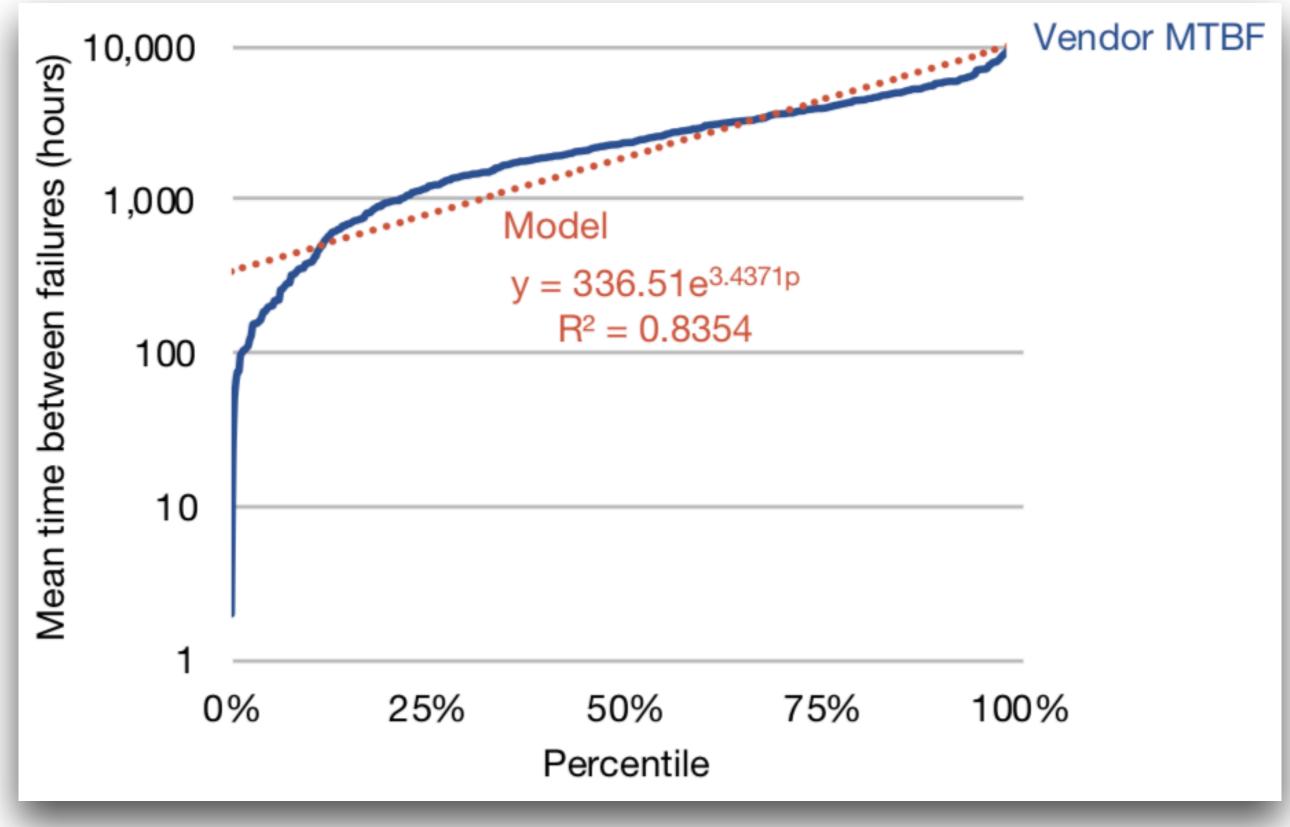
Edge node MTBF distribution



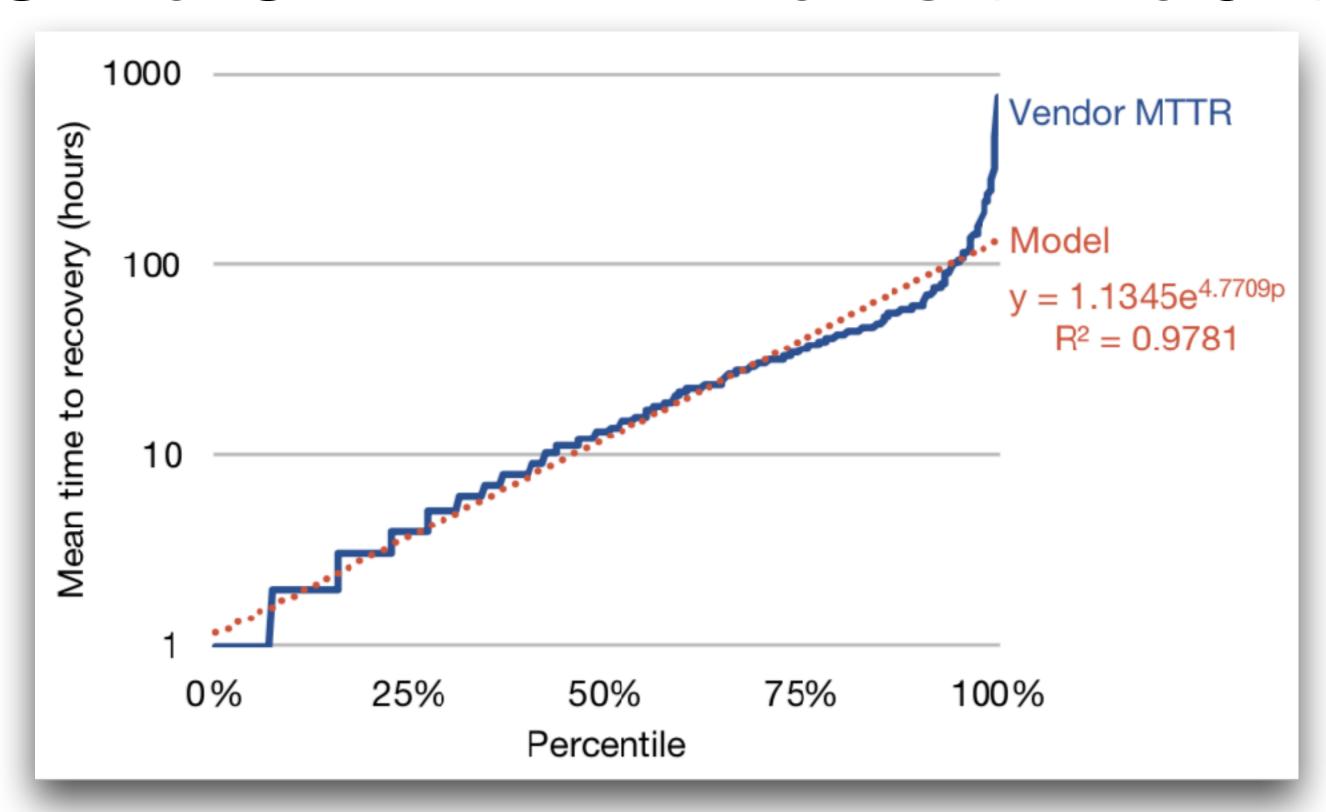
Edge node MTTR distribution



Fiber vendor MTBF distribution



Fiber vendor MTTR distribution



Minimizing backbone outages

